

# 1-Mbit (128K × 8) Quad SPI nvSRAM with Real Time Clock

## Features

- Density
  - 1 Mbit (128K × 8)
- Bandwidth
  - 108-MHz high-speed interface
  - Read and write at 54 MBps
- Serial Peripheral Interface
  - Clock polarity and phase modes 0 and 3
  - Multi I/O option – Single SPI (SPI), Dual SPI (DPI), and Quad SPI (QPI)
- High reliability
  - Infinite read, write, and RECALL cycles
  - One million STORE cycles to nonvolatile elements (SONOS FLASH Quantum Trap)
  - Data retention: 20 years at 85 °C
- Read
  - Commands: Standard, Fast, Dual I/O, and Quad I/O
  - Modes: Burst Wrap, Continuous (XIP)
- Write
  - Commands: Standard, Fast, Dual I/O, and Quad I/O
  - Modes: Burst Wrap
- Data protection
  - Hardware: Through Write Protect Pin ( $\overline{WP}$ )
  - Software: Through Write Disable instruction
  - Block Protection: Status Register bits to control protection
- Special instructions
  - STORE/RECALL: Transfer data between SRAM and Quantum Trap nvSRAM
  - Serial Number: 8-byte customer selectable (OTP)
  - Identification Number: 4-byte Manufacturer ID and Product ID
- Store from SRAM to nonvolatile SONOS FLASH Quantum Trap
  - AutoStore: Initiated automatically at power-down with a small capacitor ( $V_{CAP}$ )
  - Software: Using SPI instruction (STORE)
  - Hardware: HSB pin
- Recall from nonvolatile SONOS FLASH Quantum Trap to SRAM
  - Auto RECALL: Initiated automatically at power-up
  - Software: Using SPI instruction (RECALL)
- Low-power modes
  - Sleep: Average current = 380  $\mu$ A at 85 °C
  - Hibernate: Average current = 8  $\mu$ A at 85 °C
- Operating supply voltages
  - Core  $V_{CC}$ : 2.7 V to 3.6 V
  - I/O  $V_{CCQ}$ : 1.71 V to 2.0 V

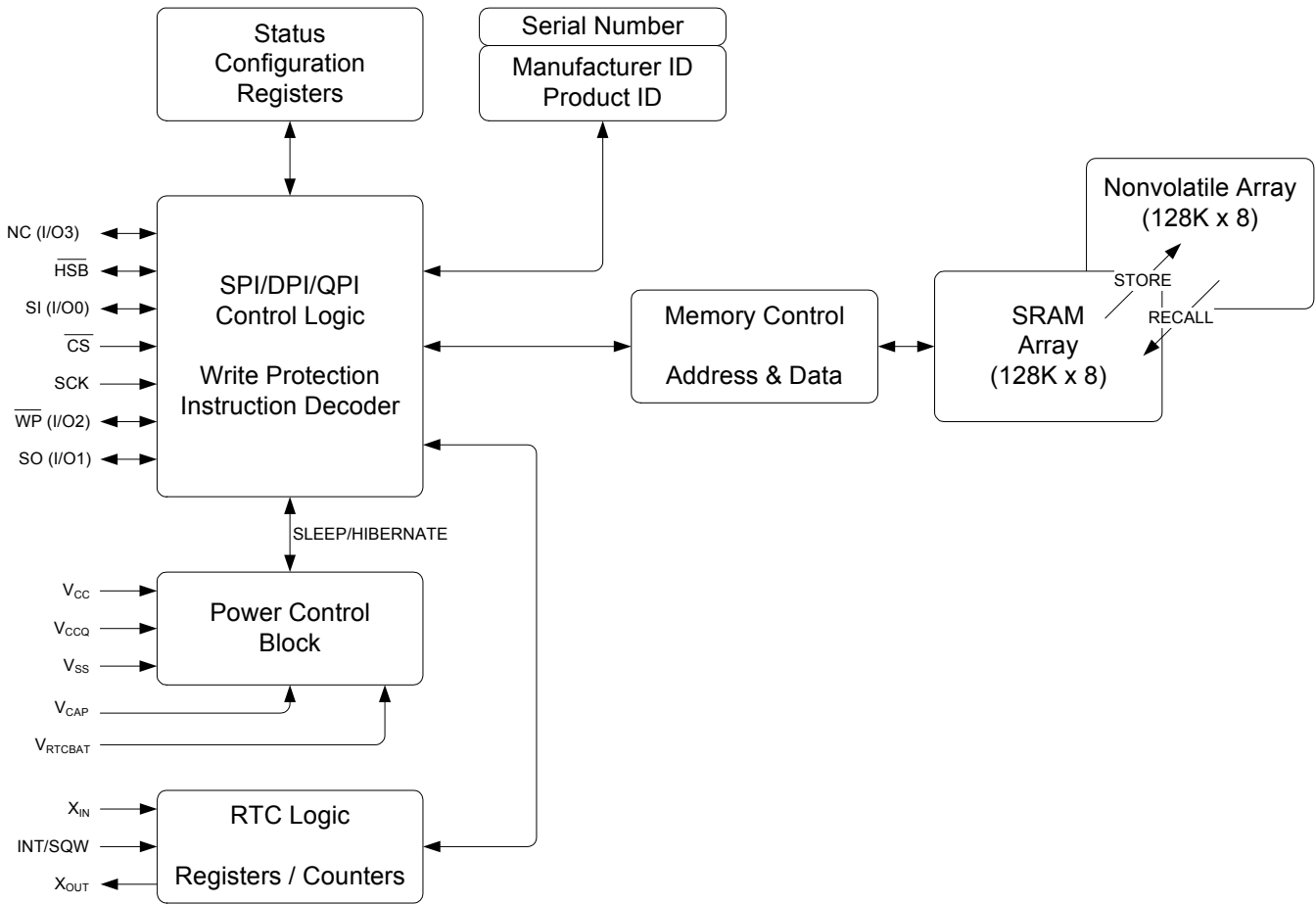
- Temperature range
  - Industrial: –40 °C to 85 °C
- Packages
  - 16-pin SOIC

## Functional Overview

The Cypress CY14V101PS combines a 1-Mbit nvSRAM with a QPI interface. The QPI allows writing and reading the memory in either a single (one I/O channel for one bit per clock cycle), dual (two I/O channels for two bits per clock cycle), or quad (four I/O channels for four bits per clock cycle) through the use of selected opcodes.

The memory is organized as 128 Kbytes each consisting of SRAM and nonvolatile SONOS FLASH Quantum Trap cells. The SRAM provides infinite read and write cycles, while the nonvolatile cells provide highly reliable storage of data. Data transfers from SRAM to the nonvolatile cells (STORE operation) take place automatically at power-down. On power-up, data is restored to the SRAM from the nonvolatile cells (RECALL operation). The user can initiate the STORE and RECALL operations through SPI instructions.

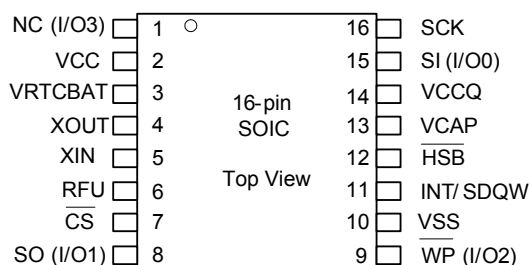
**Logic Block Diagram**



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## Pinout

**Figure 1. 16-pin SOIC Pinout**


## Pin Definitions

Pin Name	I/O Type	Description
NC (I/O3)	Input	Not connected. In Single or Dual mode, this pin is not connected and left floating. These two modes do not support QSPI instructions.
	Input/Output	I/O3: When the part is in Quad mode, the NC (I/O3) pin becomes I/O3 pin and acts as input/output. In Quad mode supporting SPI/DPI instructions, this pin needs to be tri-stated while CS is enabled.
V <sub>CCQ</sub>	Power Supply	Power supply for the I/Os of the device.
V <sub>CC</sub>	Power Supply	Power supply to the core of the device.
$\overline{\text{CS}}$	Input	Chip Select. Activates the device when pulled LOW. Driving this pin HIGH puts the device in standby state.
SO (I/O1)	Output	Serial Output. Pin for output of data through SPI.
	Input/Output	I/O1: When the part is in dual or quad mode, the SO (I/O1) pin becomes I/O1 pin and acts as input/output.
$\overline{\text{WP}}$ (I/O2)	Input	Write Protect. Implements hardware write-protection in SPI/DPI modes.
	Input/Output	I/O2: When the part is in quad mode, the $\overline{\text{WP}}$ (I/O2) pin becomes an I/O2 pin and acts as input/output.
V <sub>SS</sub>	Ground	Power supply ground to the core and I/Os of the device.
$\overline{\text{HSB}}$	Input/Output	Hardware STORE Busy: Output: Indicates the busy status of nvSRAM when LOW. After each Hardware and Software STORE operation, HSB is driven HIGH for a short time ( $t_{\text{HHHD}}$ ) with standard output HIGH current and then a weak internal pull-up resistor keeps this pin HIGH (external pull-up resistor connection is optional). Input: Hardware STORE can be initiated by pulling this pin LOW externally.
V <sub>CAP</sub>	Power Supply	AutoStore Capacitor. Supplies power to the nvSRAM during power loss to STORE data from the SRAM to nonvolatile elements. If AutoStore is not needed, this pin must be left as No Connect. It must never be connected to ground.
V <sub>RTCbat</sub>	Power supply	Battery backup for RTC.
Xout	Output	Crystal output connection. Left unconnected if RTC feature is not used.
Xin	Input	Crystal input connection. Left unconnected if RTC feature is not used.

**Pin Definitions** (continued)

Pin Name	I/O Type	Description
INT/SQW	Output	Interrupt output/calibration/square wave. Programmable to respond to the clock alarm, the watchdog timer, and the power monitor. Also programmable to either active HIGH (push or pull) or LOW (open drain). In calibration mode, a 512-Hz square wave is driven out. In the square wave mode, you may select a frequency of 1 Hz, 512 Hz, 4,096 Hz, or 32,768 Hz to be used as a continuous output. Left unconnected if RTC feature is not used.
SI (I/O0)	Input	Serial Input. Pin for input of all SPI instructions and data.
	Input/Output	I/O0: When the part is in dual or quad mode, the SI (I/O0) pin becomes I/O0 pin and acts as input/output.
SCK	Input	Serial Clock. Runs at speeds up to a maximum of $f_{SCK}$ . Serial input is latched at the rising edge of this clock. Serial output is driven at the falling edge of the clock.
NC	–	Not connected.
RFU	–	Reserved for future use.

## Device Operation

CY14V101PS is a 1-Mbit quad serial interface nvSRAM memory with a SONOS FLASH nonvolatile element interleaved with an SRAM element in each memory cell. All the reads and writes to nvSRAM happen to the SRAM, which gives nvSRAM the unique capability to handle infinite writes to the memory. The data in SRAM is secured by a STORE sequence, which transfers the data in parallel to the nonvolatile cells. A small capacitor ( $V_{CAP}$ ) is used to AutoStore the SRAM data into the nonvolatile cells when power goes down providing data integrity. The nonvolatile cells are built in the reliable SONOS technology make nvSRAM the ideal choice for data storage.

The 1-Mbit memory array is organized as 128 Kbytes. The memory can be accessed through a standard SPI interface (Single mode, Dual mode, and Quad mode) up to clock speeds of 40-MHz with zero-cycle latency for read and write operations. This SPI interface also supports 108-MHz operations (Single mode, Dual mode, and Quad mode) with cycle latency for read operations only. The device operates as a SPI slave and supports SPI modes 0 and 3 (CPOL, CPHA = [0, 0] and [1, 1]). All instructions are executed using Chip Select ( $\overline{CS}$ ), Serial Input (SI) (I/O0), Serial Output (SO) (I/O1), and Serial Clock (SCK) pins in single and dual modes. Quad mode uses  $\overline{WP}$  (I/O2) and I/O3 pins as well for command, address, and data entry.

The device uses SPI opcodes for memory access. The opcodes support SPI, Dual Data, Dual Addr/Data, Dual I/O, Quad Data, Quad Addr/Data, and Quad I/O modes for read and write operations. In addition, four special instructions are included that allow access to nvSRAM specific functions: STORE, RECALL, AutoStore Disable (ASDI), and AutoStore Enable (ASEN).

The device has built-in data security features. It provides hardware and software write-protection through the  $\overline{WP}$  pin and WRDI instruction respectively. Furthermore, the memory array block is write-protected through Status register block protect bits.

### SRAM Write

All writes to nvSRAM are carried out on the SRAM cells and do not use any endurance cycles of the SONOS FLASH nonvolatile memory. This allows you to perform infinite write operations. A write cycle is initiated through one of the Write instructions: WRITE, DIW, QIW, DIOW, and QIOW. The Write instructions consist of a write opcode, three bytes of address, and one byte of data. Write to nvSRAM is done at SPI bus speed with zero-cycle latency.

The device allows burst mode writes. This enables write operations on consecutive addresses without issuing a new Write instruction. When the last address in memory is reached in burst mode, the address rolls over to 0x00000 and the device continues to write.

The SPI write cycle sequence is defined explicitly in the nvSRAM Read Write Instructions in [“SPI Functional Description”](#) on page 12.

### SRAM Read

All reads to nvSRAM are carried out on the SRAM cells at SPI bus speeds. Read instruction (READ) executes at 40-MHz with zero cycle latency. It consists of a Read opcode byte followed by three bytes of address. The data is read out on the data output pin/pins.

Speeds higher than 40 MHz (up to 108 MHz) require Fast Read instructions: FAST\_READ, DOR, QOR, DIOR, and QIOR. The Fast Read instructions consist of a Fast Read opcode byte, three bytes of address, and a dummy/mode byte. The data is read out on the data output pin/pins.

The device allows burst mode reads. This enables read operations on consecutive addresses without issuing a new Read instruction. When the last address in memory is reached in burst mode, the address rolls over to 0x00000 and the device continues to read.

The SPI read cycle sequence is defined explicitly in the nvSRAM Read Write Instructions in [“SPI Functional Description”](#) on page 12.

### STORE Operation

STORE operation transfers the data from the SRAM to the nonvolatile cells. The device stores data using one of the three STORE operations: AutoStore, activated on device power-down (requires  $V_{CAP}$ ); Software STORE, activated by a  $\overline{STORE}$  instruction; and Hardware STORE, activated by the HSB pin. During the STORE cycle, the nonvolatile cell is first erased and then programmed. After a STORE cycle is initiated, read/write to the device is inhibited until the cycle is completed.

The  $\overline{HSB}$  signal or the WIP bit in Status Register can be monitored by the system to detect if a STORE cycle is in progress. The busy status of nvSRAM is indicated by HSB being pulled LOW or the WIP bit being set to '1'. To avoid unnecessary nonvolatile STOREs, AutoStore and Hardware STORE operations are ignored unless at least one SRAM write operation has taken place since the most recent STORE cycle. However, software initiated STORE cycles are performed regardless of whether a SRAM write operation has taken place.

### AutoStore Operation

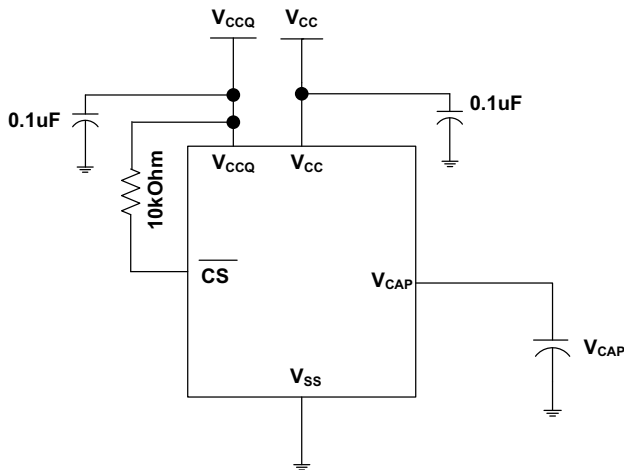
The AutoStore operation is a unique feature of nvSRAM, which automatically stores the SRAM data to the SONOS FLASH nonvolatile cells during power-down. This STORE makes use of an external capacitor ( $V_{CAP}$ ) and enables the device to safely STORE the data in the nonvolatile memory when power goes down.

During normal operation, the device draws current from  $V_{CC}$  to charge the capacitor connected to the  $V_{CAP}$  pin. When the voltage on the  $V_{CC}$  pin drops below  $V_{SWITCH}$  during power-down, the device inhibits all memory accesses to nvSRAM and automatically performs a STORE operation using the charge from the  $V_{CAP}$  capacitor. The AutoStore operation is not initiated if a write cycle has not been performed since last RECALL.

**Note** If a capacitor is not connected to the  $V_{CAP}$  pin, AutoStore must be disabled by issuing the AutoStore Disable instruction (Autostore Disable (ASDI) Instruction on page 44). If AutoStore is enabled without a capacitor on the  $V_{CAP}$  pin, the device attempts AutoStore without sufficient charge to complete the operation. This will corrupt the data stored in the memory array along with the serial number and Status Register. Updating them will be required to resume normal functionality.

Figure 2 shows the connection of the storage capacitor ( $V_{CAP}$ ) for AutoStore operation. Refer to on page 55 for the size of the  $V_{CAP}$

**Figure 2. AutoStore Mode**



**Software STORE Operation**

Software STORE allows an instruction-based STORE operation. It is initiated by executing a STORE instruction, irrespective of whether a write has been previously performed.

A STORE cycle takes  $t_{STORE}$  time to complete, during which all the memory accesses to nvSRAM are inhibited. The WIP bit of the Status Register or the HSB pin may be polled to find the Ready or Busy status. After the  $t_{STORE}$  cycle time is completed, the nvSRAM is ready for normal operations.

**Hardware STORE and HSB Pin Operation**

The  $\overline{HSB}$  pin in the device is a dual-purpose pin used to either initiate a STORE operation or to poll STORE/RECALL completion status. If a STORE or RECALL is not in progress, the  $\overline{HSB}$  pin can be driven low to initiate a Hardware STORE cycle.

Detecting a low on  $\overline{HSB}$ , nvSRAM will start a STORE operation after  $t_{DELAY}$  duration. A hardware STORE cycle is only possible if a SRAM write operation has been performed since the last STORE/RECALL cycle. This allows for optimizing the SONOS FLASH endurance cycles. All reads and writes to the memory are inhibited for  $t_{STORE}$  duration. The HSB pin also acts as an open drain driver (internal 100-kΩ weak pull-up resistor) that is internally driven LOW to indicate a busy condition when the STORE/RECALL is in progress.

**Note** After each Hardware and Software STORE operation,  $\overline{HSB}$  is driven HIGH for a short time ( $t_{HHHD}$ ) with standard output HIGH current and then remains HIGH by an internal 100-kΩ pull-up resistor.

**Note** For successful last data byte STORE, a hardware STORE should be initiated at least one clock cycle after the last data bit D0 is received.

**Note** It is recommended to perform a Hardware STORE only when the device is in Standby state. Execute-in-place (XIP) should be exited as well.

Upon completion of the STORE operation, the nvSRAM memory access is inhibited for  $t_{LZHSB}$  time after HSB pin returns HIGH. The HSB pin must be left unconnected if not used.

**RECALL Operation**

A RECALL operation transfers the data stored in the nonvolatile cells to the SRAM cells. A RECALL may be initiated in two ways: Hardware RECALL, initiated on power-up and Software RECALL, initiated by a SPI RECALL instruction.

Internally, RECALL is a two-step procedure. First, the SRAM data is cleared (set to '0'). Next, the nonvolatile information is transferred into the SRAM cells. All memory accesses are inhibited while a RECALL cycle is in progress. The RECALL operation does not alter the data in the nonvolatile elements.

**Hardware RECALL (Power-Up)**

During power-up, when  $V_{CC}$  crosses  $V_{SWITCH}$ , an automatic RECALL sequence is initiated, which transfers the content of nonvolatile cells to the SRAM cells.

A Power-Up RECALL cycle takes  $t_{FA}$  time to complete and the memory access is disabled during this time. The HSB pin is used to detect the ready status of the device.

**Software RECALL**

Software RECALL allows you to initiate a RECALL operation to restore the content of the nonvolatile memory to the SRAM. A Software RECALL is issued by using the RECALL instruction.

A Software RECALL takes  $t_{RECALL}$  time to complete during which all memory accesses to nvSRAM are inhibited.

**Disabling and Enabling AutoStore**

If the application does not require the AutoStore feature, it can be disabled by using the ASDI instruction. If this is done, the nvSRAM does not perform a STORE operation at power-down.

AutoStore can be re-enabled by using the ASEN instruction. However, ASEN and ASDI operations require a STORE operation to make them nonvolatile.

**Note** The device has AutoStore enabled and 0x00 written to all cells from the factory.

**Note** If AutoStore is disabled and  $V_{CAP}$  is not required, then the  $V_{CAP}$  pin must be left open. The  $V_{CAP}$  pin must never be connected to ground. The Power-Up RECALL operation cannot be disabled.

## Quad Serial Peripheral Interface

### SPI Overview

The SPI is a four-pin interface with Chip Select ( $\overline{CS}$ ), Serial Input (SI), Serial Output (SO), and Serial Clock (SCK) pins. The device provides serial access to the nvSRAM through the SPI interface. The SPI bus on the device can run at speed up to 108 MHz.

The SPI is a synchronous serial interface, which uses clock and data pins for memory access and supports multiple devices on the data bus. A device on the SPI bus is activated using the  $\overline{CS}$  pin.

The relationship between chip select, clock, and data is dictated by the SPI mode. This device supports SPI modes 0 and 3. In both these modes, data is clocked into the nvSRAM on the rising edge of SCK starting from the first rising edge after  $\overline{CS}$  goes active.

The SPI protocol is controlled by opcodes. These opcodes specify the commands from the bus master to the slave device. After  $\overline{CS}$  is activated, the first byte transferred from the bus master is the opcode. Following the opcode, any addresses and data are then transferred. The  $\overline{CS}$  must go inactive after an operation is complete and before a new opcode can be issued. The commonly used terms in the SPI protocol are described in the following sections.

#### SPI Master

The SPI master device controls the operations on an SPI bus. An SPI bus may have only one master with one or more slave devices. All the slaves share the same SPI bus lines and the master may select any of the slave devices with its own  $\overline{CS}$  pin. All the operations must be initiated by the master activating a slave device by pulling the  $\overline{CS}$  pin of the slave LOW. The master also generates the SCK and all the data transmission on SI and SO lines are synchronized with this clock.

#### SPI Slave

The SPI slave device is activated by the master through the Chip Select line. A slave device gets the SCK as an input from the SPI master and all the communication is synchronized with this clock. The SPI slave never initiates a communication on the SPI bus and acts on the instruction from the master.

The device operates as an SPI slave and may share the SPI bus with other SPI slave devices.

#### Chip Select ( $\overline{CS}$ )

For selecting any slave device, the master needs to pull down the corresponding  $\overline{CS}$  pin. Any instruction can be issued to a slave device only while the  $\overline{CS}$  pin is LOW. When the device is not selected, data through the SI pin is ignored and the serial output pin (SO) remains in a high-impedance state.

**Note** A new instruction must begin with the falling edge of  $\overline{CS}$ . Therefore, only one opcode can be issued for each active Chip Select cycle.

**Note** It is recommended to attach an external 10-k $\Omega$  pull-up resistor to  $V_{CCQ}$  on  $\overline{CS}$  pin.

#### Serial Clock (SCK)

The serial clock is generated by the SPI master and the communication is synchronized with this clock after  $\overline{CS}$  goes LOW.

The device enables SPI modes 0 and 3 for data communication. In both these modes, the inputs are latched by the slave device on the rising edge of SCK and outputs are issued on the falling edge. Therefore, the first rising edge of SCK signifies the arrival of the first bit (MSB) of SPI instruction on the SI pin. Further, all data inputs and outputs are synchronized with SCK.

#### Data Transmission - SI/SO

The SPI data bus consists of two lines, SI and SO, for serial data communication. The SI is also referred to as Master Out Slave In (MOSI) and SO is referred to as Master In Slave Out (MISO). The master issues instructions to the slave through the SI pin, while the slave responds through the SO pin. Multiple slave devices may share the SI and SO lines as described earlier.

The device has two separate pins for SI and SO, which can be connected with the master as shown in [Figure 3 on page 9](#).

This SI input signal is used to transfer data serially into the device. It receives opcode, addresses, and data to be programmed. Values are latched on the rising edge of serial SCK clock signal. SI becomes I/O0 - an input and output during Extended-SPI and DPI/QPI commands for receiving opcodes, addresses, and data to be written (values latched on rising edge of serial SCK clock signal) as well as shifting out data (on the falling edge of SCK).

The SO output signal is used to transfer data serially out of the device. Data is shifted out on the falling edge of the serial SCK clock signal. SO becomes I/O1 - an input and output during Extended-SPI and DPI/QPI commands for receiving opcodes, addresses, and data to be programmed (values latched on rising edge of serial SCK clock signal) as well as shifting out data (on the falling edge of SCK). SO has a Repeater/Bus-Hold circuit implemented.

#### Write-Protect ( $\overline{WP}$ )

In SPI and DSPI modes, the  $\overline{WP}$  pin when driven low protects against writes to the Status registers and all data bytes in the memory area that are protected by the Block Protect bits in the Status registers.

When  $\overline{WP}$  is driven Low, during a WRSR command and while the Status Register Write Disable (SRWD) bit of the Status Register is set to a 1, it is not possible to write to the Status and Configuration Registers. This prevents any alteration of the Block Protect (BP2, BP1, BP0) and TBPROT bits. As a consequence, all the data bytes in the memory area that are protected by the Block Protect and TBPROT bits, are protected against data modification if  $\overline{WP}$  is Low during a WRSR command.

The  $\overline{WP}$  function is not available while in the Quad transfer mode. The  $\overline{WP}$  function is replaced by I/O2 for input and output during these modes for receiving opcode, addresses, and data to be written/programmed as well as shifting out data.  $\overline{WP}$  has an internal pull-up resistor; and may be left unconnected in the host system if not used for Quad transfer mode.  $\overline{WP}$  has an internal 100-k $\Omega$  weak pull-up resistor in SPI mode.



**NC (I/O3)**

The NC (I/O3) pin functions as I/O3 for input and output during Quad transfer modes for receiving opcode, addresses, data to be written/programmed and shifting out data. NC (I/O3) has an internal pull-up resistor; and may be left unconnected in the host system if not used for Quad transfer mode. NC (I/O3) has an internal 100-kΩ weak pull-up resistor in SPI mode.

**Most Significant Bit (MSB)**

The SPI protocol requires that the first bit to be transmitted is the MSB. This is valid for both address and data transmission.

The 1-Mbit serial nvSRAM requires a 3-byte address for any read or write operation. However, because the address is only 17 bits, it implies that the first seven bits that are fed in are ignored by the device. Although these seven bits are ‘don’t care’, Cypress recommends that these bits are treated as 0s to enable seamless transition to higher memory densities.

**Serial Opcode**

After the slave device is selected with  $\overline{CS}$  going LOW, the first byte received is treated as the opcode for the intended operation. The device uses the standard opcodes for memory accesses. In addition to the memory accesses, it provides additional opcodes for the nvSRAM specific functions: STORE, RECALL, AutoStore Enable, and AutoStore Disable. Refer to [Table 2 on page 12](#) for details.

**Invalid Opcode**

If an invalid opcode is received, the opcode is ignored and the device ignores any additional serial data on the SI pin until the next falling edge of  $\overline{CS}$  and the SO pin remains tristated.

**Instruction**

The combination of the opcode, address, and mode/dummy cycles used to issue a command.

**Mode Bits**

Control bits that follow the address bits. The device uses control bits to enable execute-in-place (XIP). These bits are driven by the system controller when they are specified.

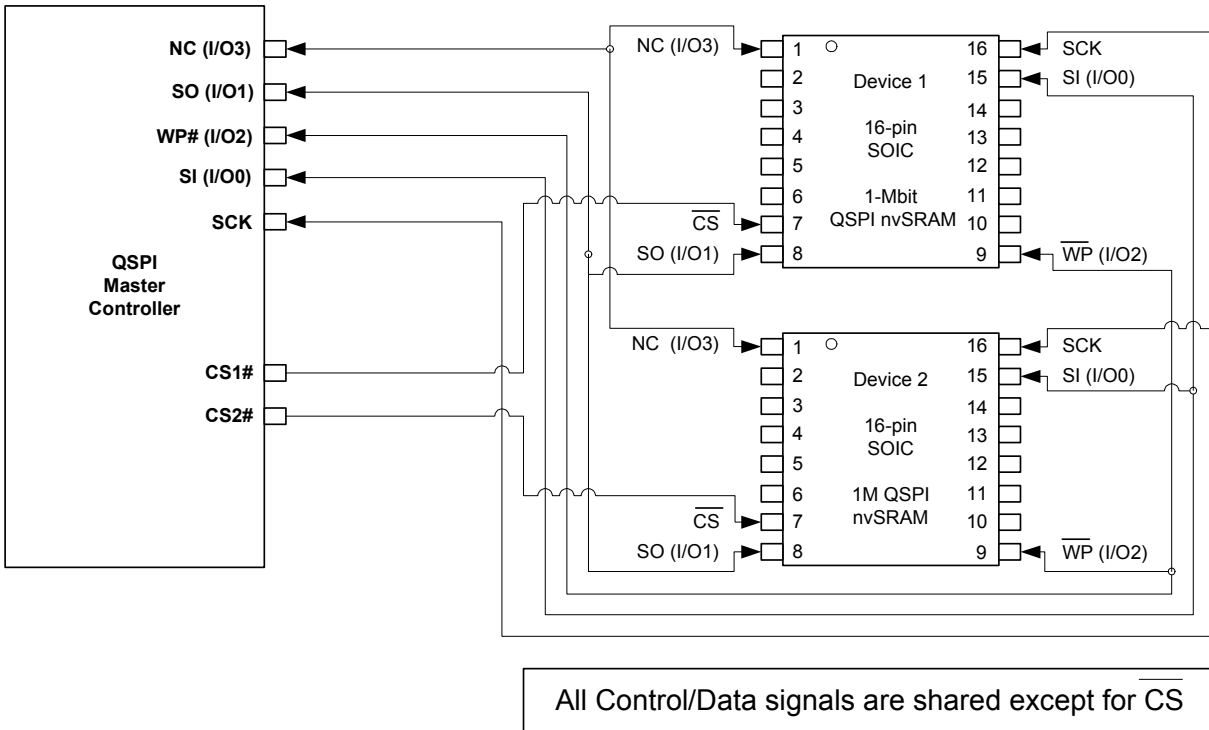
**Wait States**

Required dummy clock cycles after the address bits or optional mode bits.

**Status Register**

The device has one 8-bit Status Register. The bits in the Status Registers are used to configure the SPI bus. These bits are described in [Table 3](#) and [Table 4 on page 14](#).

**Figure 3. System Configuration Using Multiple 1-Mbit Quad SPI nvSRAM Devices**



### Dual and Quad I/O Modes

The device also has the capability to reconfigure the standard SPI pins to work in dual or quad I/O modes.

When the part is in the dual I/O mode, the SI pin and SO pin become I/O0 pin and I/O1 pin for either opcode, address, and data (Dual I/O mode) or both the address and data (Dual Addr/Data Mode) or just the data (Dual Data Mode).

When the part is in the quad I/O mode, the SI pin, SO pin, WP pin, and NC (I/O3) pin become I/O0 pin, I/O1 pin, I/O2 pin, and I/O3 pin for either opcode, address and data (Quad I/O Mode), or both the address and data (Quad Addr/Data Mode), or just the data (Quad Data Mode).

Table 1. I/O Modes

Protocol	Command Input	Address Input	Data Input/Output
SPI	SI	SI	SI/SO
DPI	I/O[1:0]	I/O[1:0]	I/O[1:0]
QPI	I/O[3:0]	I/O[3:0]	I/O[3:0]
Dual Data Mode (Dual Out)	I/O[0]	I/O[0]	I/O[1:0]
Dual Address/Data Mode (Dual I/O)	I/O[0]	I/O[1:0]	I/O[1:0]
Quad Data Mode (Quad Out)	I/O[0]	I/O[0]	I/O[3:0]
Quad Address/Data Mode (Quad I/O)	I/O[0]	I/O[3:0]	I/O[3:0]

For more details, refer to read and write timing diagrams later in the datasheet.

### SPI Modes

The device also has the capability to reconfigure. The device may be driven by a microcontroller with its SPI peripheral running in either of the following two modes:

- SPI Mode 0 (CPOL = 0, CPHA = 0)
- SPI Mode 3 (CPOL = 1, CPHA = 1)

For both these modes, the input data is latched in on the rising edge of SCK starting from the first rising edge after CS goes active. If the clock starts from a HIGH state (in mode 3), the first rising edge after the clock toggles, is considered. The output data is available on the falling edge of SCK.

The two SPI modes are shown in Figure 4 and Figure 5. The status of clock when the bus master is in standby state and not transferring data is:

- SCK remains at '0' for Mode 0
- SCK remains at '1' for Mode 3

The device detects the SPI mode from the status of SCK pin when the device is selected by bringing the CS pin LOW. If the SCK pin is LOW when the device is selected, SPI Mode 0 is assumed and if the SCK pin is HIGH, it works in SPI Mode 3.

Figure 4. SPI Mode 0

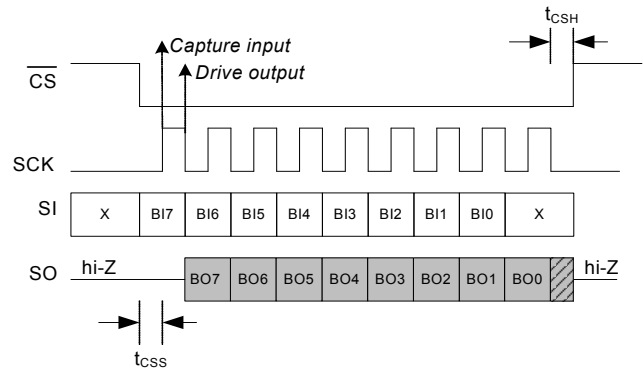
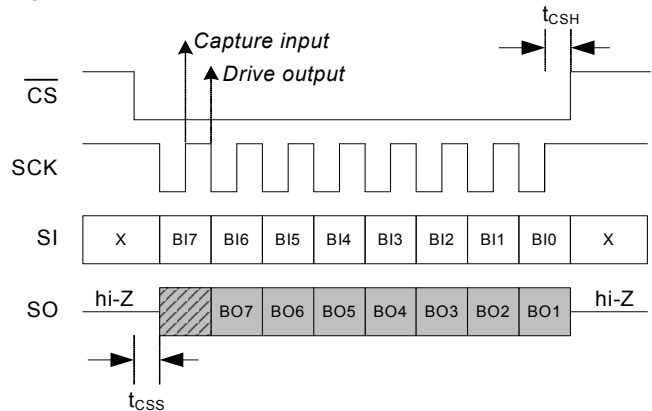


Figure 5. SPI Mode 3



## SPI Operating Features

### Power-Up

Power-up is defined as the condition when the power supply is turned on and  $V_{CC}$  crosses  $V_{SWITCH}$  voltage.

As described earlier, at power-up nvSRAM performs a Power-Up RECALL operation for  $t_{FA}$  duration during which all memory accesses are disabled. The HSB pin can be probed to check the Ready/Busy status of nvSRAM after power-up.

The following is the device status after power-up:

- SPI I/O Mode
- Pull-ups activated for  $\overline{HSB}$
- SO is tristated
- Standby power mode if  $\overline{CS}$  pin is high. Active power mode if  $\overline{CS}$  pin is LOW.
- Status Register state:
  - Write Enable bit is reset to '0'
  - SRWD not changed from previous STORE operation
  - SNL not changed from previous STORE operation
  - Block Protection bits are not changed from previous STORE operation
- $\overline{WP}$  and NC (I/O3) functionality as defined by Quad Data Width (QUAD) CR[1]. Pull-ups activated on  $\overline{WP}$  and NC (I/O3) if Quad Data width CR[1] is logic '0'.

### Power-Down

At power-down (continuous decay of  $V_{CC}$ ), when  $V_{CC}$  drops from the normal operating voltage and below the  $V_{SWITCH}$  threshold voltage, the device stops responding to any instruction sent to it.

If a write cycle is in progress and the last data bit D0 has been received when the power goes down, it is allowed  $t_{DELAY}$  time to complete the write. After this, all memory accesses are inhibited and a AutoStore operation is performed (AutoStore is not performed, if no write operations have been executed since the last RECALL cycle). This feature prevents inadvertent writes to nvSRAM from happening during power-down.

However, to completely avoid the possibility of inadvertent writes during power-down, ensure that the device is deselected and is in standby state, and the  $\overline{CS}$  follows the voltage applied on  $V_{CC}$ .

### Active Power Mode and Standby State

When  $\overline{CS}$  is LOW, the device is selected and is in the active power mode. The device consumes  $I_{CC}$  ( $I_{CC1} + I_{CCQ1}$ ) current, as specified in [on page 55](#). When  $\overline{CS}$  is HIGH, the device is deselected and the device goes into the standby state time, if a STORE or RECALL cycle is not in progress. If a STORE/RECALL cycle is in progress, the device goes into the standby state after the STORE or RECALL cycle is completed.

## SPI Functional Description

The device has an 8-bit instruction register. Instructions and their opcodes are listed in [Table 2](#). All instructions, addresses, and data are transferred with a HIGH to LOW CS transition. The SPI instructions along with WP, NC (I/O3), and HSB pins provide access to all the functions in nvSRAM.

**Table 2. Instruction Set**

Instruction Category	Instruction Name	Opcode	SPI	Dual Out	Quad Out	Dual I/O	Quad I/O	DPI	QPI	Max Frequency (MHz)
<b>Control</b>										
Write Disable	WRDI	04h	Yes	–	–	–	–	Yes	Yes	108
Write Enable	WREN	06h	Yes	–	–	–	–	Yes	Yes	108
Enable DPI	DPIEN	37h	Yes	–	–	–	–	–	Yes	108
Enable QPI	QPIEN	38h	Yes	–	–	–	–	Yes	–	108
Enable SPI	SPIEN	FFh	–	–	–	–	–	Yes	Yes	108
<b>Memory Read</b>										
Read	READ	03h	Yes	–	–	–	–	Yes	Yes	40
FastRead	FAST_READ	0Bh	Yes	–	–	–	–	Yes	Yes	108
Dual Out (Fast) Read	DOR	3Bh	–	Yes	–	–	–	–	–	108
Quad Out (Fast) Read	QOR	6Bh	–	–	Yes	–	–	–	–	108
Dual I/O (Fast) Read	DIOR	BBh	–	–	–	Yes	–	–	–	108
Quad I/O (Fast) Read	QIOR	EBh	–	–	–	–	Yes	–	–	108
<b>Memory Write</b>										
Write	WRITE	02h	Yes	–	–	–	–	Yes	Yes	108
Dual Input Write	DIW	A2h	–	Yes	–	–	–	–	–	108
Quad Input Write	QIW	32h	–	–	Yes	–	–	–	–	108
Dual I/O Write	DIOW	A1h	–	–	–	Yes	–	–	–	108
Quad I/O Write	QIOW	D2h	–	–	–	–	Yes	–	–	108
<b>SR Commands</b>										
Software Reset Enable	RSTEN	66h	Yes	–	–	–	–	Yes	Yes	108
Software Reset	RESET	99h	Yes	–	–	–	–	Yes	Yes	108
Read RTC	RDRTC	56h	Yes	–	–	–	–	Yes	Yes	40
Write RTC	WRRTC	55h	Yes	–	–	–	–	Yes	Yes	108
Fast Read RTC	FAST_RDRTC	57h	Yes	–	–	–	–	Yes	Yes	108
Enter Hibernate Mode	HIBEN	BAh	Yes	–	–	–	–	Yes	Yes	108
Enter Sleep Mode	SLEEP	B9h	Yes	–	–	–	–	Yes	Yes	108
Exit Sleep Mode	EXSLP	ABh	Yes	–	–	–	–	Yes	Yes	108
<b>Register Commands</b>										
Read Status Register	RDSR	05h	Yes	–	–	–	–	Yes	Yes	108

**Table 2. Instruction Set** (continued)

Instruction Category	Instruction Name	Opcode	SPI	Dual Out	Quad Out	Dual I/O	Quad I/O	DPI	QPI	Max Frequency (MHz)
Write Status Register	WRSR	01h	Yes	–	–	–	–	Yes	Yes	108
Read Configuration Register	RDCR	35h	Yes	–	–	–	–	Yes	Yes	108
Write Configuration Register	WRCR	87h	Yes	–	–	–	–	Yes	–	108
Read ID Register	RDID	9Fh	Yes	–	–	–	–	Yes	Yes	40
Fast Read ID Register	FAST_RDID	9Eh	Yes	–	–	–	–	Yes	Yes	108
Write Serial Number Register	WRSN	C2h	Yes	–	–	–	–	Yes	Yes	108
Read Serial Number Register	RDSN	C3h	Yes	–	–	–	–	Yes	Yes	40
Fast Read Serial Number Register	FAST_RDSN	C9h	Yes	–	–	–	–	Yes	Yes	108
<b>NV Specific Commands</b>										
STORE	STORE	8Ch	Yes	–	–	–	–	Yes	Yes	108
RECALL	RECALL	8Dh	Yes	–	–	–	–	Yes	Yes	108
Autostore Enable	ASEN	8Eh	Yes	–	–	–	–	Yes	Yes	108
Autostore Disable	ASDI	8Fh	Yes	–	–	–	–	Yes	Yes	108
<b>Mode Bits</b>										
Mode Bit (Set, Reset)	–	Axh, not Axh	Yes	–	–	–	–	Yes	Yes	–

Based on their functionality, the SPI instructions are divided into the following types:

■ Control instructions:

- Write-protection: WREN, WRDI instructions
- I/O modes: DPIEN, QPIEN, SPIEN

■ Memory Read instructions:

- Memory access: READ, FAST\_READ, DOR, QOR, DIOR, QIOR

■ Memory Write instructions:

- Memory access: WRITE, DIW, QIW, DIOW, QIOW

■ System Resources instructions:

- Software Reset: RSTEN, RESET
- Real Time Clock: RDRTC, WRRTC, FAST\_RDRTC
- Power modes: HIBEN, SLEEP, EXSLP

■ Register instructions:

- Configuration Register: RDCR, WRCR
- Status Register: RDSR, WRSR
- Identification: RDID, FAST\_RDID
- Serial Number: RDSN, WRSN, FAST\_RDSN

■ nvSRAM Special instructions:

- STORE: STORE

- RECALL: RECALL

- Enable/Disable: ASEN, ASDI

**Note** The instruction waveforms shown in the following sections do not incorporate the effects of pull-ups on WP (I/O2), NC (I/O3) and Repeater/Bus-Hold circuitry on SO.

**Note** Instruction Opcode C5h, 1Eh, C8h, CEh, CBh, CCh, CDh are Cypress reserved opcodes and change the configuration of the device. If any one of these opcodes are erroneously entered, a software reset (66h, 99h) is required to return the device back to correct configuration. Otherwise, the device will not behave correctly.

## Status Register

The device has one Status Register, which is listed in [Table 3](#) along with its bit descriptions. The bit format in the Status Register shows whether the bit is read only (R) or can be written to as well (W/R). The only exception to this is the serial number lock bit (SNL). The serial number can be written using the WRSN

instruction multiple times while SNL is still '0'. When set to '1', this bit prevents any modification to the serial number. This bit is factory-programmed to '0' and can only be written to once. After this bit is set to '1', it can never be cleared to '0'.

**Table 3. Status Register Format and Bit Definitions**

Bit	Field Name	Function	Type	R/W	Default State	Description
7	SRWD	Status Register Write Disable	NV	R/W	0	1 = Locks state of SR when $\overline{WP}$ is low by ignoring WRSR command 0 = No protection, even when $\overline{WP}$ is low
6	SNL	Serial Number Lock	OTP	R/W	0	Locks the Serial Number
5	TBPROT	Configures Start of Block	NV	R/W	0	1 = BP starts at bottom (Low address) 0 = BP starts at top (High address)
4	BP2	Block Protection	NV	R/W	0	Protects selected range of Block from Write, Program or Erase
3	BP1		NV	R/W	0	
2	BP0		NV	R/W	0	
1	WEL	Write Enable Latch	V	R	0	1 = Device accepts Write Registers (WRSR), Write, program or erase commands 0 = Device ignores Write Registers (WRSR), write, program or erase commands This bit is not affected by WRSR, only WREN and WRDI commands affect this bit
0	WIP	Work in Progress	V	R	0	1 = Device Busy, a Write Registers (WRSR), program, erase or other operation is in progress 0 = Ready Device is in standby state and can accept commands

### Status Register Write Disable (SRWD) SR[7]

Places the device in the Hardware Protected mode when this bit is set to '1' and the  $\overline{WP}$  input is driven LOW. In this mode, all the SRWD bits except WEL, become read-only bits and the Write Registers (WRSR) command is no longer accepted for execution. If  $\overline{WP}$  is HIGH, the SRWD bits may be changed by the WRSR command. If SRWD is '0',  $\overline{WP}$  has no effect and the SRWD bits may be changed by the WRSR command.

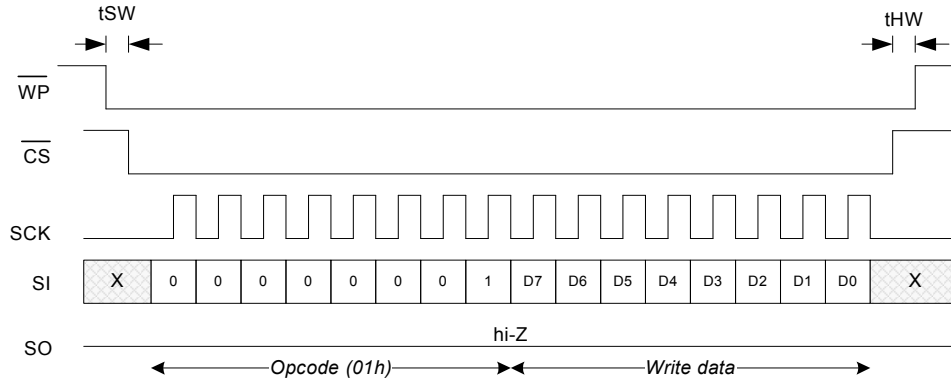
**Note**  $\overline{WP}$  internally defaults to logic '0', if Quad bit CR[1] in Configuration register is set. If SRWD is set to logic '1', protection cannot be changed till Quad bit CR[1] is reset to logic '0'.

**Table 4. SRWD,  $\overline{WP}$ , WEL and Protection**

SRWD	$\overline{WP}$	WEL	Protected Blocks	Unprotected Blocks	Status Register (Except WEL)
X	X	0	Protected	Protected	Protected
0	X	1	Protected	Writable	Writable
1	Low	1	Protected	Writable	Protected
1	High	1	Protected	Writable	Writable

**Note**  $\overline{WP}$  is sampled with respect to  $\overline{CS}$  during a write Status register instruction to determine if hardware protection is enabled. The timing waveforms are shown in [Figure 6](#).

Figure 6.  $\overline{WP}$  Timing w.r.t  $\overline{CS}$



**Serial Number Lock (SNL) SR[6]**

When set to '1', this bit prevents any modification to the serial number. This bit is factory programmed to '0' and can only be written to once. After this bit is set to '1', it can never be cleared to '0'.

**Top or Bottom Protection (TBPROT) CR[5]**

This bit defines the operation of the Block Protection bits BP2, BP1, and BP0. The desired state of TBPROT must be selected during the initial configuration of the device during system manufacture.

**Block Protection (BP2, BP1, BP0) SR[4:2]**

These bits define the memory array area to be software-protected against write commands. The BP bits are nonvolatile. When one or more of the BP bits is set to '1', the relevant memory area is protected against write, program, and erase.

The Block Protect bits (Status Register bits BP2, BP1, BP0) in combination with the TBPROT bit can be used to protect an address range of the memory array. The size of the range is determined by the value of the BP bits and the upper or lower starting point of the range is selected by the TBPROT bit of the status register.

Table 5. Upper Array Start of Protection (TBPROT = 0)

Status Register Content			Protection Fraction of Memory Array	Address Range
BP2	BP1	BP0		
0	0	0	None	None
0	0	1	Upper 64th	0x1F800 - 0x1FFFF
0	1	0	Upper 32nd	0x1F000 - 0x1FFFF
0	1	1	Upper 16th	0x1E000 - 0x1FFFF
1	0	0	Upper 8th	0x1C000 - 0x1FFFF
1	0	1	Upper 4th	0x18000 - 0x1FFFF
1	1	0	Upper Half	0x10000 - 0x1FFFF
1	1	1	All Sectors	0x00000 - 0x1FFFF

Table 6. Lower Array Start of Protection (TBPROT = 1)

Status Register Content			Protection Fraction of Memory Array	Address Range
BP2	BP1	BP0		
0	0	0	None	None
0	0	1	Lower 64th	0x00000 - 0x007FF
0	1	0	Lower 32nd	0x00000 - 0x00FFF
0	1	1	Lower 16th	0x00000 - 0x01FFF
1	0	0	Lower 8th	0x00000 - 0x03FFF
1	0	1	Lower 4th	0x00000 - 0x07FFF
1	1	0	Lower Half	0x00000 - 0x0FFFF
1	1	1	All Sectors	0x00000 - 0x1FFFF

### Write Enable (WEL) SR[1]

The WEL bit must be set to '1' to enable program, write, or erase operations as a means to provide protection against inadvertent changes to memory or register values. The Write Enable (WREN) command execution sets the Write Enable Latch to a '1' to allow any write commands to execute afterwards. The Write Disable (WRDI) command sets the Write Enable Latch to 0 to prevent all write commands from execution. The WEL bit is cleared to 0 at the end of any successful write to registers, STORE, RECALL, program or erase operation – note it is not cleared after write operations to memory macro. After a power-down/power-up sequence, hardware reset, or software reset, the Write Enable Latch is set to '0'. The WRSR command does not affect this bit.

**Note:** AutoStore, power up RECALL and Hardware STORE (HSB based) are not affected by WEL bit.

**Table 7. Instructions Requiring WEL Bit Set**

Instruction Description	Instruction Name	Opcode
<b>Memory Write</b>		
Write	WRITE	02h
Dual Input Write	DIW	A2h
Quad Input Write	QIW	32h
Dual I/O Write	DIOW	A1h
Quad I/O Write	QIOW	D2h
<b>Register Commands</b>		
Write Status Register	WRSR	01h
Write Configuration Register	WRCR	87h
Write Serial Number Register	WRSN	C2h
<b>NV Specific Commands</b>		
STORE	STORE	8Ch
RECALL	RECALL	8Dh
AutoStore Enable	ASEN	8Eh
AutoStore Disable	ASDI	8Fh

**Table 8. Configuration Register**

Bit	Field Name	Function	Type	R/W	Default State	Description
7	RFU	Reserved	–	R/W	0	Reserved for future use
6	RFU	Reserved	–	R/W	1	Reserved for future use
5	RFU	Reserved	–	–	0	Reserved for future use
4	RFU	Reserved	–	–	0	Reserved for future use
3	RFU	Reserved	–	–	0	Reserved for future use
2	RFU	Reserved	–	–	0	Reserved for future use
1	QUAD	Puts device in Quad Mode	NV	R/W	0	1 = Quad; 0 = Dual or Serial
0	RFU	Reserved	–	–	0	Reserved for future use

### Work In Progress (WIP) SR[0]

Indicates whether the device is performing a program, write, erase operation, or any other operation, during which a new operation command will be ignored. When the bit is set to '1', the device is busy performing a background operation. While WIP is '1', only Read Status (RDSR) command may be accepted. When the WIP bit is cleared to '0', no operation is in progress. This is a read-only bit.

All values written to SR are saved to nonvolatile memory only after a STORE operation. If AutoStore is disabled, any modifications to the Status Register must be secured by performing a software STORE operation.

Hardware Store will only commit Status register values to non-volatile memory if there is a write to the SRAM.

### Configuration Register

QPI nvSRAM has one Configuration register which is listed in [Table 8](#) along with its bit descriptions. The bit format in the Configuration register shows whether the bit is read only (R) or can be written to as well (W/R). The Configuration register controls interface functions.



#### *Quad Data Width (QUAD) CR[1]*

When set to '1', this bit switches the data width of the device to four bits i.e.  $\overline{WP}$  becomes I/O2 and NC (I/O3) becomes I/O3. The  $\overline{WP}$  input is not monitored for its normal function and is internally taken to be active. The commands for Serial, Dual Output, and Dual I/O Read still function normally but, there is no need to drive  $\overline{WP}$  input for those commands when switching between commands using different data path widths. The QUAD bit must be set to '1' when using QUAD Out Read, QUAD I/O Read, QUAD Input Write, QUAD I/O Write, and all QUAD SPI commands. The QUAD bit is non-volatile.

**Note** To set the Quad bit, 0x42 must be written to the Configuration register. Similarly, to reset the Quad bit, 0x40 must be written to the Configuration register. Any other data combination will change the configuration of the device and make it unusable.

**Note** When Quad bit CR[1] in Configuration register is set,  $\overline{WP}$  internally defaults to logic '0'.

**Note** The values written to Configuration Register are saved to nonvolatile memory only after a STORE operation. If AutoStore is disabled, any modifications to the Configuration Register must be secured by performing a Software STORE operation. Hardware Store will only commit Configuration register values to nonvolatile memory if there is a write to the SRAM.

## SPI Control Instructions

### Write Disable (WRDI) Instruction

The Write Disable instruction disables all writes by clearing the WEL bit to '0' to protect the device against inadvertent writes. This instruction is issued after the falling edge of CS followed by opcode for WRDI instruction. The WEL bit is cleared on the rising edge of CS.

Figure 7. WRDI Instruction in SPI Mode

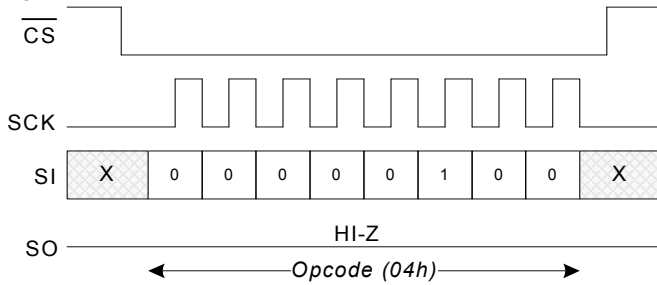


Figure 8. WRDI Instruction in DPI Mode

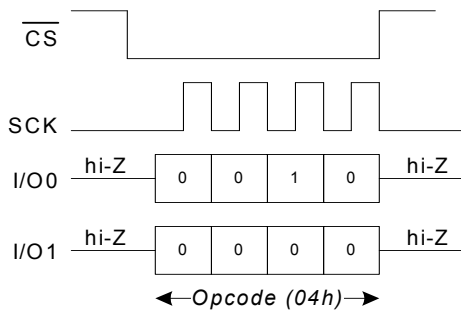
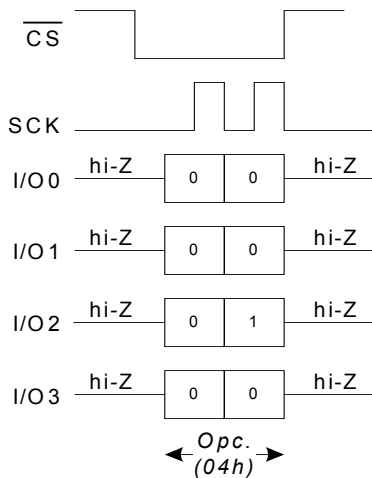


Figure 9. WRDI Instruction in QPI Mode



### Write Enable (WREN) Instruction

On power-up, the device is always in the Write Disable state. The write instructions and nvSRAM special instruction must therefore be preceded by a Write Enable instruction. If the device is not write enabled (WEL = '0'), it ignores the write instructions and returns to the standby state when CS is brought HIGH. This instruction is issued following the falling edge of CS and sets the WEL bit of the Status Register to '1'. The WEL bit defaults to '0' on power-up.

**Note** The WEL bit is cleared to 0 at the end of any successful write to registers, STORE, RECALL, ASEN, and ASDI operation. It is not cleared after write operations to memory macro.

Figure 10. WREN Instruction in SPI Mode

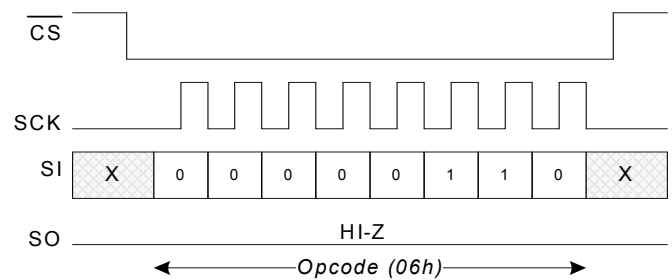


Figure 11. WREN Instruction in DPI Mode

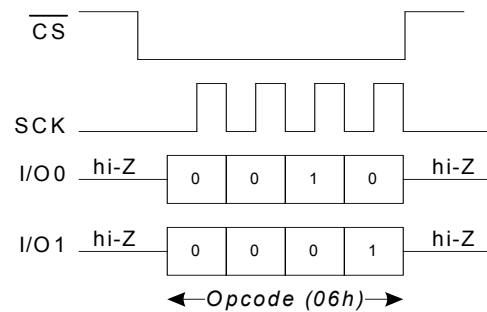
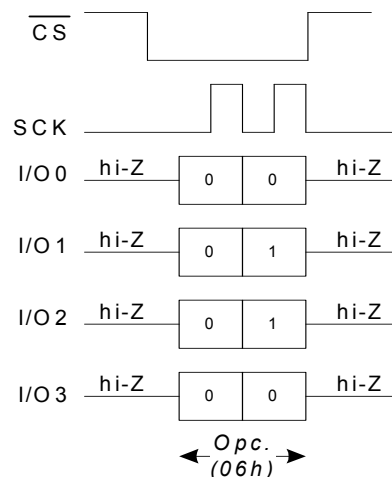


Figure 12. WREN Instruction in QPI Mode



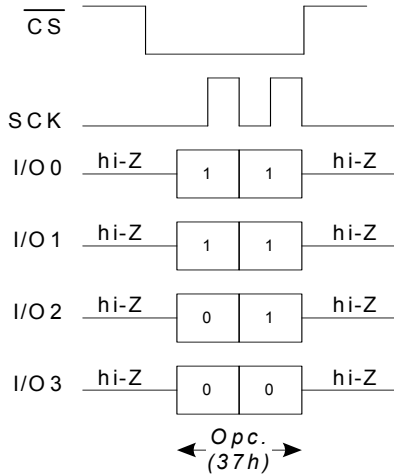
**Enable DPI (DPIEN) Instruction**

DPIEN enables the Dual I/O mode wherein opcode, address, mode bits, and data is sent over I/O0 and I/O1.

**Figure 13. Enable Dual I/O Instruction in SPI Mode**



**Figure 14. Enable Dual I/O Instruction in QPI Mode**

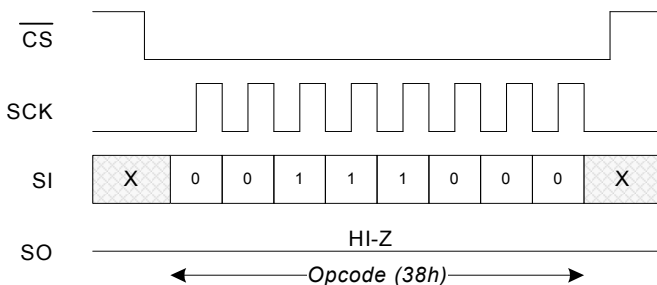


**Enable QPI (QPIEN) Instruction**

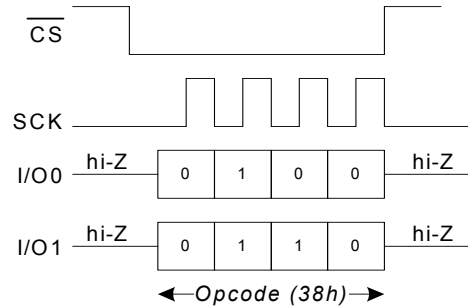
QPIEN enables QPI mode wherein opcode, address, dummy/mode bits and data is sent over I/O0, I/O1, I/O2, and I/O3. QPIEN instruction does not set the Quad bit CR[1] in Configuration register. WRCR instruction to set Quad bit CR[1] must therefore proceed QPIEN instruction.

**Note** Disabling QPI mode does not reset Quad bit CR[1].

**Figure 15. Enable Quad I/O instruction in SPI Mode**



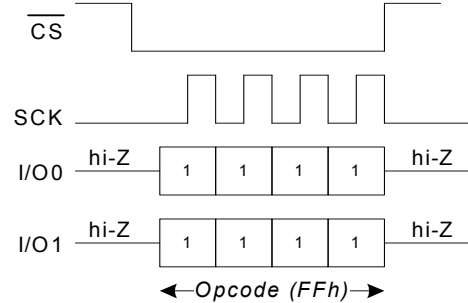
**Figure 16. Enable Quad I/O in DPI Mode**



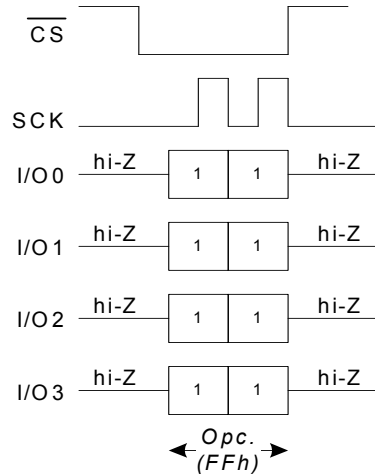
**Enable SPI (SPIEN) Instruction**

SPIEN disables Dual I/O or Quad I/O modes and returns the device in SPI mode. SPIEN instruction does not reset the Quad bit CR[1] in Configuration register.

**Figure 17. Enable SPI Instruction in DPI Mode**



**Figure 18. Enable SPI Instruction in QPI Mode**



## SPI Memory Read Instructions

Read instructions access the memory array. These instructions cannot be used while a STORE or RECALL cycle is in progress. A STORE cycle in progress is indicated by the WIP bit of the Status Register and the HSB pin.

### Read Instructions

The device performs the read operations when read instruction opcodes are given on the SI pin and provides the read output data on the SO pin for SPI mode or the I/O1, I/O0 pins for Dual I/O Mode or the I/O3, I/O2, I/O1, and I/O0 pins for Quad I/O Mode. After the CS pin is pulled LOW to select a device, the read opcode is entered followed by three bytes of address. The device contains a 17-bit address space for 1-Mbit configuration.

The most significant address byte contains A16 in bit 0 and other bits as 'don't care'. Address bits A15 to A0 are sent in the following two address bytes. After the last address bit is transmitted, the data (D7-D0) at the specific address is shifted out on the falling edge of SCK starting with D7. The reads can be performed in burst mode if CS is held LOW.

The device automatically increments to the next higher address after each byte of data is output. When the last data memory address (0x1FFFF) is reached, the address rolls over to 0x00000 and the device continues the read instruction. The read operation is terminated by driving CS HIGH at any time during data output.

**Note** The Read instruction operates up to maximum of 40-MHz frequency. In Dual and Quad I/O modes, dummy cycle is required after the address bytes. This allows the device to pre-fetch the first byte and start the pipeline flowing.

### READ Instruction

READ instruction can be used in SPI, Dual I/O (DPI) or Qua I/O (QPI) Modes. In SPI Mode, opcode and address bytes are transmitted through SI pin, one bit per clock cycle. At the falling edge of SCK of the last address cycle, the data (D7-D0) at the specific address is shifted out on SO pin one bit per clock cycle starting with D7.

In DPI Mode, opcode and address bytes are transmitted through I/O1 and I/O0 pins, two bits per clock cycle. At the falling edge of SCK after the last address cycle, the data (D7-D0) at the specific address is shifted out two bits per clock cycle starting with D7 on I/O1 and D6 on I/O0. In QPI Mode, opcode and address bytes are transmitted through I/O3, I/O2, I/O1, and I/O0 pins, four bits per clock cycle. At the falling edge of SCK of the last address cycle, data (D7-D0) at the specific address is shifted out four bits per clock cycle starting with D7 on I/O3, D6 on I/O2, D5 on I/O1, and D4 on I/O0.

Figure 19. READ Instruction in SPI Mode

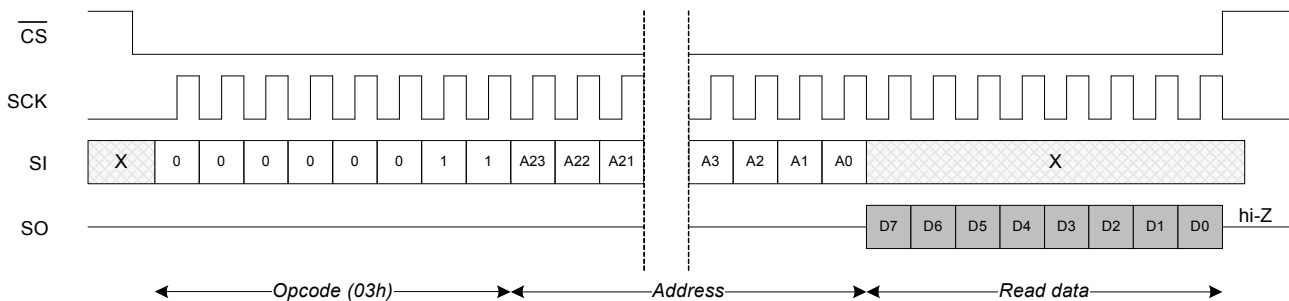


Figure 20. Burst Mode READ Instruction in SPI Mode

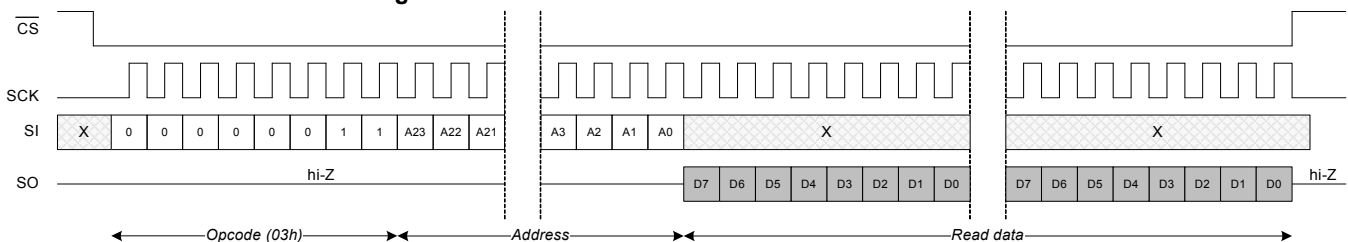


Figure 21. READ Instruction in DPI Mode

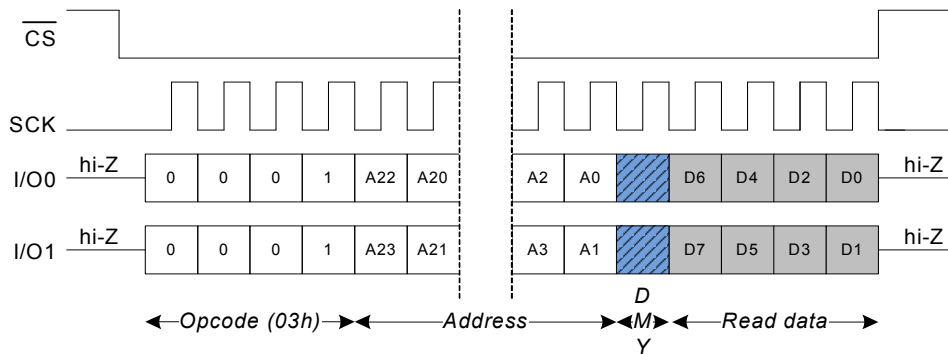
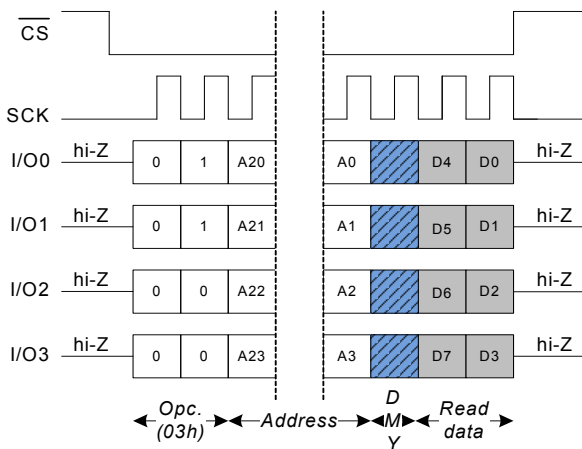


Figure 22. READ Instruction in QPI Mode



byte specified can be at any location. The device automatically increments to the next higher address after each byte of data is output. The entire memory array can therefore be read with a single fast read instruction. When the highest address in the memory array is reached, the address counter rolls over to starting address 0x00000 and allows the read sequence to continue indefinitely. The fast read instructions are terminated by driving CS HIGH at any time during data output.

**Note** These instructions operate up to maximum of 108-MHz SPI frequency.

*FAST\_READ Instruction*

FAST\_READ instruction can be used in SPI, Dual I/O (DPI) or Quad I/O (QPI) Modes. In SPI Mode, opcode, address and mode byte are transmitted through SI pin, one bit per clock cycle. At the falling edge of SCK of the last mode byte cycle, the data (D7-D0) from the specific address is shifted out on SO pin, one bit per clock cycle starting with D7. In DPI Mode, opcode, address and mode byte are transmitted through I/O1 and I/O0 pins, two bits per clock cycle. At the falling edge of the last mode cycle, the data (D7-D0) from the specific address is shifted out two bits per clock cycle starting with D7 on I/O1 and D6 on I/O0. In QPI Mode, opcode, and address bytes are transmitted through I/O3, I/O2, I/O1, and I/O0 pins, four bits per clock cycle. At the falling edge of SCK of the last mode cycle, the data (D7-D0) from the specific address is shifted out, four bits per clock cycle starting with D7 on I/O3, D6 on I/O2, D5 on I/O1, and D4 on I/O0.

**Note:** Quad bit CR[1] must be logic '1' before executing the READ instruction in QPI mode.

**Fast Read Instructions**

The fast read instructions allow you to read memory at SPI frequency up to 108 MHz (max). The instruction is similar to the normal read instruction with the addition of a wait state in all I/O configurations; a mode byte must be sent after the address and before the first data is sent out. This allows the device to pre-fetch the first byte and start the pipeline flowing. The host system must first select the device by driving CS LOW, followed by the 3 address bytes and then a mode byte. At the next falling edge of the SCK, data from the specific address is shifted out on the SO pin for SPI Mode or the I/O1, I/O0 pins for Dual I/O Mode or the I/O3, I/O2, I/O1, and I/O0 pins for Quad I/O Mode. The first

Figure 23. FAST\_READ Instruction in SPI Mode

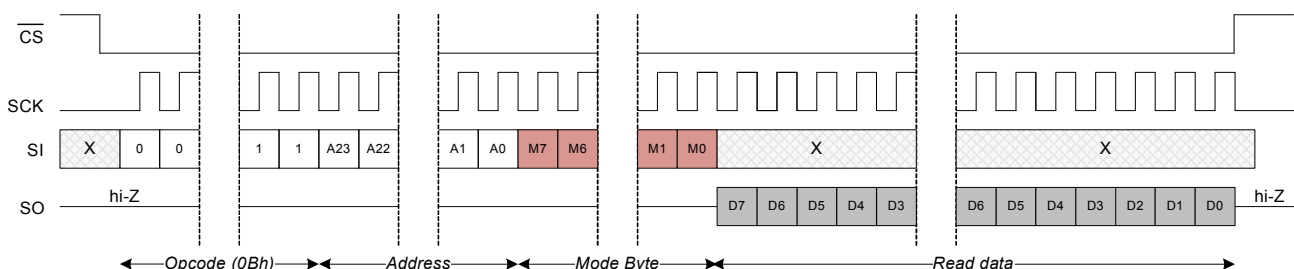


Figure 24. FAST\_READ Instruction in DPI Mode

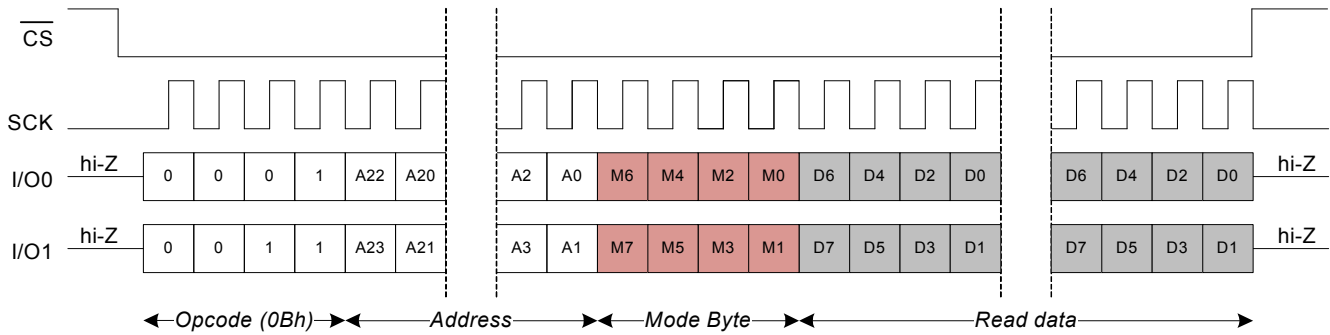
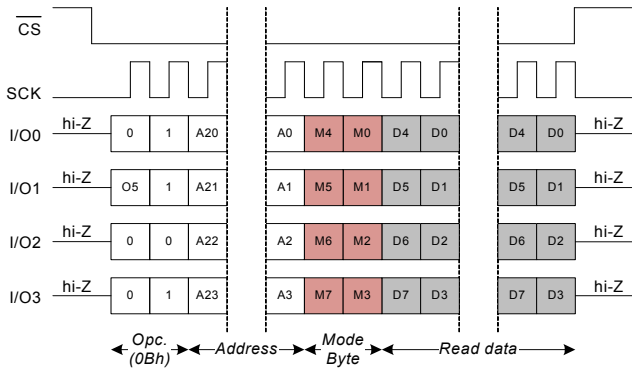


Figure 25. FAST\_READ Instruction in QPI Mode



DOR Instruction

DOR instruction is used in Dual Data Mode, which is part of Extended SPI Read commands. In Dual Data Mode, opcode, address and mode byte are transmitted through SI pin, one bit per clock cycle. At the falling edge of SCK of the last mode cycle, the pins are reconfigured as SO becoming I/O1, and SI becoming I/O0. The data (D7-D0) from the specified address is shifted out on I/O1, and I/O0 pins two bits per clock cycle starting with D7 on I/O1, and D6 on I/O0.

QOR Instruction

QOR instruction is used in Quad Data Mode, which is part of Extended SPI Read commands. In Quad Data Mode, opcode, address and mode byte are transmitted through SI pin, one bit per clock cycle. At the falling edge of SCK of the last mode cycle, the pins are reconfigured as NC becoming I/O3, WP becoming I/O2, SO becoming I/O1, and SI becoming I/O0. The data (D7-D0) from the specified address is shifted out on I/O3, I/O2, I/O1, and I/O0 pins four bits per clock cycle starting with D7 on I/O3 and D6 on I/O2, D5 on I/O1, and D4 on I/O0.

**Note** Quad bit CR[1] must be logic '1' before executing the QOR instruction.

Figure 26. DOR Instruction

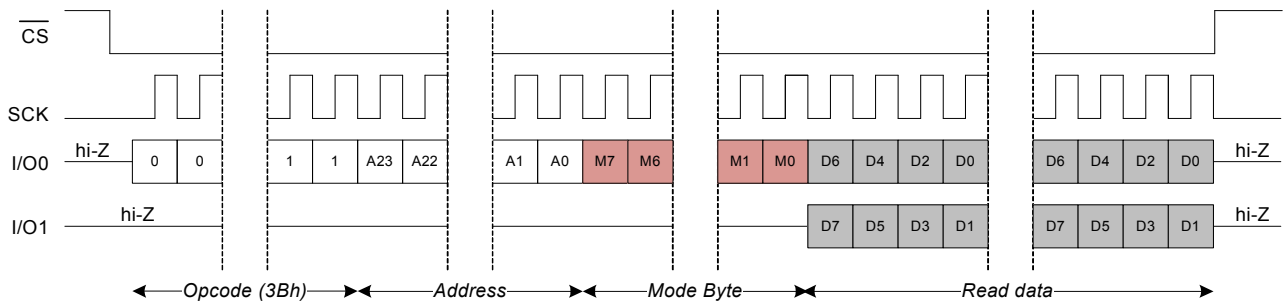
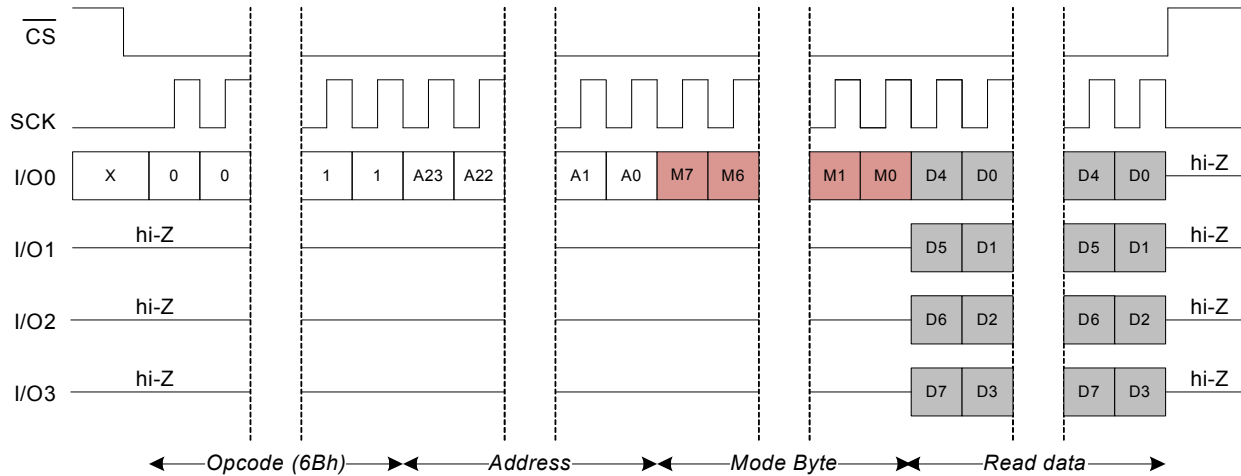


Figure 27. QOR Instruction

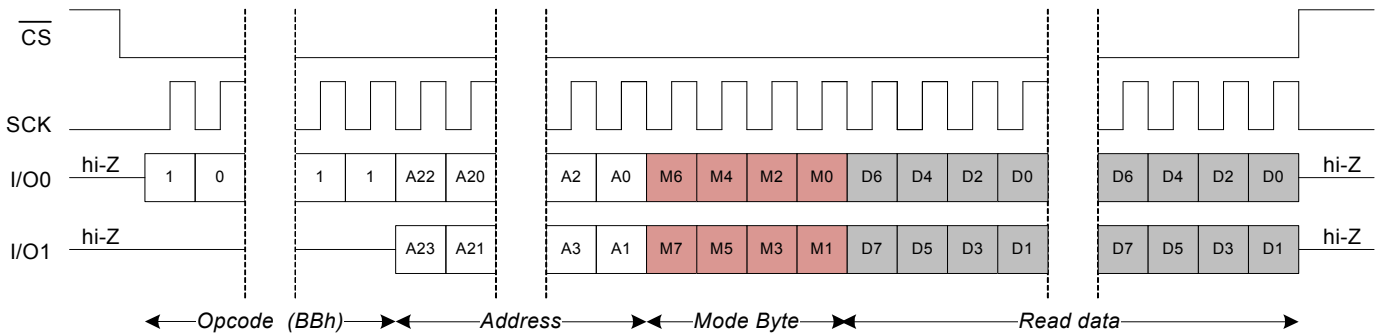


**DIOR Instruction**

DIOR instruction is used in Dual Addr/Data Mode, which is part of Extended SPI Read commands. In Dual Addr/Data Mode, opcode is transmitted through SI pin, one bit per clock cycle. After the last bit of the opcode, the pins are reconfigured as SO becoming I/O1, and SI becoming I/O0. The address is then

transmitted into the part through I/O1 and I/O0 pins, 2 bits per clock cycle, starting with A23 on I/O1 and A22 on I/O0, until three bytes worth of address is input. The data (D7-D0) at the specific address is shifted out on I/O1, and I/O0 pins two bits per clock cycle starting with D7 on I/O1, and D6 on I/O0.

Figure 28. DIOR Instruction

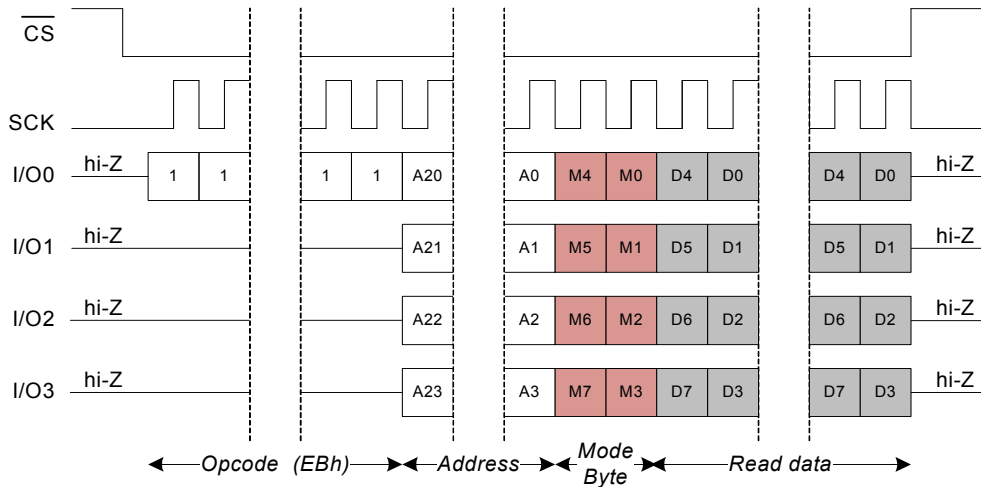


**QIOR Instruction**

QIOR instruction is used in Quad Addr/Data Mode, which is part of Extended SPI Read commands. In Quad Addr/Data Mode, opcode is transmitted through SI pin, one bit per clock cycle. After the last bit of the opcode, the pins are reconfigured as NC becoming I/O3, WP becoming I/O2, SO becoming I/O1, and SI becoming I/O0. The address is then transmitted into the part through I/O3, I/O2, I/O1 and I/O0 pins, 4 bits per clock cycle, starting with A23 on I/O3, A22 in I/O2, A21 on I/O1 and A20 on I/O0, until three bytes worth of address is input. The data (D7-D0) at the specific address is shifted out on I/O3, I/O2, I/O1, and I/O0 pins four bits per clock cycle starting with D7 on I/O3 and D6 on I/O2, D5 on I/O1, and D4 on I/O0.

**Note** Quad bit CR[1] must be logic '1' before executing the QIOR instruction.

Figure 29. QIOR Instruction



**Write Instructions**

The device performs the write operations when write instruction opcodes along with write data are given on the SI pin for SPI Mode or the I/O1, I/O0 pins for Dual I/O Mode or the I/O3, I/O2, I/O1, and I/O0 pins for Quad I/O Mode. To perform a write operation, if the device is write disabled, then the device must be first write enabled through the WREN instruction. When the writes are enabled (WEL = '1'), WRITE instruction is issued after the falling edge of CS. nvSRAM enables writes to be performed in bursts which can be used to write consecutive addresses without issuing a new Write instruction. If only one byte is to be written, the CS pin must be driven HIGH after the D0 (LSB of data) is transmitted. However, if more bytes are to be written, CS pin must be held LOW and the address is incremented automatically. The data bytes on the input pin(s) are written in successive addresses. When the last data memory address (0x1FFFF) is reached, the address rolls over to 0x00000 and the device continues to write.

**Note** The WEL bit in the Status Register does not reset to '0' on completion of a Write sequence to the memory array.

**Note** When a burst write reaches a protected block address, it continues incrementing the address into the protected space but does not write any data to the protected memory. If the address rolls over and takes the burst write to unprotected space, it resumes writes. The same operation is true if a burst write is initiated within a write-protected block.

**Note** These instructions operate up to a maximum of 108-MHz frequency.

After the CS pin is pulled LOW to select a device, the write opcode is followed by three bytes of address. The device has a 17-bit address space for 1-Mbit configuration. The most significant address byte contains A16 in bit 0 and the remaining bits as 'don't care'. Address bits A15 to A0 are sent in the following two address bytes. Immediately after the last address bit is transmitted, the data (D7-D0) is transmitted through the input line(s). This command can be used in SPI, DPI or QPI Modes.

*WRITE Instruction*

WRITE instruction can be used in SPI, DPI, or QPI Modes. In SPI Mode, opcode, address bytes and data bytes are transmitted through SI pin, one bit per clock cycle starting with D7. In DPI Mode, opcode, address bytes and data bytes are transmitted through I/O1 and I/O pins, two bits per clock cycle starting with D7 on I/O1 and D6 on I/O0. In QPI Mode, opcode, address bytes, and data bytes are transmitted through I/O3, I/O2, I/O1, and I/O0 pins, four bits per clock cycle starting with D7 on I/O3, D6 on I/O2, D5 on I/O1, and D4 on I/O0.

Figure 30. WRITE Instruction in SPI Mode





Figure 31. Burst WRITE Instruction in SPI Mode

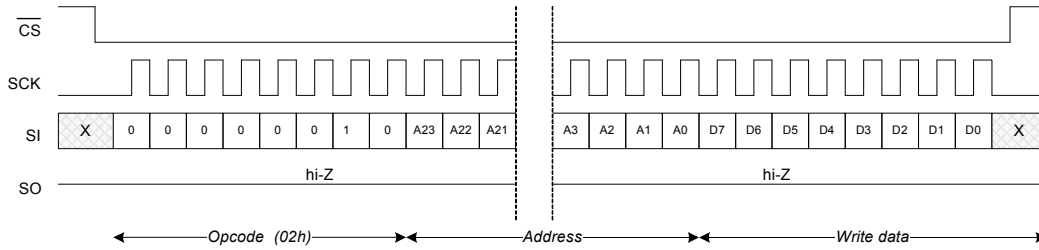


Figure 32. WRITE Instruction in DPI Mode

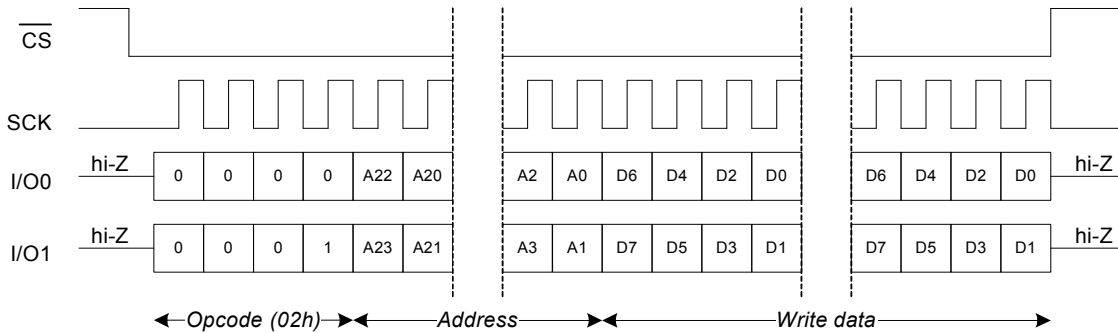
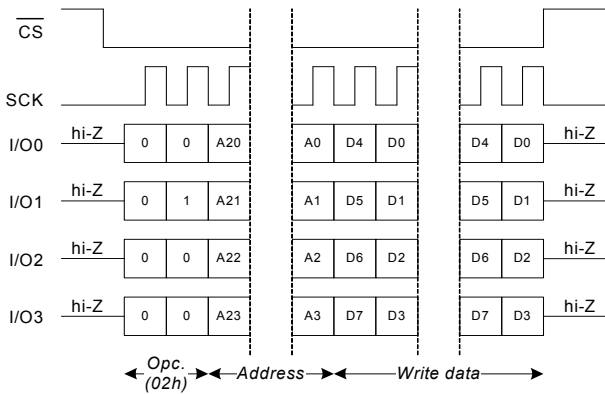


Figure 33. WRITE Instruction in QPI Mode

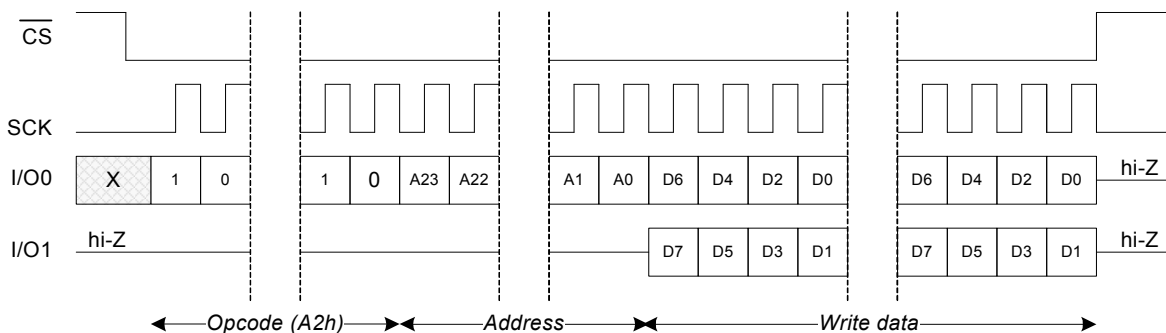


*DIW Instruction*

DIW Instruction can be used in Dual Data Mode, which is part of Extended SPI Write commands. In Dual Data Mode, opcode, and address bytes are transmitted through SI pin, one bit per clock cycle. Immediately after the last address bit is transmitted, the pins are reconfigured as SO becoming I/O1, and SI becoming I/O0, and the data (D7-D0) is transmitted into the I/O1, and I/O0 pins, 2 bits per clock cycle, starting with D7 on I/O1 and D6 on I/O0.

**Note** Quad bit CR[1] must be logic '1' before executing the WRITE instruction in QPI mode.

Figure 34. DIW Instruction



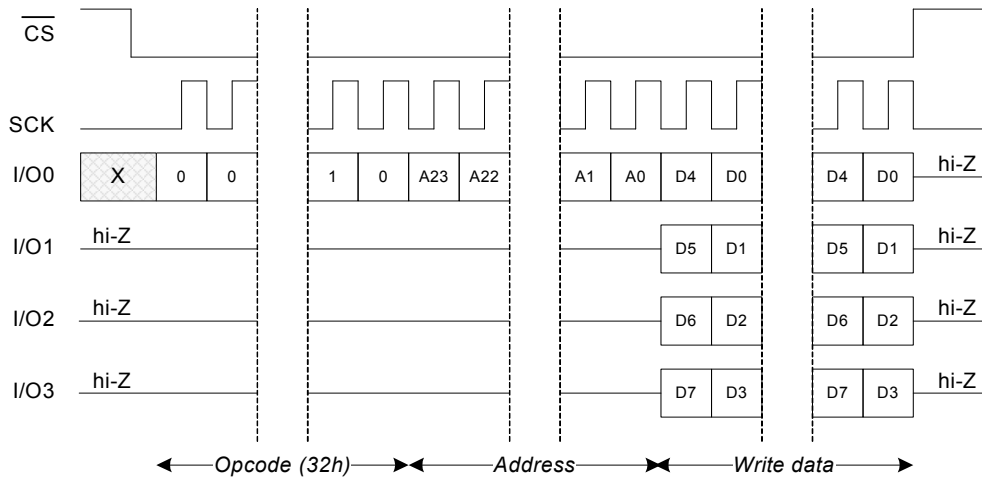
**QIW Instructions**

QIW Instruction can be used in Quad Data Mode, which is part of Extended SPI Write commands. In Quad Data Mode, opcode, and address bytes are transmitted through SI pin, one bit per clock cycle. Immediately after the last address bit is transmitted, the pins are reconfigured as NC becoming I/O3, WP becoming

I/O2, SO becoming I/O1, and SI becoming I/O0, and the data (D7-D0) is transmitted into the I/O3 I/O2, I/O1, and I/O0 pins, 4 bits per clock cycle, starting with D7 on I/O3 and D6 on I/O2, D5 on I/O1, and D4 on I/O0.

**Note** Quad bit CR[1] must be logic '1' before executing the QIW instruction.

**Figure 35. QIW Instruction**

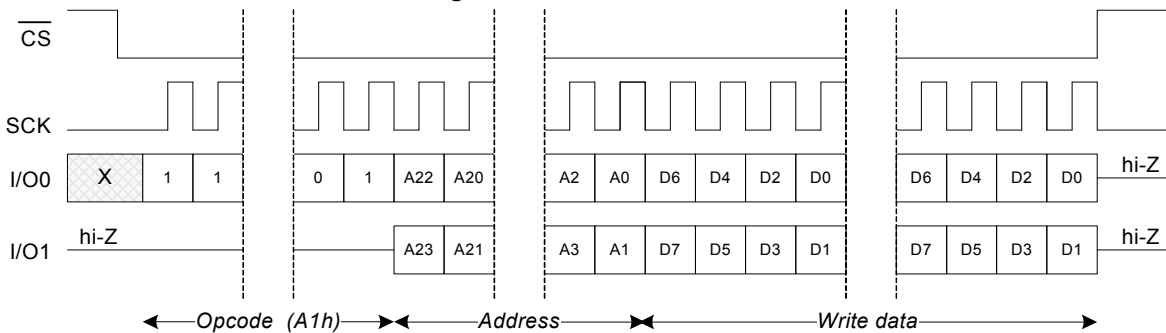


**DLOW Instruction**

DLOW Instruction can be used in Dual Addr/Data Mode, which is part of Extended SPI Write commands. In Dual Addr/Data Mode, opcode is transmitted through SI pin, one bit per clock cycle. Immediately after the last opcode bit is transmitted, the pins are reconfigured as SO becoming I/O1, and SI becoming I/O0, and

the address is transmitted into the part through I/O1 and I/O0 pins, 2 bits per clock cycle, starting with A23 on I/O1, A22 on I/O0, until three bytes worth of address is input. After the last address bits are transmitted, the data (D7-D0) is transmitted into the part through I/O1 and I/O0 two bits per clock cycle starting with D7 on I/O1 and D6 on I/O0.

**Figure 36. DLOW Instruction**

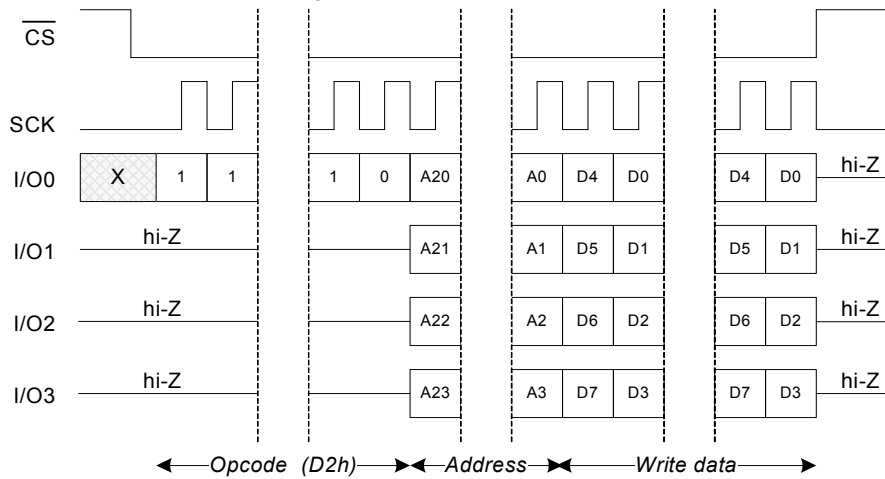


**QIOW Instruction**

QIOW instruction can be used in Quad Addr/Data Mode, which is part of Extended SPI Write commands. In Quad Addr/Data Mode, opcode is transmitted through SI pin, one bit per clock cycle. Immediately after the last opcode bit is transmitted, the pins are reconfigured as NC becoming I/O3, WP becoming I/O2, SO becoming I/O1, and SI becoming I/O0, and the address is transmitted into the part through I/O3, I/O2, I/O1 and I/O0 pins, 4 bits per clock cycle, starting with A23 on I/O3, A22 in I/O2, A21 on I/O1, and A20 on I/O0, until three bytes worth of address is input. After the last address bits are transmitted, the data (D7-D0) is transmitted into the part through I/O3, I/O2, I/O1 and I/O0 four bits per clock cycle starting with D7 on I/O3, D6 on I/O2, D5 on I/O1, and D4 on I/O0.

**Note** Quad bit CR[1] must be logic '1' before executing the QIOW instruction.

Figure 37. QIOW Instruction



Execute-In-Place (XIP)

Execute-in-place (XIP) mode allows the memory to perform a series of reads beginning at different addresses without having to load the command code for every read. This improves random access time and eliminates the need to shadow code onto RAM for fast execution. The read commands supported in XIP mode are FAST\_READ (in SPI, DPI, and QPI mode), DOR, DIOR, QOR and QIOR.

XIP mode for these commands is Set or Reset by entering the Mode bits. The upper nibble (bits 7-4) of the Mode bits control the length of the next afore mentioned read command through the inclusion or exclusion of the first byte instruction code. The lower nibble (bits 3-0) of the Mode bits are “don't care” (“x”) and

may be high impedance – it is often used by the microcontrollers to turn the bus around for read data. If the Mode bits is equal to Axh, then the device is set to be/remain in read Mode and the next address can be entered without the opcode, as shown in figure below; thus, eliminating some cycles for the opcode sequence. If the Mode bits is not equal to Axh, then the XIP mode is reset and the device expects an opcode after the end of the current transaction.

XIP can be entered or exited during these commands at any time and in any sequence. If it is necessary to perform another operation, not supported by XIP, such as a write, then XIP must be exited before the new command code is entered for the desired operation.

Figure 38. XIP for SPI Mode and FAST\_READ Instruction (0Bh)

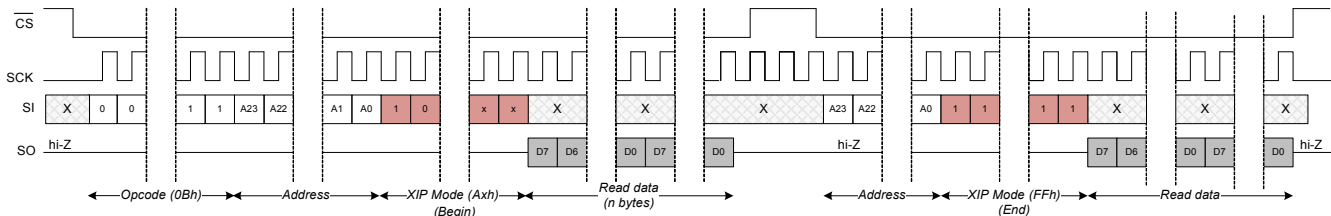
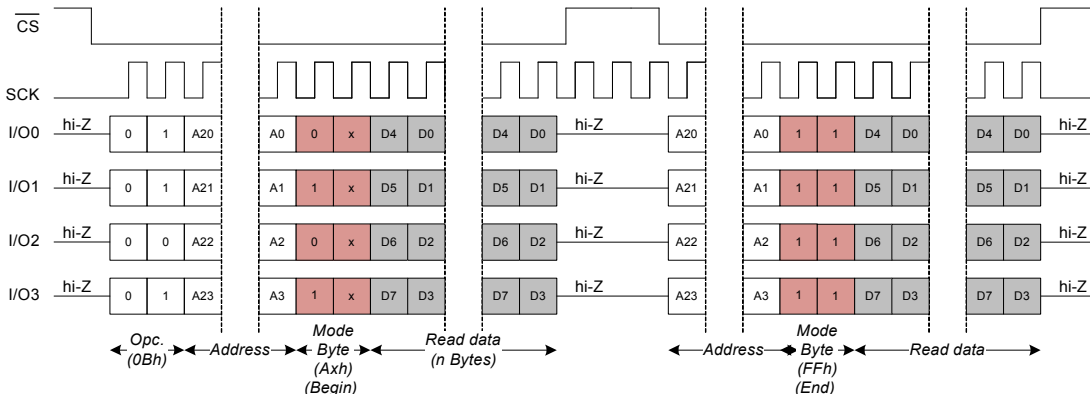


Figure 39. XIP for QPI Mode and FAST\_READ Instruction (0Bh)



## System Resources Instructions

### Software Reset (RESET) Instruction

RESET instruction resets the whole device and makes it ready to receive commands. The I/O mode is configured to SPI. All nonvolatile registers or nonvolatile register bits maintain their values. All volatile registers or volatile register bits default to logic '0'. It takes  $t_{RESET}$  time to complete. No STORE/RECALL operations are performed. To initiate the software reset process, the reset enable (RSTEN) instruction is required. This ensures protection against any inadvertent resets. Thus software reset is a sequence of two commands.

**Note** Any command other than RESET following the RSTEN command, will clear the reset enable condition and prevent a later RESET command from being recognized.

**Note** If WIP (SR[0]) bit is high and the RSTEN/RESET instruction is entered, the device ignores the RSTEN/RESET instruction.

**Note** The functionalities of  $\overline{WP}$  and  $\overline{NC}$  (I/O3) are controlled by the Quad bit CR[1] in Configuration register. If Quad bit is set to logic '1',  $\overline{WP}$  and  $\overline{NC}$  (I/O3) are configured as I/O2 and I/O3 respectively. Otherwise,  $\overline{WP}$  and  $\overline{NC}$  (I/O3) functionality is configured.

Table 9 summarizes the device's state after software reset.

Table 9. Software Reset State

State 1	State 2	State 3	I/O Mode & Register Bits
STANDBY	Software RESET	STANDBY	I/O Mode: SPI SRWD SR[7]: Same as State 1 SNL SR[6]: Same as State 1 TBPROT SR[5]: Same as State 1 BP2 SR[4]: Same as State 1 BP1 SR[3]: Same as State 1 BP0 SR[2]: Same as State 1 WEL SR[1]: 0 WIP SR[0]: 0 QUAD CR[1]: Same as State 1

Figure 40. RESET Instruction in SPI Mode

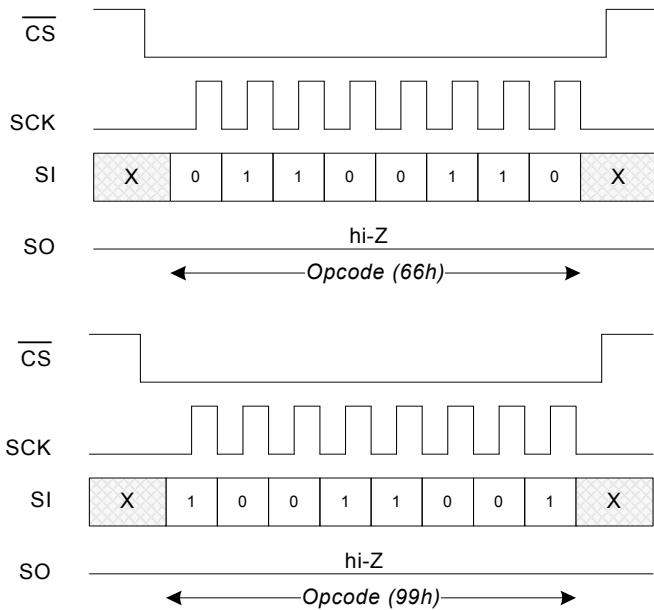


Figure 41. RESET Instruction in DPI Mode

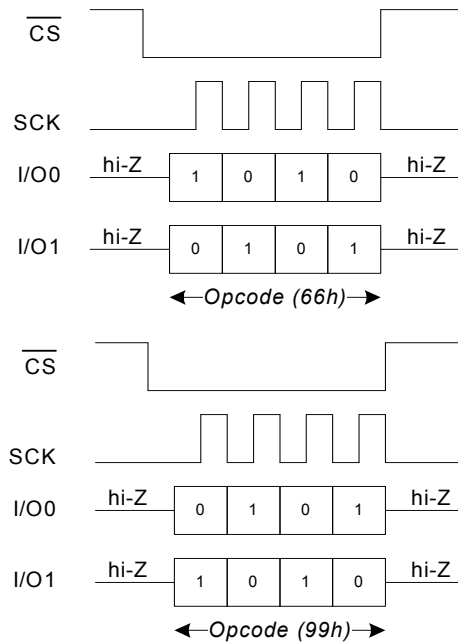
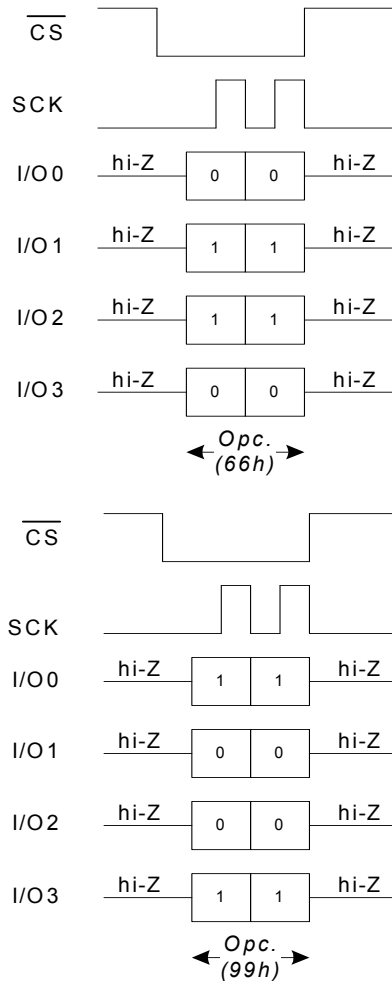


Figure 42. RESET Instruction in QPI Mode



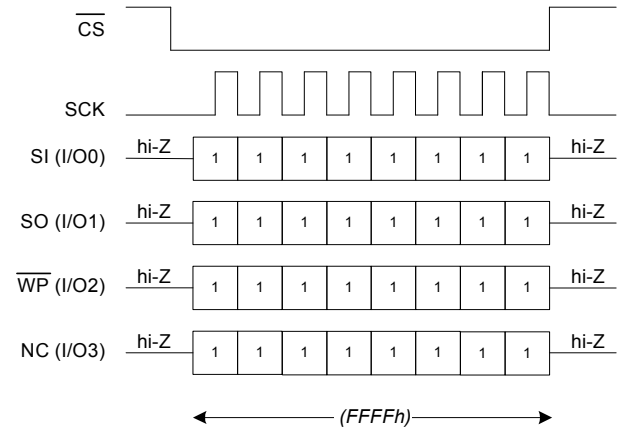
**Note** Quad bit CR[1] must be logic '1' before executing RSTEN/RESET instructions in QPI mode.

**Default Recovery Instruction**

The device provides a default recovery mode where the device is brought back to SPI mode. A logic high on all I/Os (I/O3, I/O2, I/O1, I/O0) with eight SCLKs brings the device into a known mode (SPI) so that the host can communicate to the device if the starting mode is unknown.

**Note** The functionalities of  $\overline{WP}$  and NC (I/O3) are controlled by the Quad bit CR[1] in configuration register. If Quad bit is set to logic '1',  $\overline{WP}$  and NC (I/O3) are configured as I/O2 and I/O3 respectively. Otherwise,  $\overline{WP}$  and NC (I/O3) functionality is configured.

Figure 43. Default Recovery Instruction



**Read Real Time Clock (RDRTC) Instruction**

Read RTC (RDRTC) instruction allows you to read the contents of RTC registers at SPI frequency up to 40 MHz. In SPI mode, after the CS line is pulled LOW to select a device, the RDRTC opcode is transmitted through the SI line followed by eight address bits for selecting the register. The data (D7–D0) at the specified address is then shifted out onto the SO line. RDRTC also allows burst mode read operation. When reading multiple bytes from RTC registers, the address rolls over to 0x00 after the last RTC register address (0x0F) is reached. DPI and QPI operations are similar to SPI except in DPI mode, I/O1, I/O0 pins are used whereas in QPI mode, I/O3, I/O2, I/O1, and I/O0 pins are used. The 'R' bit in RTC flags register must be set to '1' before reading RTC time keeping registers to avoid reading transitional data. Modifying the RTC flag registers requires a Write RTC cycle. The R bit must be cleared to '0' after completion of the read operation. The easiest way to read RTC registers is to perform RDRTC in burst mode. The read may start from the first RTC register (0x00) and the CS must be held LOW to allow the data from all 16 RTC registers to be transmitted through the SO pin.

**Note** After a RTC structure access, the RTC address is updated by incrementing it by '1'. As a result, an update wraps around in the RTC structure: an access to the last Byte in the RTC structure (RTC address '15') is followed by an access to the first Byte (RTC address '0').

Figure 44. RDRTC Instruction in SPI Mode

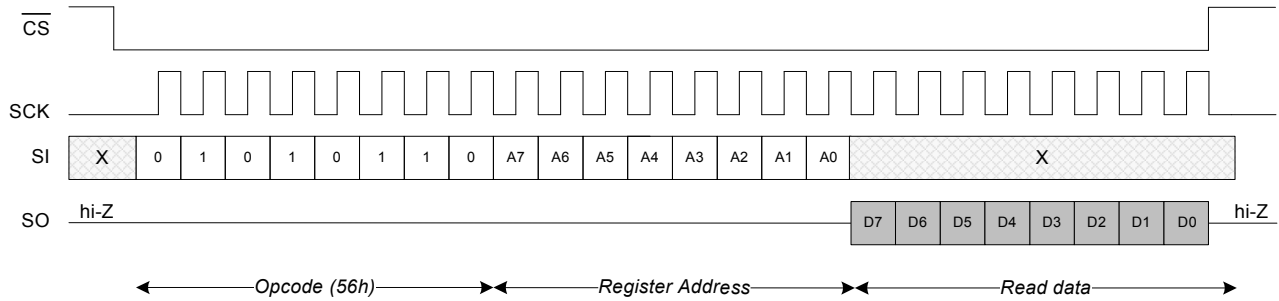


Figure 45. RDRTC Instruction in DPI Mode

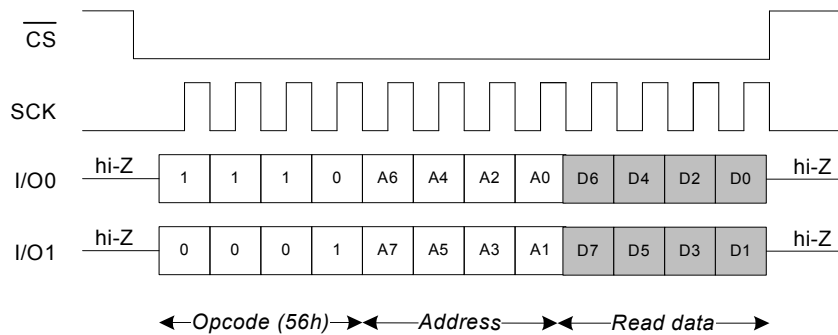
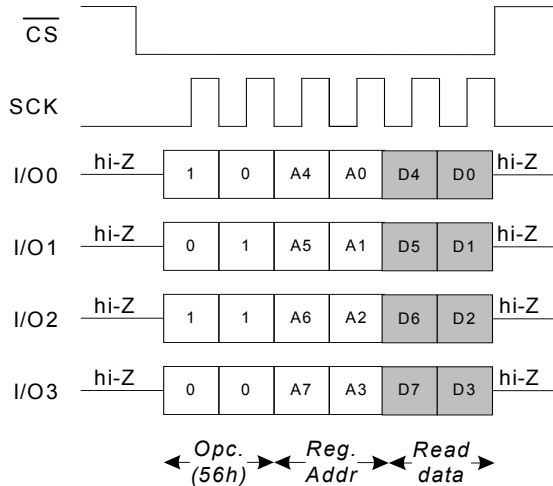


Figure 46. RDRTC Instruction in QPI Mode



**Note:** Quad bit CR[1] must be logic '1' before executing the RDRTC instruction in QPI mode.

**Fast Read Real Time Clock (FAST\_RDRTC) Instruction**

Fast Read RTC (FAST\_RDRTC) instruction is similar to RDRTC except it allows for a dummy byte after the opcode and can operate up to 108 MHz..

Figure 47. FAST\_RDRTC Instruction in SPI Mode

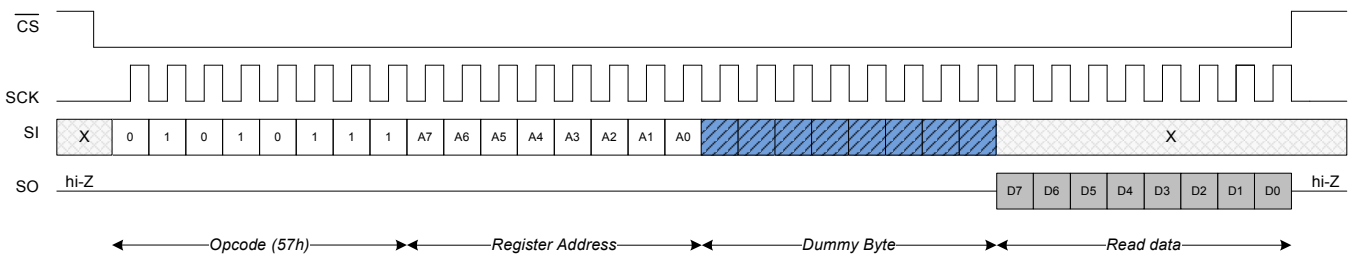


Figure 48. FAST\_RDRTC Instruction in DPI Mode

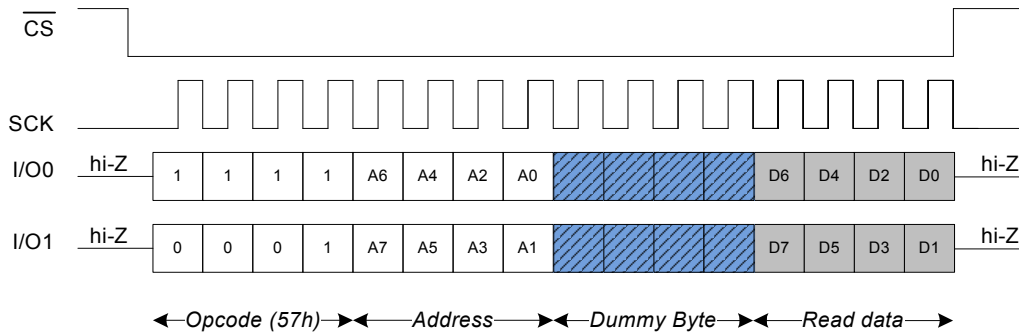
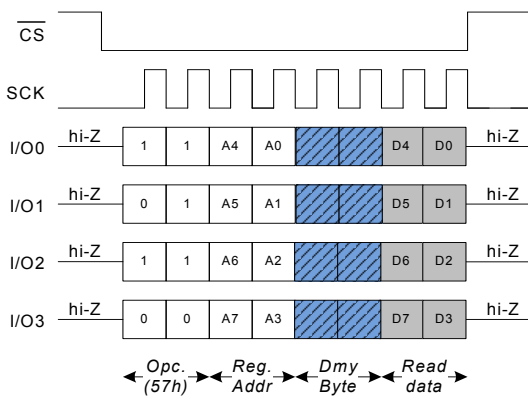


Figure 49. FAST\_RDRTC Instruction in QPI Mode



**Note:** Quad bit CR[1] must be logic '1' before executing FAST\_RDRTC instruction in QPI mode.

**Write Real Time Clock (WRRTC) Instruction**

WRITE RTC (WRRTC) instruction allows you to modify the contents of RTC registers. The WRRTC instruction requires the WEL bit in the status register to be set to '1' before it can be issued. If the WEL bit is '0', the WREN instruction needs to be issued before using WRRTC. In SPI mode, after the CS line is pulled LOW to select a device, the WRRTC opcode is transmitted through the SI line followed by eight address bits identifying the register which is to be written to and one or more bytes of data. WRRTC also allows burst mode write operation. When writing multiple bytes to RTC registers, the address rolls over to 0x00 after the last RTC register address (0x0F) is reached. DPI and QPI operations are similar to SPI except in

**Note** Writing to RTC timekeeping and control registers require the W bit to be set to '1'. The values in these RTC registers take effect only after the W bit is cleared to '0'. The Write Enable bit (WEL) is automatically cleared to '0' after completion of the WRRTC instruction.

Figure 50. WRRTC Instruction in SPI Mode

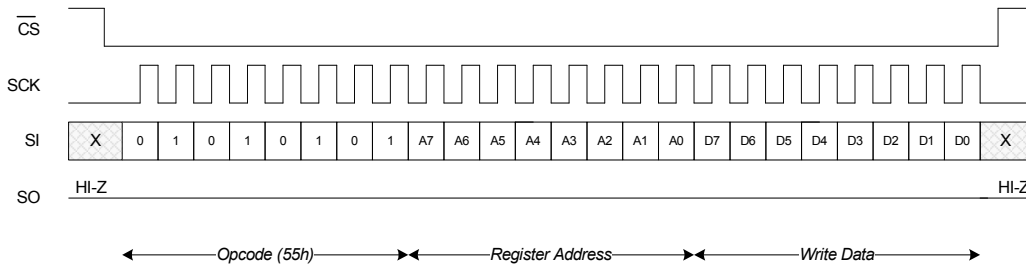


Figure 51. WRRTC Instruction in DPI Mode

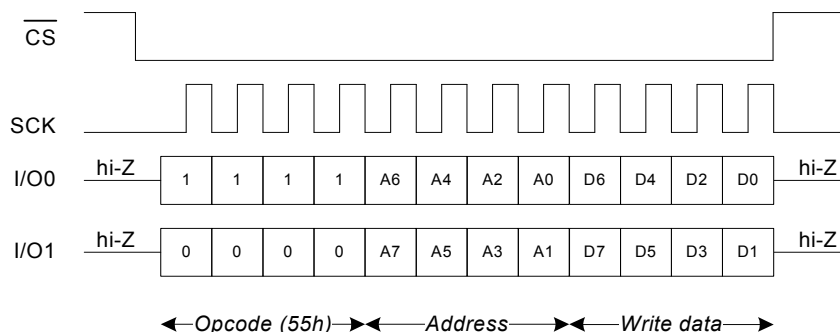
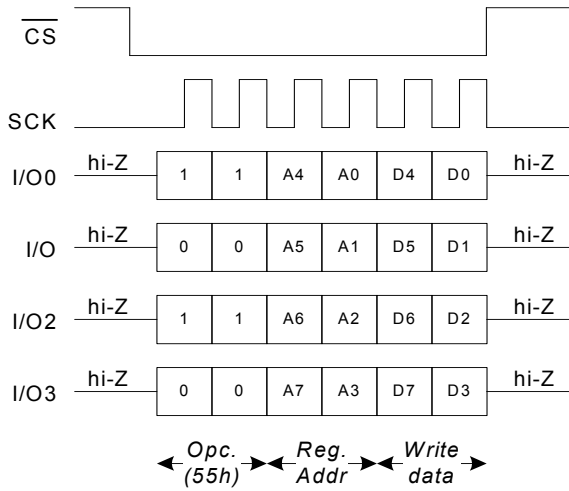


Figure 52. WRRTC Instruction in QPI Mode



Note: Quad bit CR[1] must be logic '1' before executing the WRRTC instruction in QPI mode.

Hibernate (HIBEN) Instruction

HIBEN instruction puts the nvSRAM in hibernate mode. When the HIBEN instruction is issued, the nvSRAM takes  $t_{SS}$  time to process the HIBEN request. After the HIBEN command is successfully registered and processed, the nvSRAM toggles HSB LOW, performs a STORE operation to secure the data to nonvolatile cells and then enters hibernate mode. The device starts consuming  $I_{ZZ}$  current after  $t_{HIBEN}$  time when the HIBEN instruction is registered. The device is not accessible for normal operations after the HIBEN instruction is issued. In hibernate mode, the SCK and SI pins are ignored and SO will be HI-Z but the device continues to monitor the CS pin.

To wake the nvSRAM from the hibernate mode, the device must be selected by toggling the CS pin from HIGH to LOW. The device wakes up and is accessible for normal operations after  $t_{WAKE}$  duration after a falling edge of CS pin is detected. The part will wake up in the same mode as before the HIBEN instruction.

Note Whenever nvSRAM enters hibernate mode, it initiates a nonvolatile STORE cycle, which results in an endurance cycle per hibernate command execution. A STORE cycle starts only if a write to the SRAM has been performed since the last STORE or RECALL cycle.

Table 10 summarizes the wake from Hibernate device states.

Table 10. Wake (Exit Hibernate) States

State 1	State 2	State 3	I/O Mode and Register Bits
STANDY	Hibernate	STANDBY	I/O Mode: Same mode as State 1 (SPI/DPI/QPI) SRWD SR[7]: Same as State 1 SNL SR[6]: Same as State 1 TBPROT SR[5]: Same as State 1 BP2 SR[4]: Same as State 1 BP1 SR[3]: Same as State 1 BP0 SR[2]: Same as State 1 WEL SR[1]: 0 WIP SR[0]: 0 QUAD CR[1]: Same as State 1

Figure 53. HIBEN Instruction in SPI Mode

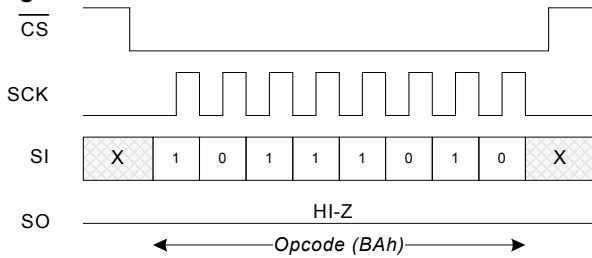
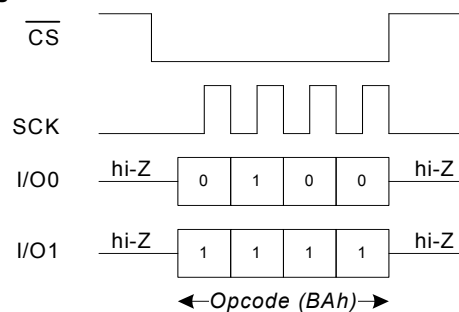
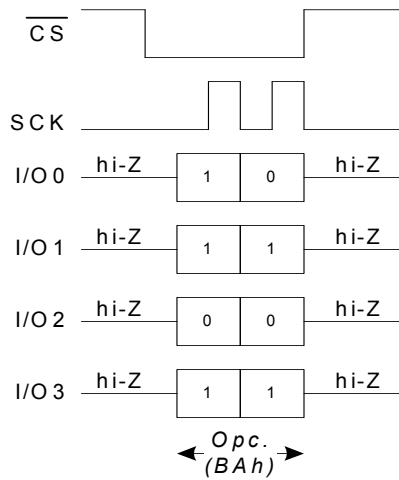


Figure 54. HIBEN Instruction in DPI Mode





**Figure 55. HIBEN Instruction in QPI Mode**

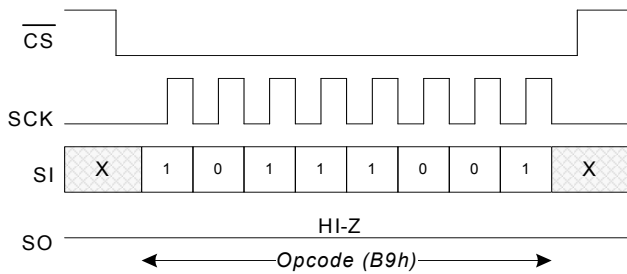


**Note** Quad bit CR[1] must be logic ‘1’ before executing the HIBEN instruction in QPI mode.

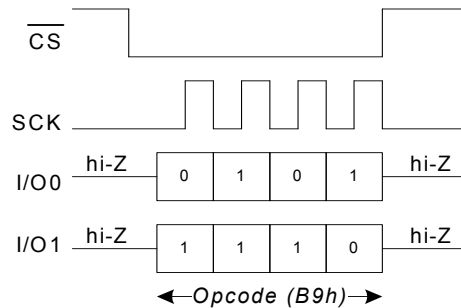
**Table 11. Exit SLEEP (EXSLP) States**

State 1	State 2	State 3	I/O Mode & Register Bits
STANDY	SLEEP	STANDBY	I/O Mode: Same mode as State 1 (SPI/DPI/QPI) SRWD SR[7]: Same as State 1 SNL SR[6]: Same as State 1 TBPROT SR[5]: Same as State 1 BP2 SR[4]: Same as State 1 BP1 SR[3]: Same as State 1 BP0 SR[2]: Same as State 1 WEL SR[1]: Same as State 1 WIP SR[0]: 0 QUAD CR[1]: Same as State 1

**Figure 56. SLEEP Instruction in SPI Mode**



**Figure 57. SLEEP Instruction in DPI Mode**



**Sleep (SLEEP) Instruction**

SLEEP instruction puts the nvSRAM in sleep mode. When the SLEEP instruction is issued, the nvSRAM takes  $t_{SLEEP}$  time to process the SLEEP request and starts consuming  $I_{SLEEP}$  current. The device is not accessible for normal operations after the SLEEP instruction is issued. In sleep mode, all pins are active.

To wake the nvSRAM from sleep mode, EXSLP instruction must be entered. The nvSRAM is accessible for normal operations after  $t_{EXSLP}$  duration. The part will wake in the same mode as before the SLEEP instruction. Any instructions entered other than EXSLP and RDSR instructions while the device is in sleep mode will be ignored.

Table 11 summarizes the exit from sleep device states.

Figure 58. SLEEP Instruction in QPI Mode

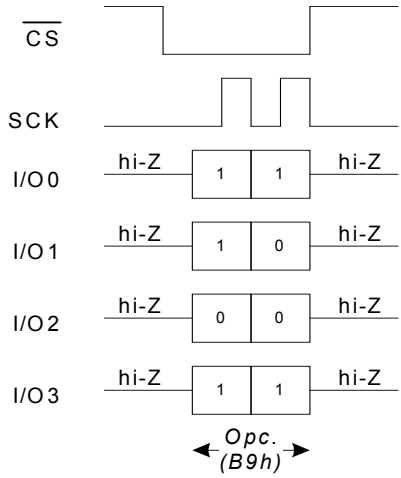


Figure 60. EXSLP Instruction in DPI Mode

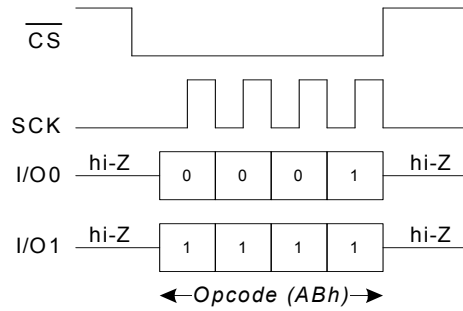


Figure 59. EXSLP Instruction in SPI Mode

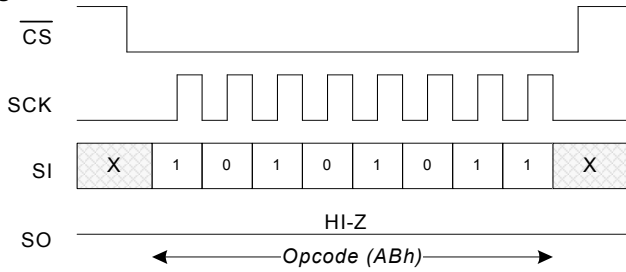
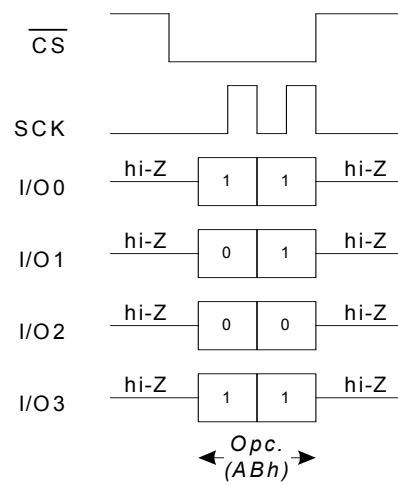


Figure 61. EXSLP Instruction in QPI Mode



## Register Instructions

### Read Status Register (RDSR) Instruction

The RDSR instruction provides access to Status Register at SPI frequencies up to 108 MHz. This instruction is used to probe the status of the device.

**Note** After the last bit of Status Register is read, the device loops back to the first bit of the Status Register.

Figure 62. RDSR Instruction in SPI Mode

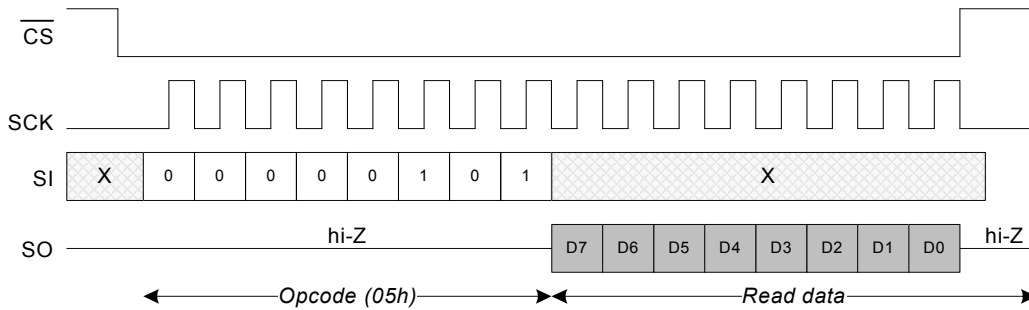


Figure 63. RDSR Instruction in DPI Mode

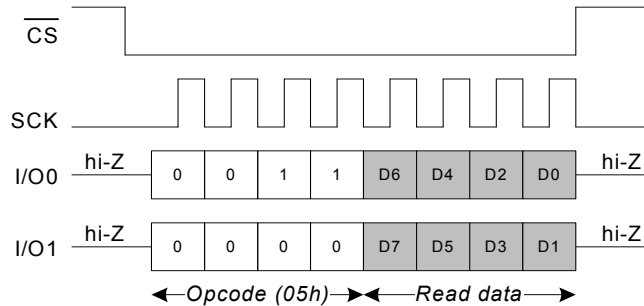
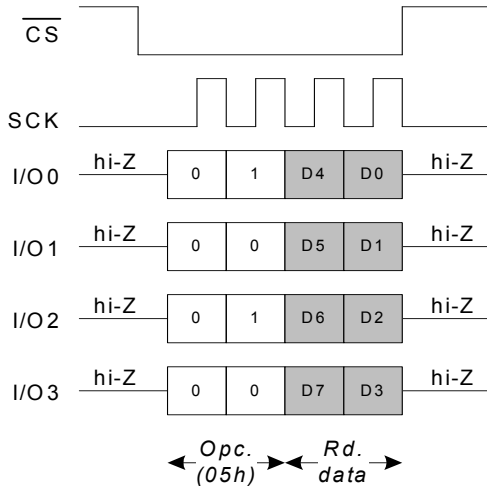


Figure 64. RDSR Instruction in QPI Mode

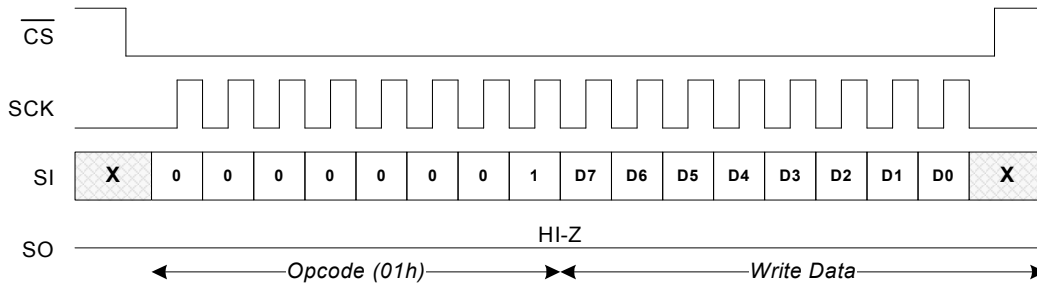
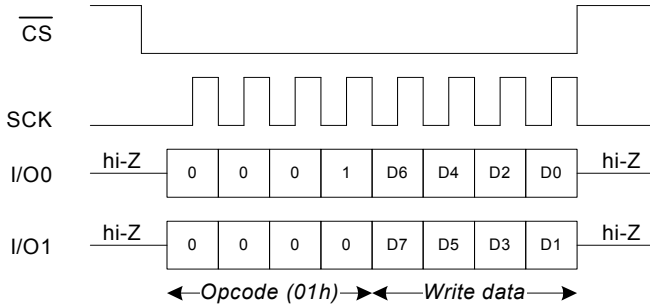


### Write Status Register (WRSR) Instruction

The WRSR instruction enables the user to write to Status Register. However, this instruction can only modify writable bits - bit 2 (BP0), bit 3 (BP1), bit 4 (BP2) bit 5 (TBPROT), bit 6 (SNL), and bit 7 (SRWD). WRSR instruction is a write instruction and needs the WEL bit set to '1' (by using WREN instruction). WRSR instruction opcode is issued after the falling edge of  $\overline{CS}$  followed by eight bits of data to be stored in Status Register. As mentioned before, WRSR instruction can only modify bits 2, 3, 4, 5, 6, and 7 of Status Register.

**Note** The values written to Status Register are saved to nonvolatile memory only after a STORE operation. If AutoStore is disabled, any modifications to the Status Register must be secured by performing a Software STORE operation.

**Note** The WEL bit in the Status Register resets to '0' on completion of a Status Register Write sequence.

**Figure 65. WRSR Instruction in SPI Mode**

**Figure 66. WRSR Instruction in DPI Mode**

**Read Configuration Register (RDCR) Instruction**

The RDCR instruction provides access to Configuration Register at SPI frequencies up to 108 MHz. The following figures provide the configuration register instruction transfer waveforms in SPI, DPI, and QPI modes.

**Note** After the last bit of Configuration Register is read, the device loops back to the first bit of the Configuration register.

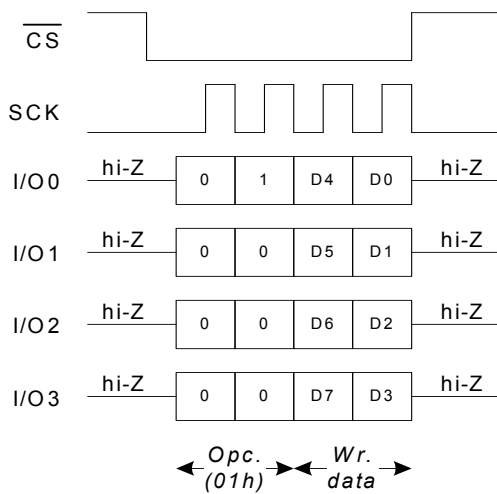
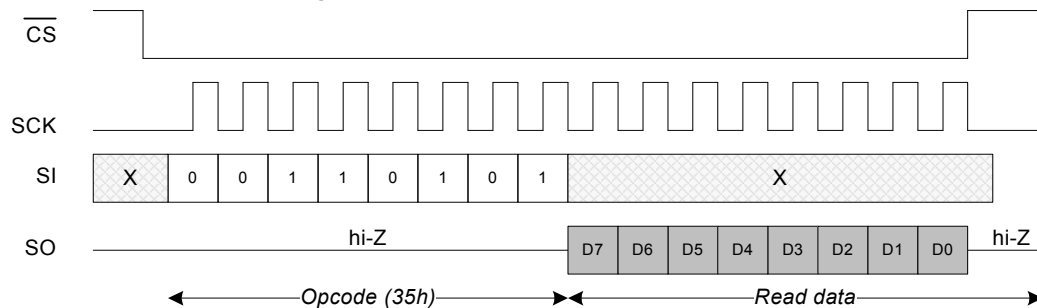
**Figure 67. WRSR Instruction in QPI Mode**

**Figure 68. RDCR Instruction in SPI Mode**


Figure 69. RDCR Instruction in DPI Mode

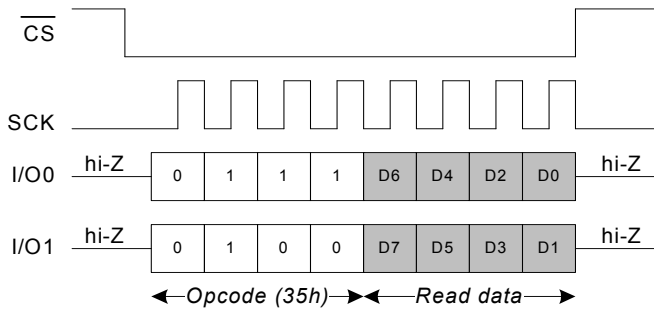
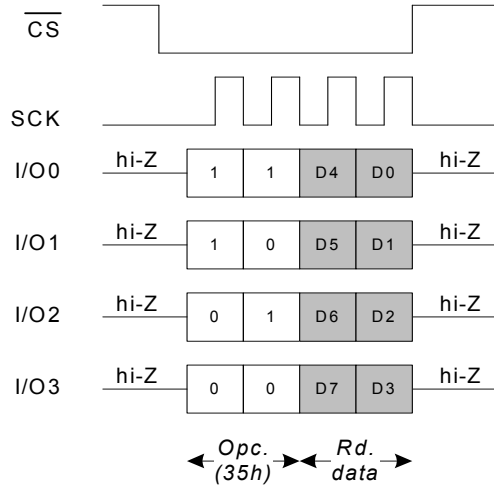


Figure 70. RDCR Instruction in QPI Mode



**Note** Quad bit CR[1] must be logic '1' before executing the RDCR instruction in QPI mode.

**Write Configuration Register (WRCR) Instruction**

The WRCR instruction enables user to change the data width of the device by setting the Quad Bit. The Quad bit must be set to one when using Read Quad Out, Quad I/O Read, and Quad Input Write commands. The QUAD bit is non-volatile.

**Note** Enabling the QPI mode (QPIEN Instruction) does not set the Quad bit in configuration register.

**Note** It is recommended that RFU bits should always be written as provided in Table 8.

Figure 71. WRCR Instruction in SPI Mode

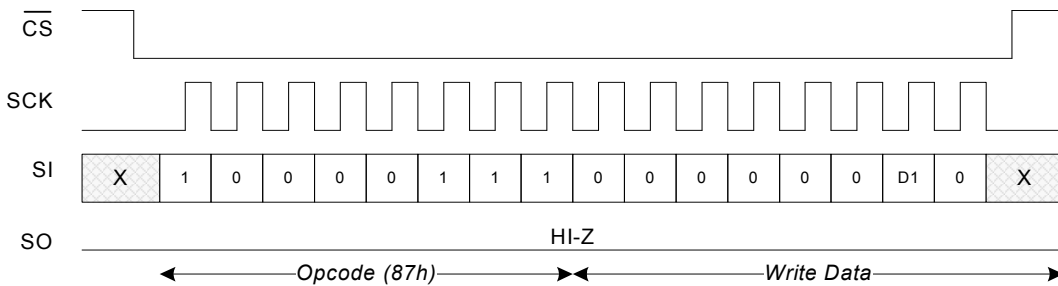
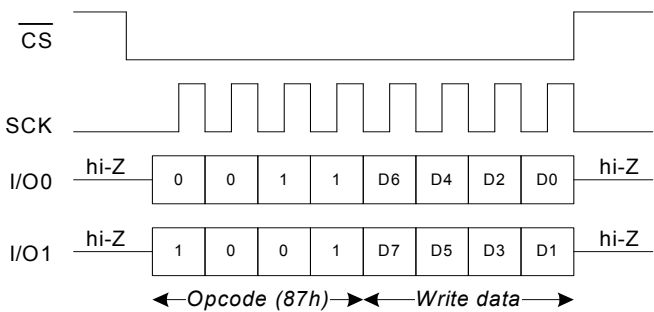


Figure 72. WRCR Instruction in DPI Mode



**Identification Register (RDID) Instruction**

RDID instruction is used to read the JEDEC-assigned manufacturer ID and product ID of the device at an SPI frequency of up to 40 MHz. This instruction can be used to identify a device on the bus. An RDID instruction can be issued by shifting the opcode for RDID after CS# goes LOW.

Device ID is 4-byte read only code identifying 1-Mbit QPI nvSRAM product uniquely. This includes the product family code, configuration and density of the product.

The RDID command reads the 4 byte Device ID structure (the structure cannot be written to). The structure is accessed one

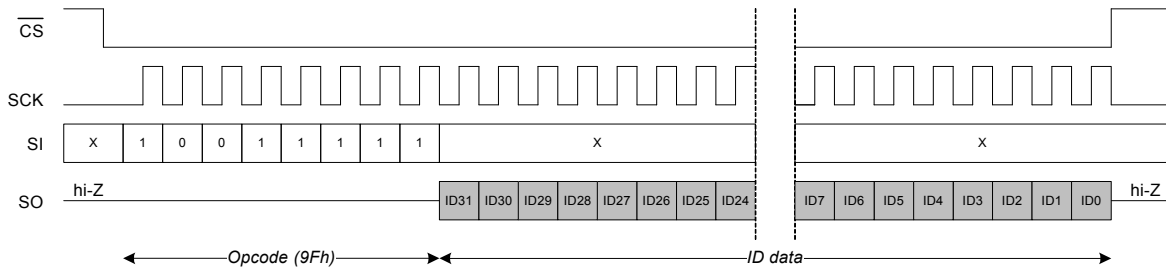
Byte at a time. The first accessed Byte is the most significant byte of the structure ID[31:24], the second accessed byte is ID[23:16], ..., the last accessed Byte is ID[7:0].

**Note** As the structure is always accessed in the same order, no address transfer is required. Instead an internal 2-bit address pointer is used that is initialized to "0" when the opcode is decoded. After each Byte access the internal address pointer is incremented. The address pointer wraps around from '3' to '0'; after the 4th Byte ID[7:0] is accessed, the 1st Byte ID[31:24] is accessed. This command can be issued in SPI, DPI or QPI Modes.

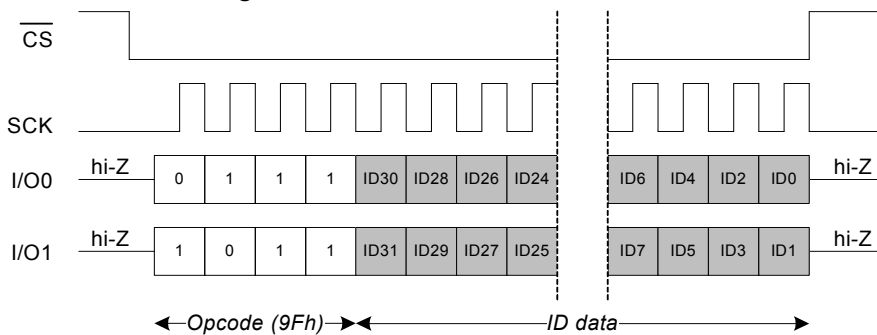
**Table 12. Device Identification**

Device	Manufacturer ID	Product ID	Density	Die REV
	31-21	20-7	6-3	2-0
	11 bits	14 bits	4 bits	3 bits
CY14V101PS	00000110100	00001110000001	0100	001

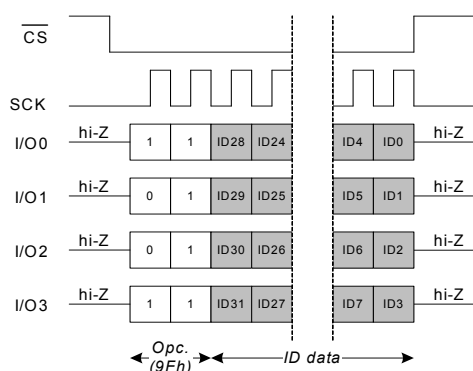
**Figure 73. RDID Instruction in SPI Mode**



**Figure 74. RDID Instruction in DPI Mode**



**Figure 75. RDID Instruction in QPI Mode**



**Note:** Quad bit CR[1] must be logic '1' before executing the RDID instruction in QPI mode.

### Identification Register (FAST\_RDID) Instruction

The FAST\_RDID instruction is similar to RDID except it allows for a dummy byte after the opcode. FAST\_RDID instruction is used to read the JEDEC-assigned manufacturer ID and product ID of the device at an SPI frequency of up to 108 MHz.

Figure 76. FAST\_RDID in SPI Mode

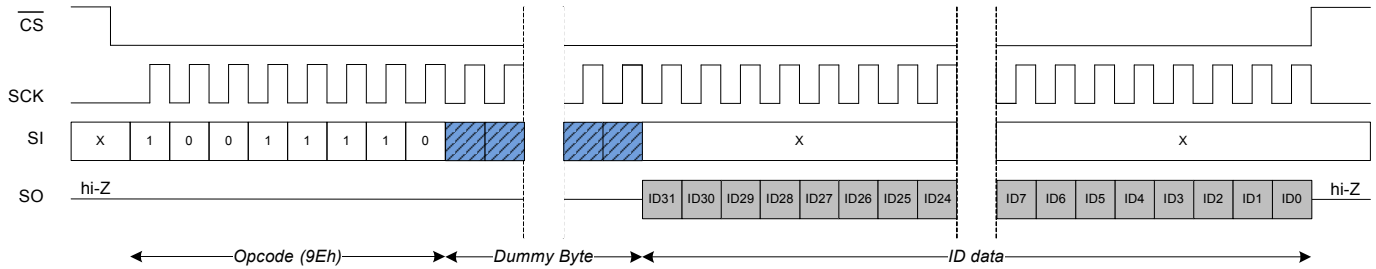


Figure 77. FAST\_RDID in DPI Mode

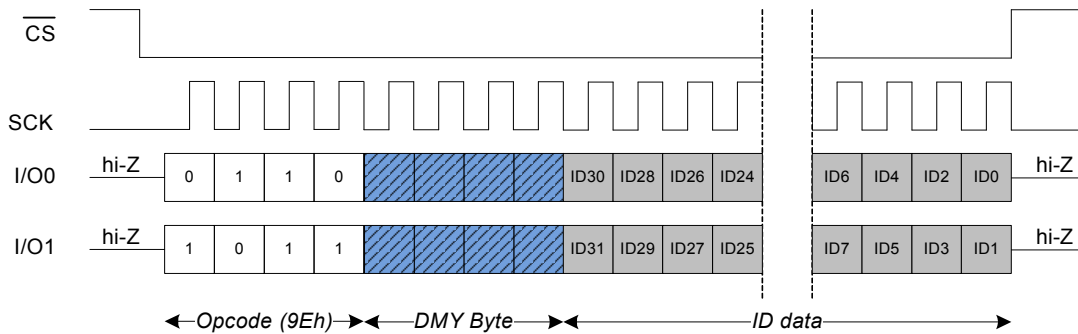
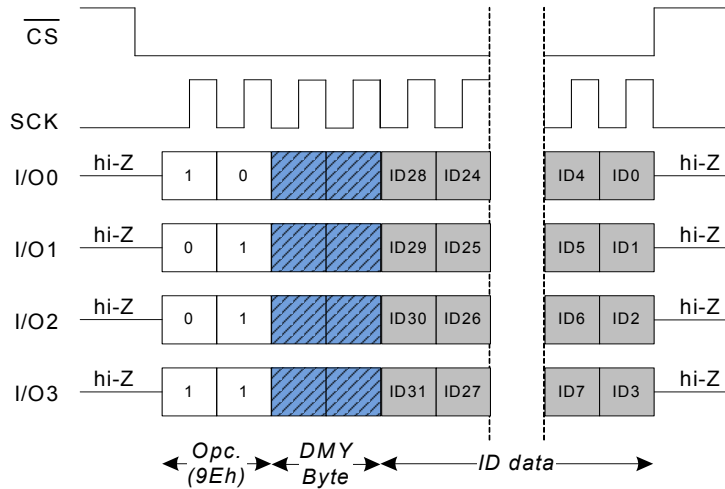


Figure 78. FAST\_RDID in QPI Mode



### Serial Number Register Write (WRSN) Instruction

The serial number is an 8 byte programmable memory space provided to the user to uniquely identify the device. It typically consists of a two byte Customer ID, followed by five bytes of unique serial number and one byte of CRC check. However, device does not calculate the CRC and it is up to the system designer to utilize the eight byte memory space in whatever manner desired. The default value for eight byte locations are set to '0x00'.

The serial number is written using WRSN command. To write serial number, the write must be enabled using the WREN command. The WRSN command can be used in burst mode to write all the 8 bytes of serial number. After the last byte of serial number is written, the device loops back to the first (MSB) byte of the serial number. The serial number is locked using the SNL bit of the Status Register. Once this bit is set to '1', no modification to the serial number is possible. After the SNL bit is set to '1', using the WRSN command has no effect on the serial number. This command requires the WEL bit to be set before it

can be executed. The WEL bit is reset to '0' after completion of this command if SRWD bit in the Status register is not set to '1' This command can be issued in SPI, DPI or QPI Modes.

The serial number is written using the WRSN instruction at an SPI frequency of up to 108 MHz.

**Note** A STORE operation (AutoStore or Software STORE) is required to store the serial number in the nonvolatile memory. If AutoStore is disabled, you must perform a Software STORE operation to secure and lock the serial number. If the SNL bit is set to '1' and is not stored (AutoStore disabled), the SNL bit and serial number defaults to '0' at the next power cycle. If the SNL bit is set to '1' and is stored, the SNL bit can never be cleared to '0'. This instruction requires the WEL bit to be set before it can be executed. This instruction can be issued in SPI, DPI, or QPI modes.

**Note** The WEL bit is reset to '0' after completion of this instruction.

Figure 79. WRSN Instruction in SPI Mode

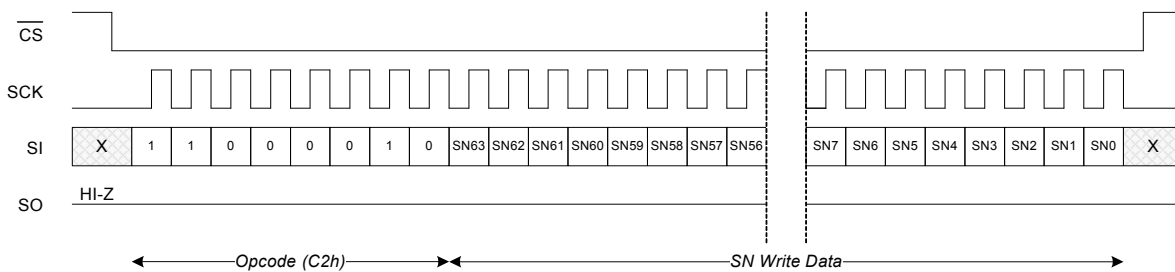


Figure 80. WRSN Instruction in DPI Mode

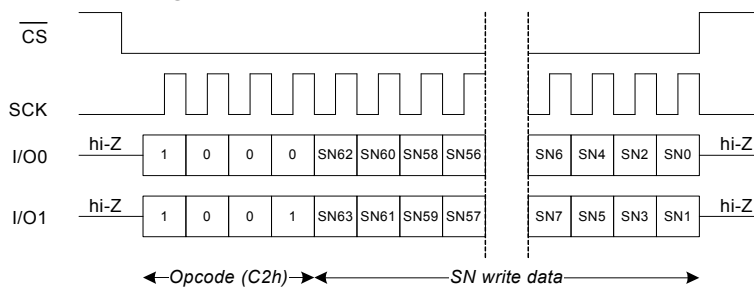
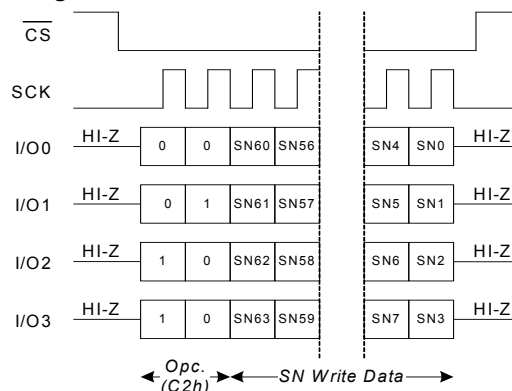


Figure 81. WRSN Instruction in QPI Mode





### Serial Number Register Read (RDSN) Instruction

The serial number is read using the RDSN instruction at an SPI frequency of up to 40 MHz. A serial number read may be performed in burst mode to read all the eight bytes at once. After the last byte of serial number is read, the device loops back to the first (MSB) byte of the serial number. An RDSN instruction

can be issued by shifting the opcode for RDSN after  $\overline{CS}$  goes LOW. This is followed by nvSRAM shifting out the eight bytes of the serial number. This instruction can be issued in SPI, DPI or QPI modes.

Figure 82. RDSN Instruction in SPI Mode

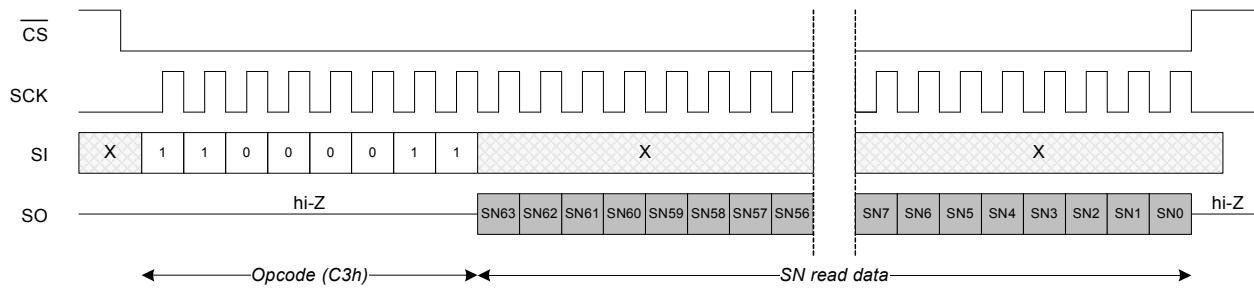


Figure 83. RDSN Instruction in DPI Mode

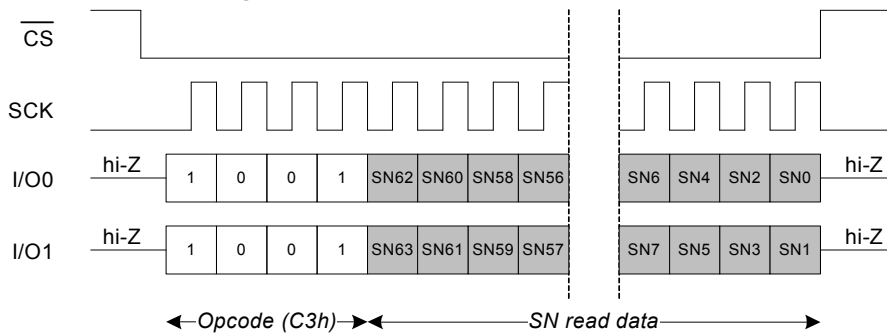
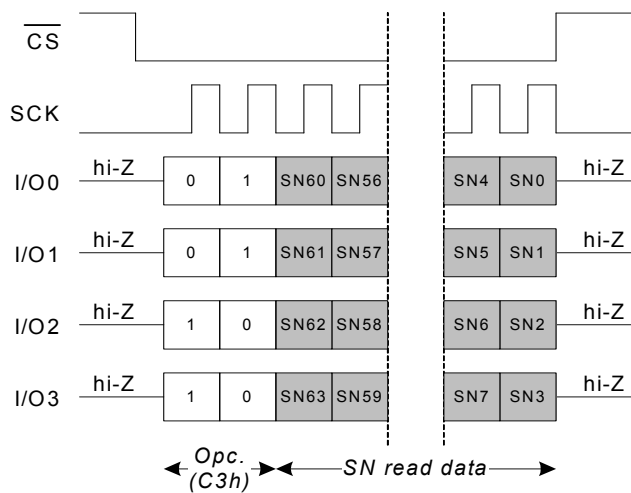


Figure 84. RDSN Instruction in QPI Mode



**Note** Quad bit CR[1] must be logic '1' before executing the RDSN instruction in QPI mode.

### Fast Read Serial Number Register (FAST\_RDSN) Instruction

The FAST\_RDSN instruction is similar to RDSN except it allows for a dummy byte after the opcode. FAST\_RDSN instruction is used up to 108 MHz.

Figure 85. FAST\_RDSN Instruction in SPI Mode

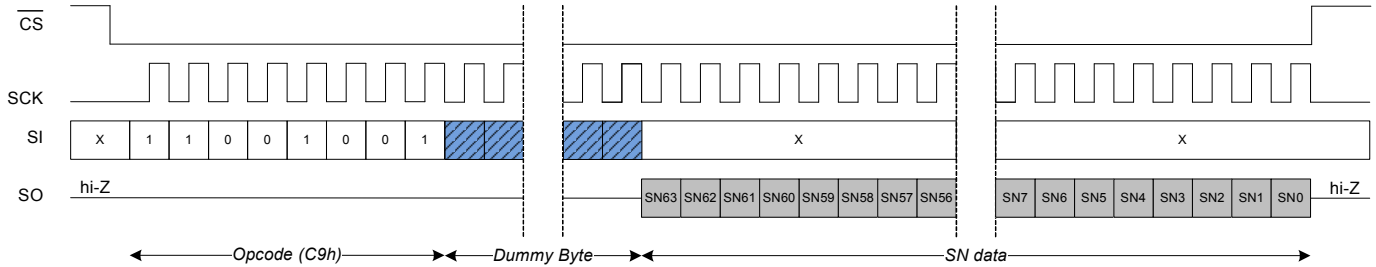


Figure 86. FAST\_RDSN Instruction in DPI Mode

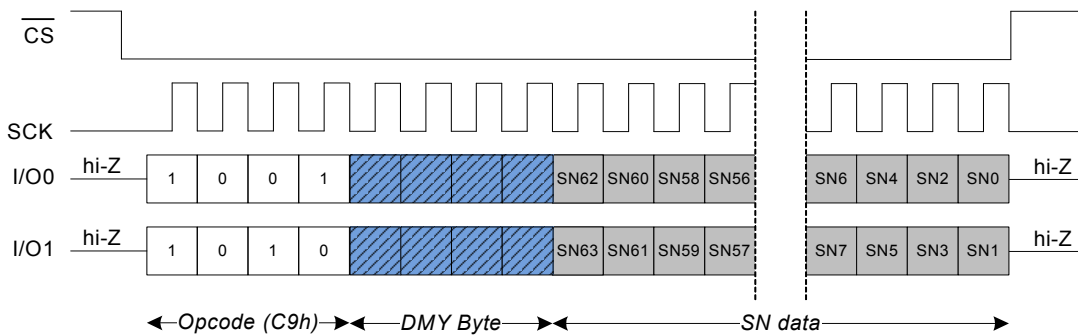
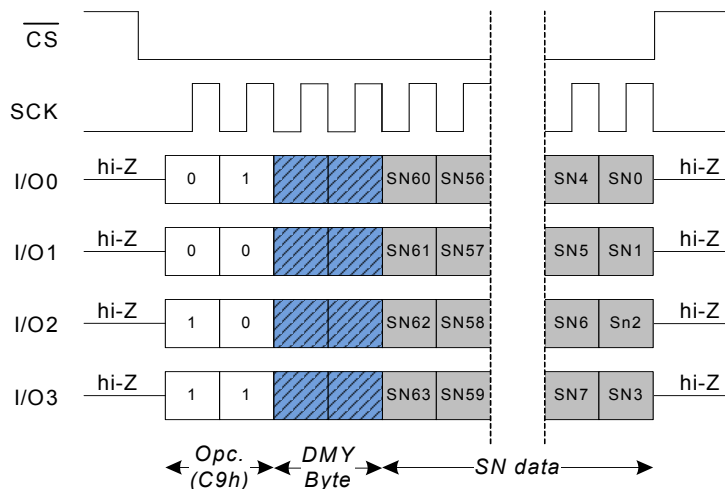


Figure 87. FAST\_RDSN Instruction in QPI Mode



### NV Specific Instructions

The nvSRAM device provides four special instructions, which enable access to the nvSRAM specific functions: STORE, RECALL, ASEN, and ASDI.

#### Software Store (STORE) Instruction

When a STORE instruction is executed, nvSRAM performs a Software STORE operation. The STORE operation is performed irrespective of whether a write has taken place since the last STORE or RECALL operation. To issue this instruction, the device must be write enabled (WEL bit = '1'). The instruction can be issued in SPI, DPI and QPI modes.

**Note** The WEL bit is cleared on the positive edge of  $\overline{CS}$  following the STORE instruction.

Figure 88. STORE Instruction in SPI Mode

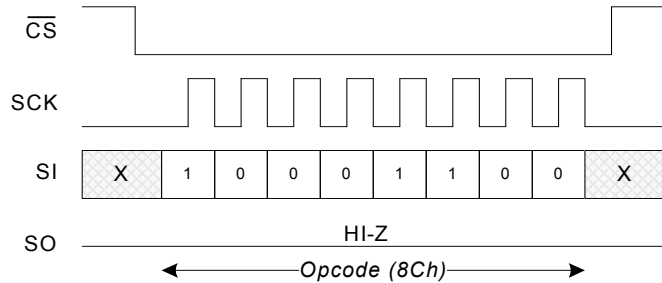
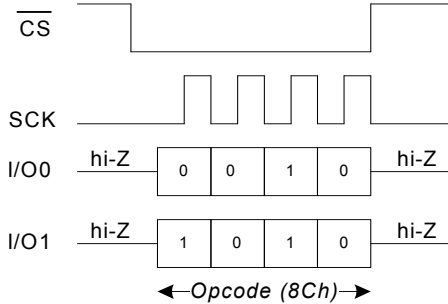


Figure 89. STORE Instruction in DPI Mode



#### Software Recall (RECALL) Instruction

When a RECALL instruction is executed, nvSRAM performs a Software RECALL operation. To issue this instruction, the device must be write enabled (WEL = '1'). This instruction can be issued in SPI, DPI, or QPI modes.

**Note** The WEL bit is cleared on the positive edge of  $\overline{CS}$  following the RECALL instruction.

Figure 90. STORE Instruction in QPI Mode

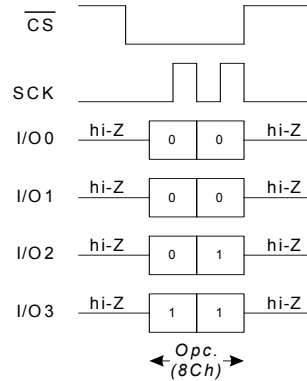


Figure 91. RECALL Instruction in SPI Mode

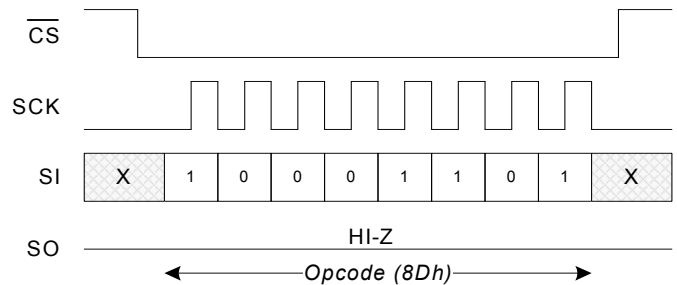


Figure 92. RECALL Instruction in DPI Mode

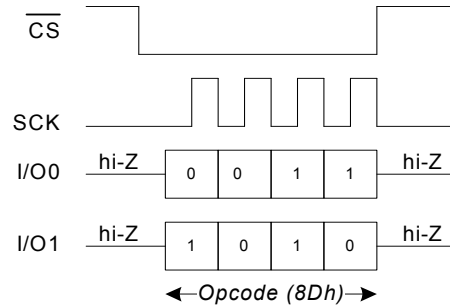
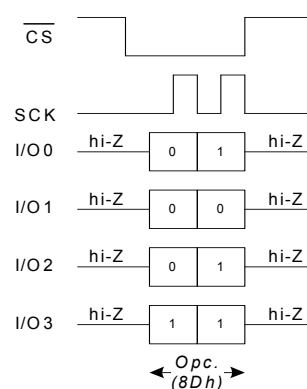


Figure 93. RECALL Instruction in QPI Mode



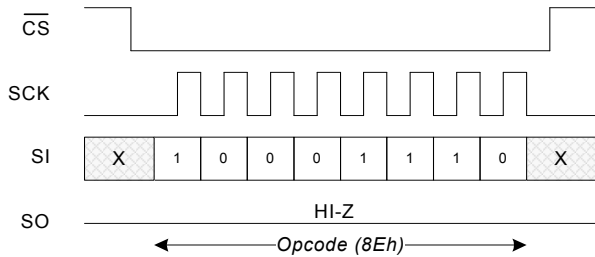
**Autostore Enable (ASEN) Instruction**

The AutoStore Enable instruction enables the AutoStore on the nvSRAM device. This setting is not nonvolatile and needs to be followed by a STORE sequence to survive the power cycle. To issue this instruction, the device must be write enabled (WEL = '1'). This instruction can be issued in SPI, DPIO, or QPI modes.

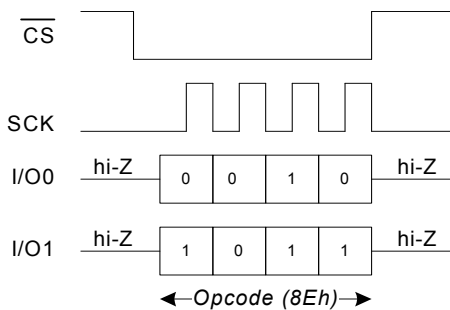
**Note** If the ASDI and ASEN instructions are executed, the device is busy for the duration of software sequence processing time ( $t_{SS}$ ).

**Note** The WEL bit is cleared on the positive edge of  $\overline{CS}$  following the ASE instruction.

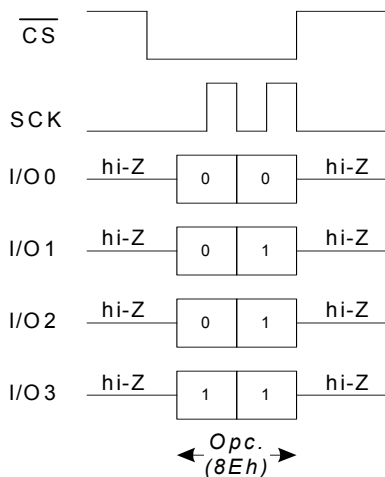
**Figure 94. ASEN Instruction in SPI Mode**



**Figure 95. ASEN Instruction in DPIO Mode**



**Figure 96. ASEN Instruction in QPI Mode**

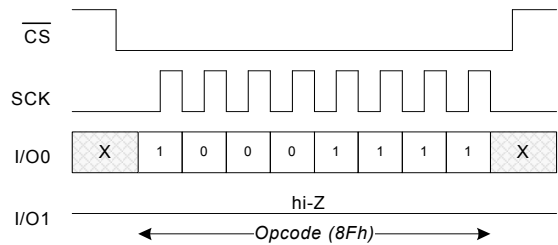


**Autostore Disable (ASDI) Instruction**

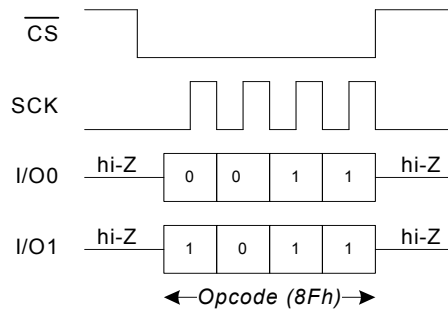
AutoStore is enabled by default in this device. The ASDI instruction disables the AutoStore. This setting is not nonvolatile and needs to be followed by a STORE sequence to survive the power cycle. To issue this instruction, the device must be write enabled (WEL = '1'). This instruction can be issued in SPI, DPIO, or QPI modes.

**Note** The WEL bit is cleared on the positive edge of  $\overline{CS}$  following the ASDI instruction.

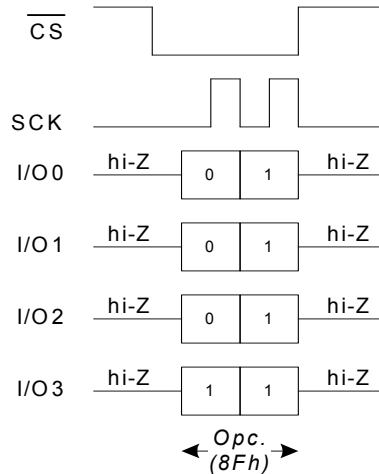
**Figure 97. ASDI Instruction in SPI Mode**



**Figure 98. ASDI Instruction in DPIO Mode**



**Figure 99. ASDI Instruction in QPI Mode**



**Note:** Quad bit CR[1] must be logic '1' before executing the ASDI instruction in QPI mode.

## Real Time Clock Operation

### nvTIME Operation

The device offers internal registers that contain clock, alarm, watchdog, interrupt, and control functions. The RTC registers occupy a separate address space from nvSRAM and are accessible through the Read RTC register and Write RTC register sequence on register addresses 0x00 to 0x0F. Internal double buffering of the time keeping registers prevents accessing transitional internal clock data during a read or write operation. Double buffering also circumvents disrupting normal timing counts or the clock accuracy of the internal clock when accessing clock data. Clock and alarm registers store data in BCD format.

### Clock Operations

The clock registers maintain time up to 9,999 years in one-second increments. The time can be set to any calendar time and the clock automatically keeps track of days of the week and month, leap years, and century transitions. There are eight registers dedicated to the clock functions, which are used to set time with a write cycle and to read time with a read cycle. These registers contain the time of day in BCD format. Bits defined as '0' are currently not used and are reserved for future use by Cypress.

### Reading the Clock

The double-buffered RTC register structure reduces the chance of reading incorrect data from the clock. Internal updates to the device time keeping registers are stopped when the read bit 'R' (in the flags register at 0x00) is set to '1' before reading clock data to prevent reading of data in transition. Stopping the register updates does not affect clock accuracy.

When a read sequence of RTC device is initiated, the update of the user timekeeping registers stops and does not restart until a '0' is written to the R bit (in the flags register at 0x00). After the end of read sequence, all the RTC registers are simultaneously updated within 20 ms.

### Setting the Clock

A write access to the RTC device stops updates to the time keeping registers and enables the time to be set when the write bit 'W' (in the flags register at 0x00) is set to '1'. The correct day, date, and time is then written into the registers and must be in 24 hour BCD format. The time written is referred to as the "Base Time". This value is stored in nonvolatile registers and used in the calculation of the current time. When the W bit is cleared by writing '0' to it, the values of timekeeping registers are transferred to the actual clock counters after which the clock resumes normal operation.

If the time written to the timekeeping registers is not in the correct BCD format, each invalid nibble of the RTC registers continue counting to 0xF before rolling over to 0x0 after which RTC resumes normal operation.

**Note** After the W bit is set to '0', values written into the timekeeping, alarm, calibration, and interrupt registers are transferred to the RTC time keeping counters in  $t_{RTCP}$  time. These counter values must be saved to nonvolatile memory either by

initiating a Software/Hardware STORE or AutoStore operation. While working in AutoStore disabled mode, perform a STORE operation after  $t_{RTCP}$  time while writing into the RTC registers for the modifications to be correctly recorded.

### Backup Power

The RTC in the device is intended for permanently powered operation. The  $V_{RTCbat}$  or  $V_{RTCbat}$  pin is connected to a battery. It is recommended to use a 3-V lithium battery and the device sources current only from the battery when the primary power is removed. However, the battery is not recharged at any time by the device. The battery capacity must be chosen for total anticipated cumulative down time required over the life of the system.

When the primary power,  $V_{CC}$ , fails and drops below  $V_{SWITCH}$  the device switches to the backup power supply. The clock oscillator uses very little current, which maximizes the backup time available from the backup source. Regardless of the clock operation with the primary source removed, the data stored in the nvSRAM is secure, having been stored in the nonvolatile elements when power was lost. During backup operation, the device consumes a 0.45  $\mu$ A (typ) at room temperature.

**Note** If a battery is applied to  $V_{RTCbat}$  pin prior to  $V_{CC}$ , the chip will draw high  $I_{BAK}$  current. This occurs even if the oscillator is disabled. In order to maximize battery life,  $V_{CC}$  must be applied before a battery is applied to  $V_{RTCbat}$  pin.

### Stopping and Starting the Oscillator

The OSCEN bit in the calibration register at 0x08 controls the enable and disable of the oscillator. This bit is nonvolatile and is shipped to customers in the "enabled" (set to '0') state. To preserve the battery life when the system is in storage, OSCEN must be set to '1'. This turns off the oscillator circuit, extending the battery life. If the OSCEN bit goes from disabled to enabled, it takes approximately one second (two seconds maximum) for the oscillator to start.

While system power is off, if the voltage on the backup supply ( $V_{RTCcap}$  or  $V_{RTCbat}$ ) falls below their respective minimum level, the oscillator may fail. The device has the ability to detect oscillator failure when system power is restored. This is recorded in the Oscillator Fail Flag (OSCF) of the flags register at the address 0x00. When the device is powered on ( $V_{CC}$  goes above  $V_{SWITCH}$ ) the OSCEN bit is checked for the 'enabled' status. If the OSCEN bit is enabled and the oscillator is not active within the first 5 ms, the OSCF bit is set to '1'. The system must check for this condition and then write '0' to clear the flag.

Note that in addition to setting the OSCF flag bit, the time registers are reset to the 'Base Time', which is the value last written to the timekeeping registers. The control or calibration registers and the OSCEN bit are not affected by the 'oscillator failed' condition.

The value of OSCF must be reset to '0' when the time registers are written for the first time. This initializes the state of this bit, which may have become set when the system was first powered on.

To reset OSCF, set the W bit (in the flags register at 0x00) to a '1' to enable writes to the flags register. Write a '0' to the OSCF bit and then reset the W bit to '0' to disable writes.

## Calibrating the Clock

The RTC is driven by a quartz controlled crystal with a nominal frequency of 32.768 kHz. Clock accuracy depends on the quality of the crystal and calibration. The crystals available in market typically have an error of  $\pm 20$  ppm to  $\pm 35$  ppm. However, the device employs a calibration circuit that improves the accuracy to  $+1/-2$  ppm at 25 °C. This implies an error of +2.5 seconds to -5 seconds per month.

The calibration circuit adds or subtracts counts from the oscillator divider circuit to achieve this accuracy. The number of pulses that are suppressed (subtracted, negative calibration) or split (added, positive calibration) depends upon the value loaded into the five calibration bits found in calibration register at 0x08. The calibration bits occupy the five lower order bits in the calibration register. These bits are set to represent any value between '0' and 31 in binary form. Bit D5 is a sign bit, where a '1' indicates positive calibration and a '0' indicates negative calibration. Adding counts speeds the clock up and subtracting counts slows the clock down. If a binary '1' is loaded into the register, it corresponds to an adjustment of 4.068 or  $-2.034$  ppm offset in oscillator error, depending on the sign.

Calibration occurs within a 64-minute cycle. The first 62 minutes in the cycle may, once per minute, have one second shortened by 128 or lengthened by 256 oscillator cycles. If a binary '1' is loaded into the register, only the first two minutes of the 64-minute cycle are modified. If a binary 6 is loaded, the first 12 are affected, and so on. Therefore, each calibration step has the effect of adding 512 or subtracting 256 oscillator cycles for every 125,829,120 actual oscillator cycles, that is, 4.068 or  $-2.034$  ppm of adjustment per calibration step in the calibration register.

To determine the required calibration, the CAL bit in the flags register (0x00) must be set to '1'. This causes the INT pin to toggle at a nominal frequency of 512 Hz. Any deviation measured from the 512 Hz indicates the degree and direction of the required correction. For example, a reading of 512.01024 Hz indicates a +20 ppm error. Hence, a decimal value of  $-10$  (001010b) must be loaded into the calibration register to offset this error.

**Note** Setting or changing the calibration register does not affect the test output frequency.

To set or clear CAL, set the W bit (in the flags register at 0x00) to '1' to enable writes to the flags register. Write a value to CAL, and then reset the W bit to '0' to disable writes.

## Alarm

The alarm function compares user-programmed values of alarm time and date (stored in the registers 0x01–5) with the corresponding time of day and date values. When a match occurs, the alarm internal flag (AF) is set and an interrupt is generated on INT pin, if the Alarm Interrupt Enable (AIE) bit is set.

There are four alarm match fields: date, hours, minutes, and seconds. Each of these fields has a match bit that is used to determine if the field is used in the alarm match logic. Setting the match bit to '0' indicates that the corresponding field is used in the match process. Depending on the match bits, the alarm occurs as specifically as once a month or as frequently as once every minute. Selecting none of the match bits (all 1s) indicates that no match is required and therefore, alarm is disabled.

Selecting all match bits (all 0s) causes an exact time and date match.

There are two ways to detect an alarm event: by reading the AF flag or monitoring the INT pin. The AF flag in the flags register at 0x00 indicates that a date or time match has occurred. The AF bit is set to '1' when a match occurs. Reading the flags register clears the alarm flag bit (and all others). A hardware interrupt pin may also be used to detect an alarm event.

To set, clear or enable an alarm, set the W bit (in the flags register - 0x00) to '1' to enable writes to alarm registers. After writing the alarm value, clear the W bit back to '0' for the changes to take effect.

**Note** The device requires the alarm match bit for seconds (bit 'D7' in Alarm-Seconds register 0x02) to be set to '0' for proper operation of Alarm Flag and Interrupt.

## Watchdog Timer

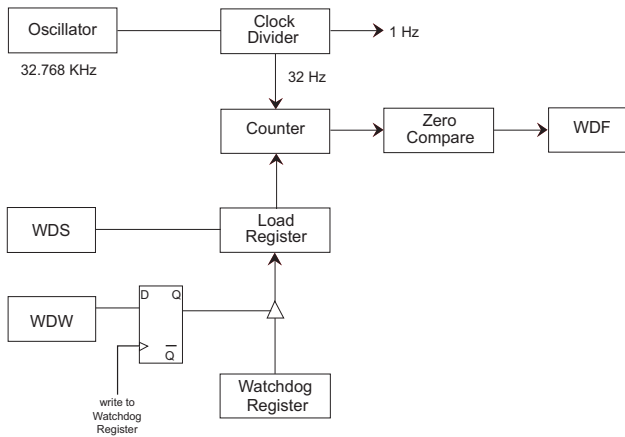
The watchdog timer is a free-running down counter that uses the 32-Hz clock (31.25 ms) derived from the crystal oscillator. The oscillator must be running for the watchdog to function. It begins counting down from the value loaded in the watchdog timer register.

The timer consists of a loadable register and a free-running counter. On power-up, the watchdog timeout value in register 0x07 is loaded into the counter load register. Counting begins on power-up and restarts from the loadable value any time the Watchdog Strobe (WDS) bit is set to '1'. The counter is compared to the terminal value of '0'. If the counter reaches this value, it causes an internal flag and an optional interrupt output. You can prevent the timeout interrupt by setting the WDS bit to '1' prior to the counter reaching '0'. This causes the counter to reload with the watchdog timeout value and to be restarted. As long as the user sets the WDS bit prior to the counter reaching the terminal value, the interrupt and WDT flag never occur.

New timeout values are written by setting the watchdog write bit to '0'. When the WDW is '0', new writes to the watchdog timeout value bits D5–D0 are enabled to modify the timeout value. When WDW is '1', writes to bits D5–D0 are ignored. The WDW function enables you to set the WDS bit without concern that the watchdog timer value is modified. A logical diagram of the watchdog timer is shown in [Figure 100 on page 47](#). Note that setting the watchdog timeout value to '0' disables the watchdog function.

The output of the watchdog timer is the flag bit WDF that is set if the watchdog is allowed to timeout. If the Watchdog Interrupt Enable (WIE) bit in the interrupt register is set, a hardware interrupt on INT pin is also generated on watchdog timeout. The flag and the hardware interrupt are both cleared when user reads the flag registers.

Figure 100. Watchdog Timer Block Diagram



### Programmable Square Wave Generator

The square wave generator block uses the crystal output to generate a desired frequency on the INT pin of the device. The output frequency can be programmed to be one of these:

- 1 Hz
- 512 Hz
- 4096 Hz
- 32768 Hz

The square wave output is not generated while the device is running on backup power.

### Power Monitor

The device provides a power management scheme with power fail interrupt capability. It also controls the internal switch to backup power for the clock and protects the memory from low  $V_{CC}$  access. The power monitor is based on an internal band gap reference circuit that compares the  $V_{CC}$  voltage to  $V_{SWITCH}$  threshold.

As described in the section [AutoStore Operation on page 6](#), when  $V_{SWITCH}$  is reached as  $V_{CC}$  decays from power loss, a data STORE operation is initiated from SRAM to the nonvolatile elements, securing the last SRAM data state. Power is also switched from  $V_{CC}$  to the backup supply (battery) to operate the RTC oscillator.

When operating from the backup source, read and write operations to nvSRAM are inhibited and the RTC functions are not available to the user. The RTC clock continues to operate in the background. The updated RTC time keeping registers are available to the user after  $V_{CC}$  is restored to the device (see [AutoStore or Power-Up RECALL on page 59](#)).

### Backup Power Monitor

The device provides a backup power monitoring system which detects the backup power (battery backup) failure. The backup power fail flag (BPF) is issued on the next power-up in case of backup power failure. The BPF flag is set in the event of backup voltage falling lower than  $V_{BAKFAIL}$ . The backup power is monitored even while the RTC is running in backup mode. Low voltage detected during backup mode is flagged through the BPF flag. BPF can hold the data only until a defined low level of the back-up voltage ( $V_{DR}$ ).

### Interrupts

The CY14X101Q has a flags register, interrupt register, and Interrupt logic that can signal interrupt to the microcontroller. There are three potential sources for interrupt: watchdog timer, power monitor, and alarm timer. Each of these can be individually enabled to drive the INT pin by appropriate setting in the interrupt register (0x06). In addition, each has an associated flag bit in the flags register (0x00) that the host processor uses to determine the cause of the interrupt. The INT pin driver has two bits that specify its behavior when an interrupt occurs.

An Interrupt is raised only if both a flag is raised by one of the three sources and the respective interrupt enable bit in interrupts register is enabled (set to '1'). After an interrupt source is active, two programmable bits, H/L and P/L, determine the behavior of the output pin driver on INT pin. These two bits are located in the interrupt register and can be used to drive level or pulse mode output from the INT pin. In pulse mode, the pulse width is internally fixed at approximately 200 ms. This mode is intended to reset a host microcontroller. In the level mode, the pin goes to its active polarity until the flags register is read by the user. This mode is used as an interrupt to a host microcontroller. The control bits are summarized in the section [Interrupt Register](#).

Interrupts are only generated while working on normal power and are not triggered when system is running in backup power mode.

**Note** The device generates valid interrupts only after the Power Up RECALL sequence is completed. All events on INT pin must be ignored for  $t_{FA}$  duration after power-up.

### Interrupt Register

**Watchdog Interrupt Enable (WIE):** When set to '1', the watchdog timer drives the INT pin and an internal flag when a watchdog timeout occurs. When WIE is set to '0', the watchdog timer only affects the WDF flag in flags register.

**Alarm Interrupt Enable (AIE):** When set to '1', the alarm match drives the INT pin and an internal flag. When AIE is set to '0', the alarm match only affects the AF flag in flags register.

**Power Fail Interrupt Enable (PFE):** When set to '1', the power fail monitor drives the pin and an internal flag. When PFE is set to '0', the power fail monitor only affects the PF flag in flags register.

**Square Wave Enable (SQWE):** When set to '1', a square wave of programmable frequency is generated on the INT pin. The frequency is decided by the SQ1 and SQ0 bits of the interrupts register. This bit is nonvolatile and survives power cycle. The SQWE bit over rides all other interrupts. However, the CAL bit will take precedence over the square wave generator. This bit defaults to '0' from factory.

**High/Low (H/L):** When set to a '1', the INT pin is active HIGH and the driver mode is push pull. The INT pin drives HIGH only when  $V_{CC}$  is greater than  $V_{SWITCH}$ . When set to a '0', the INT pin is active LOW and the drive mode is open drain. The INT pin must be pulled up to  $V_{CC}$  by a 10k resistor while using the interrupt in active LOW mode.

**Pulse/Level (P/L):** When set to a '1' and an interrupt occurs, the INT pin is driven for approximately 200 ms. When P/L is set to a '0', the INT pin is driven HIGH or LOW (determined by H/L) until the flags register is read.

**SQ1 and SQ0.** These bits are used together to fix the frequency of square wave on INT pin output when the SQWE bit is set to '1'. These bits are nonvolatile and survive power cycle. The output frequency is decided as per the following table.

**Table 13. SQW Output Selection**

SQ1	SQ0	Frequency	Comment
0	0	1 Hz	1 Hz signal
0	1	512 Hz	Useful for calibration
1	0	4096 Hz	4 kHz clock output
1	1	32768 Hz	Oscillator output frequency

When an enabled interrupt source activates the INT pin, an external host reads the flag registers to determine the cause. Remember that all flag are cleared when the register is read. If the INT pin is programmed for Level mode, then the condition clears and the INT pin returns to its inactive state. If the pin is programmed for pulse mode, then reading the flag also clears the flag and the pin. The pulse does not complete its specified duration if the flags register is read. If the INT pin is used as a host reset, the flags register is not read during a reset.

This summary table shows the state of the INT pin.

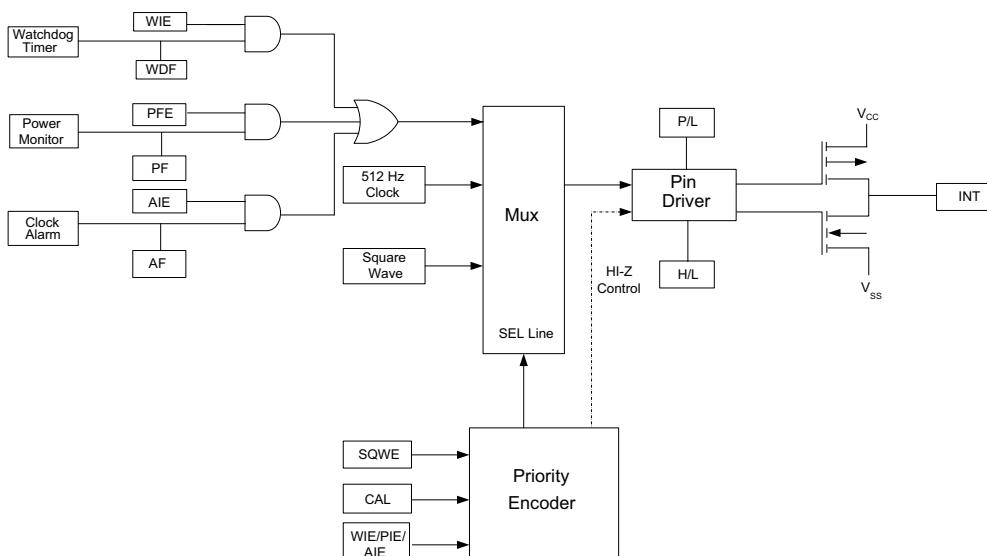
**Table 14. State of the INT Pin**

CAL	SQWE	WIE/AIE/PFE	INT Pin Output
1	X	X	512 Hz
0	1	X	Square Wave Output
0	0	1	Alarm
0	0	0	HI-Z

**Flags Register**

The flags register has three flag bits: WDF, AF, and PF, which can be used to generate an interrupt. These flag are set by the watchdog timeout, alarm match, or power fail monitor respectively. The processor can either poll this register or enable interrupts to be informed when a flag is set. These flags are automatically reset after the register is read. The flags register is automatically loaded with the value 0x00 on power-up (except for the OSCF bit. See [Stopping and Starting the Oscillator on page 45](#)).

**Figure 101. Interrupt Block Diagram**



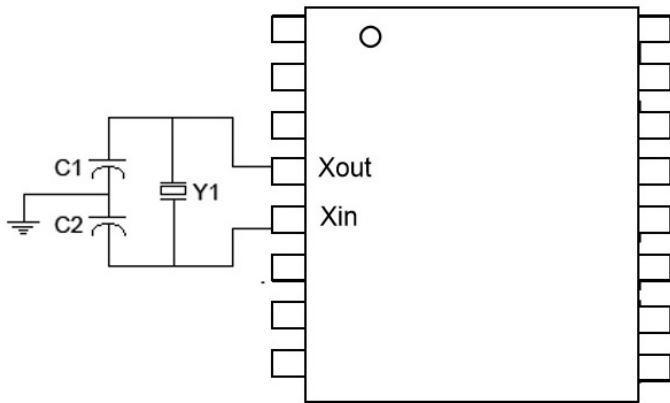
- WDF - Watchdog Timer Flag
- WIE - Watchdog Interrupt Enable
- PF - Power Fail Flag
- PFE - Power Fail Enable
- AF - Alarm Flag
- AIE - Alarm Interrupt Enable
- P/L - Pulse Level
- H/L - High/Low
- SQWE - Square wave enable



**RTC External Components**

The RTC requires connecting an external 32.768-kHz crystal and  $C_1$ ,  $C_2$  load capacitance as shown in the [Figure 102](#). The figure shows the recommended RTC external component values. The load capacitances  $C_1$  and  $C_2$  are inclusive of parasitic of the printed circuit board (PCB). The PCB parasitic includes the capacitance due to land pattern of crystal pads/pins,  $X_{in}/X_{out}$  pads and copper traces connecting crystal and device pins.

**Figure 102. RTC Recommended Component Configuration<sup>[1]</sup>**



**Recommended Values**

Y1 = 32.768 kHz

$C_1$  = 20 pF

$C_2$  = 40 pF

**Note:** The recommended values for  $C_1$  and  $C_2$  include board trace capacitance.

**Notes**

1. For nvSRAM RTC design guidelines and best practices, refer to the application note, [AN61546](#).

## PCB Design Considerations for RTC

RTC crystal oscillator is a low-current circuit with high-impedance nodes on their crystal pins. Due to lower timekeeping current of RTC, the crystal connections are very sensitive to noise on the board. Hence it is necessary to isolate the RTC circuit from other signals on the board.

It is also critical to minimize the stray capacitance on the PCB. Stray capacitances add to the overall crystal load capacitance and therefore cause oscillation frequency errors. Proper bypassing and careful layout are required to achieve the optimum RTC performance.

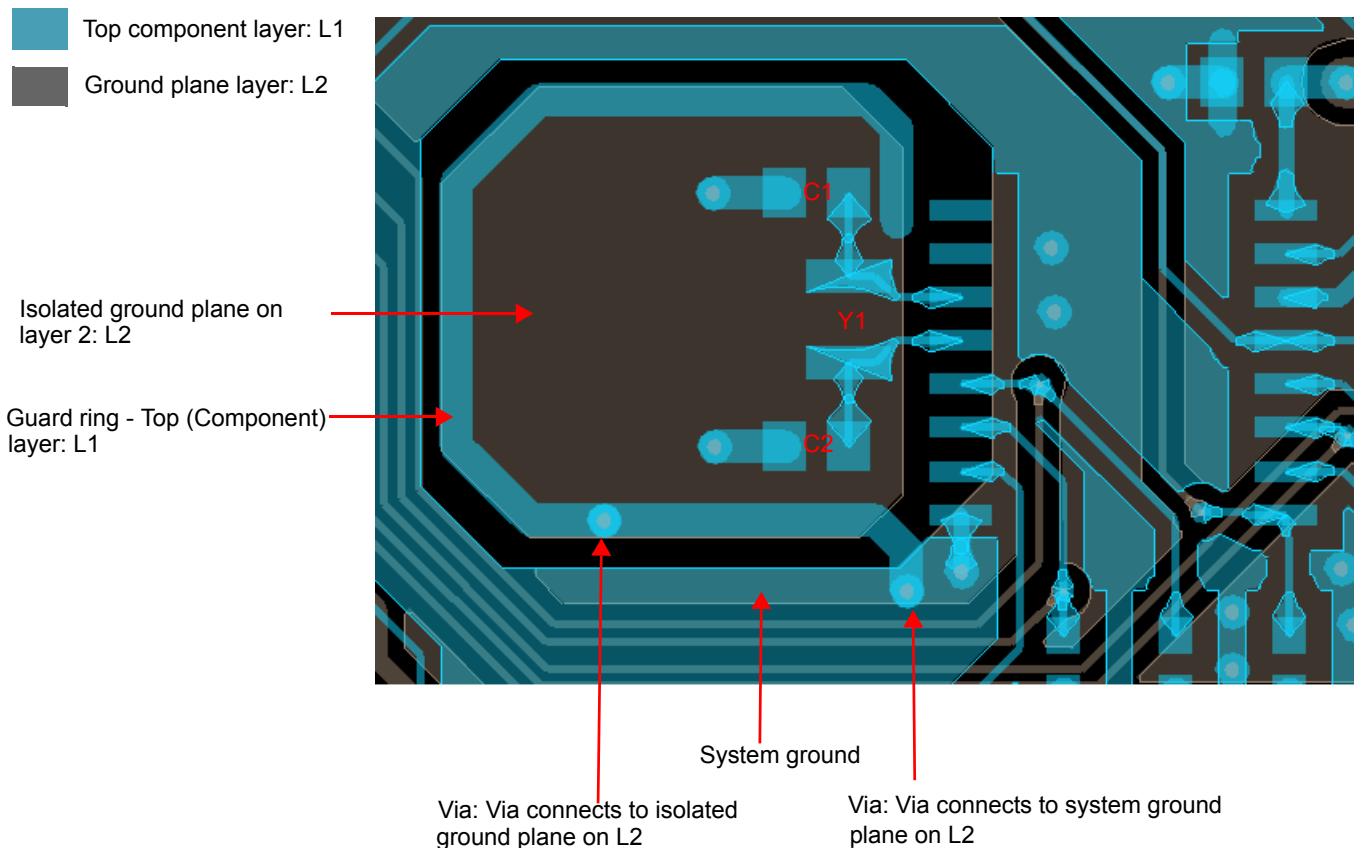
### Layout Requirements

The board layout must adhere to (but not limited to) the following guidelines during routing RTC circuitry. Following these guidelines help you achieve optimum performance from the RTC design.

- It is important to place the crystal as close as possible to the  $X_{in}$  and  $X_{out}$  pins. Keep the trace lengths between the crystal and RTC equal in length and as short as possible to reduce the probability of noise coupling by reducing the length of the antenna.

- Keep  $X_{in}$  and  $X_{out}$  trace width lesser than 8 mils. Wider trace width leads to larger trace capacitance. The larger these bond pads and traces are, the more likely it is that noise can couple from adjacent signals.
- Shield the  $X_{in}$  and  $X_{out}$  signals by providing a guard ring around the crystal circuitry. This guard ring prevents noise coupling from neighboring signals.
- Take care while routing any other high-speed signal in the vicinity of RTC traces. The more the crystal is isolated from other signals on the board, the less likely it is that noise is coupled into the crystal. Maintain a minimum of 200 mil separation between the  $X_{in}$ ,  $X_{out}$  traces and any other high-speed signal on the board.
- No signals should run underneath crystal components on the same PCB layer.
- Create an isolated solid copper plane on adjacent PCB layer and underneath the crystal circuitry to prevent unwanted noise coupled from traces routed on the other signal layers of the PCB. The local plane should be separated by at least 40 mils from the neighboring plane on the same PCB layer. The solid plane should be in the vicinity of RTC components only and its perimeter should be kept equal to the guard ring perimeter. [Figure 103](#) shows the recommended layout for RTC circuit.

Figure 103. Recommended Layout for RTC



**Table 15. RTC Register Map**<sup>[2, 3]</sup>

Register	BCD Format Data								Function/Range
	D7	D6	D5	D4	D3	D2	D1	D0	
0x0F	10s years				Years				Years: 00–99
0x0E	0	0	0	10s months	Months				Months: 01–12
0x0D	0	0	10s day of month		Day of month				Day of month: 01–31
0x0C	0	0	0	0	0	Day of week			Day of week: 01–07
0x0B	0	0	10s hours		Hours				Hours: 00–23
0x0A	0	10s minutes			Minutes				Minutes: 00–59
0x09	0	10s seconds			Seconds				Seconds: 00–59
0x08	OSCEN (0)	0	Cal sign (0)	Calibration (00000)					Calibration values <sup>[4]</sup>
0x07	WDS (0)	WDW (1)	WDT (000000)						Watchdog <sup>[4]</sup>
0x06	WIE (0)	AIE (0)	PFE (0)	SQWE (0)	H/L (1)	P/L (0)	SQ1 (0)	SQ0 (0)	Interrupts <sup>[4]</sup>
0x05	M (1)	0	10s alarm date		Alarm day				Alarm, day of month: 01–31
0x04	M (1)	0	10s alarm hours		Alarm hours				Alarm, hours: 00–23
0x03	M (1)	10s alarm minutes			Alarm minutes				Alarm, minutes: 00–59
0x02	M (1)	10s alarm seconds			Alarm seconds				Alarm, seconds: 00–59
0x01	10s centuries				Centuries				Centuries: 00–99
0x00	WDF	AF	PF	OSCF <sup>[5]</sup>	BPF <sup>[5]</sup>	CAL (0)	W (0)	R (0)	Flags <sup>[4]</sup>

**Notes**

2. ( ) designates values shipped from the factory.
3. The unused bits of RTC registers are reserved for future use and should be set to '0'.
4. This is a binary value, not a BCD value.
5. When user resets OSCF and BPF flag bits, the flags register will be updated after  $t_{RTCp}$  time.

**Table 16. Register Map Detail**

<b>0x0F</b>	<b>Time Keeping - Years</b>							
	<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
	10s years				Years			
	Contains the lower two BCD digits of the year. Lower nibble (four bits) contains the value for years; upper nibble (four bits) contains the value for 10s of years. Each nibble operates from 0 to 9. The range for the register is 0–99.							
<b>0x0E</b>	<b>Time Keeping - Months</b>							
	<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
	0	0	0	10s month		Months		
	Contains the BCD digits of the month. Lower nibble (four bits) contains the lower digit and operates from 0 to 9; upper nibble (one bit) contains the upper digit and operates from 0 to 1. The range for the register is 1–12.							
<b>0x0D</b>	<b>Time Keeping - Date</b>							
	<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
	0	0	10s day of month		Day of month			
	Contains the BCD digits for the date of the month. Lower nibble (four bits) contains the lower digit and operates from 0 to 9; upper nibble (two bits) contains the 10s digit and operates from 0 to 3. The range for the register is 1–31. Leap years are automatically adjusted for.							
<b>0x0C</b>	<b>Time Keeping - Day</b>							
	<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
	0	0	0	0	0	Day of week		
	Lower nibble (three bits) contains a value that correlates to day of the week. Day of the week is a ring counter that counts from 1 to 7 then returns to 1. The user must assign meaning to the day value, because the day is not integrated with the date.							
<b>0x0B</b>	<b>Time Keeping - Hours</b>							
	<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
	0	0	10s hours		Hours			
	Contains the BCD value of hours in 24 hour format. Lower nibble (four bits) contains the lower digit and operates from 0 to 9; upper nibble (two bits) contains the upper digit and operates from 0 to 2. The range for the register is 0–23.							
<b>0x0A</b>	<b>Time Keeping - Minutes</b>							
	<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
	0	10s minutes			Minutes			
	Contains the BCD value of minutes. Lower nibble (four bits) contains the lower digit and operates from 0 to 9; upper nibble (three bits) contains the upper minutes digit and operates from 0 to 5. The range for the register is 0–59.							
<b>0x09</b>	<b>Time Keeping - Seconds</b>							
	<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
	0	10s seconds			Seconds			
	Contains the BCD value of seconds. Lower nibble (four bits) contains the lower digit and operates from 0 to 9; upper nibble (three bits) contains the upper digit and operates from 0 to 5. The range for the register is 0–59.							
<b>0x08</b>	<b>Calibration/Control</b>							
	<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
	OSCEN	0	Calibration sign	Calibration				
OSCEN	Oscillator Enable. When set to '1', the oscillator is stopped. When set to '0', the oscillator runs. Disabling the oscillator saves battery power during storage.							
Calibration Sign	Determines if the calibration adjustment is applied as an addition (1) to or as a subtraction (0) from the time-base.							
Calibration	These five bits control the calibration of the clock.							

**Table 16. Register Map Detail (continued)**

0x07	Watchdog Timer							
	D7	D6	D5	D4	D3	D2	D1	D0
	WDS	WDW	WDT					
WDS	Watchdog Strobe. Setting this bit to '1' reloads and restarts the watchdog timer. Setting the bit to '0' has no effect. The bit is cleared automatically after the watchdog timer is reset. The WDS bit is write only. Reading it always returns a '0'.							
WDW	Watchdog Write Enable. Setting this bit to '1' disables any WRITE to the watchdog timeout value (D5–D0). This enables the user to set the watchdog strobe bit without disturbing the timeout value. Setting this bit to '0' allows bits D5–D0 to be written to the watchdog register when the next write cycle is complete. This function is explained in more detail in <a href="#">Watchdog Timer on page 46</a> .							
WDT	Watchdog Timeout Selection. The watchdog timer interval is selected by the 6-bit value in this register. It represents a multiplier of the 32 Hz count (31.25 ms). The range of timeout value is 31.25 ms (a setting of 1) to 2 seconds (setting of 3 Fh). Setting the watchdog timer register to 0 disables the timer. These bits can be written only if the WDW bit was set to '0' on a previous cycle.							
0x06	Interrupt Status/Control							
	D7	D6	D5	D4	D3	D2	D1	D0
	WIE	AIE	PFE	SQWE	H/L	P/L	SQ1	SQ0
WIE	Watchdog Interrupt Enable. When set to '1' and a watchdog timeout occurs, the watchdog timer drives the INT pin and the WDF flag. When set to '0', the watchdog timeout affects only the WDF flag.							
AIE	Alarm Interrupt Enable. When set to '1', the alarm match drives the INT pin and the AF flag. When set to '0', the alarm match only affects the AF flag.							
PFE	Power Fail Enable. When set to '1', the alarm match drives the INT pin and the PF flag. When set to '0', the power fail monitor affects only the PF flag.							
SQWE	Square Wave Enable. When set to '1', a square wave is driven on the INT pin with frequency programmed using SQ1 and SQ0 bits. The square wave output takes precedence over interrupt logic. If the SQWE bit is set to '1', when an enabled interrupt source becomes active, only the corresponding flag is raised and the INT pin continues to drive the square wave.							
H/L	High/Low. When set to '1', the INT pin is driven active HIGH. When set to '0', the INT pin is open drain, active LOW.							
P/L	Pulse/Level. When set to '1', the INT pin is driven active (determined by H/L) by an interrupt source for approximately 200 ms. When set to '0', the INT pin is driven to an active level (as set by H/L) until the flags register is read.							
SQ1, SQ0	SQ1, SQ0. These bits are used to decide the frequency of the Square wave on the INT pin output when the SQWE bit is set to '1'. The following is the frequency output for each combination of (SQ1, SQ0): (0, 0) - 1 Hz (0, 1) - 512 Hz (1, 0) - 4096 Hz (1, 1) - 32768 Hz							
0x05	Alarm - Day							
	D7	D6	D5	D4	D3	D2	D1	D0
	M	0	10s alarm date			Alarm date		
M	Contains the alarm value for the date of the month and the mask bit to select or deselect the date value.							
M	Match. When this bit is set to '0', the date value is used in the alarm match. Setting this bit to '1' causes the match circuit to ignore the date value.							
0x04	Alarm - Hours							
	D7	D6	D5	D4	D3	D2	D1	D0
	M	0	10s alarm hours			Alarm hours		
M	Contains the alarm value for the hours and the mask bit to select or deselect the hours value.							
M	Match. When this bit is set to '0', the hours value is used in the alarm match. Setting this bit to '1' causes the match circuit to ignore the hours value.							

**Table 16. Register Map Detail** (continued)

		<b>Alarm - Minutes</b>							
<b>0x03</b>		<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
		M	10s alarm minutes				Alarm minutes		
		Contains the alarm value for the minutes and the mask bit to select or deselect the minutes value.							
M	Match. When this bit is set to '0', the minutes value is used in the alarm match. Setting this bit to '1' causes the match circuit to ignore the minutes value.								
		<b>Alarm - Seconds</b>							
<b>0x02</b>		<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
		M	10s alarm seconds				Alarm seconds		
		Contains the alarm value for the seconds and the mask bit to select or deselect the seconds' value.							
M	Match. When this bit is set to '0', the seconds value is used in the alarm match. Setting this bit to '1' causes the match circuit to ignore the seconds value.								
		<b>Time Keeping - Centuries</b>							
<b>0x01</b>		<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
		10s centuries				Centuries			
		Contains the BCD value of centuries. Lower nibble contains the lower digit and operates from 0 to 9; upper nibble contains the upper digit and operates from 0 to 9. The range for the register is 0–99 centuries.							
		<b>Flags</b>							
<b>0x00</b>		<b>D7</b>	<b>D6</b>	<b>D5</b>	<b>D4</b>	<b>D3</b>	<b>D2</b>	<b>D1</b>	<b>D0</b>
		WDF	AF	PF	OSCF	BPF	CAL	W	R
WDF	Watchdog Timer Flag. This read only bit is set to '1' when the watchdog timer is allowed to reach 0 without being reset by the user. It is cleared to '0' when the flags register is read or on power-up								
AF	Alarm Flag. This read-only bit is set to '1' when the time and date match the values stored in the alarm registers with the match bits = '0'. It is cleared when the flags register is read or on power-up.								
PF	Power Fail Flag. This read-only bit is set to '1' when power falls below the power fail threshold $V_{SWITCH}$ . It is cleared when the flags register is read.								
OSCF	Oscillator Fail Flag. Set to '1' on power-up if the oscillator is enabled and not running in the first 5 ms of operation. This indicates that RTC backup power failed and clock value is no longer valid. This bit survives power cycle and is never cleared internally by the chip. The user must check for this condition and write '0' to clear this flag. When user resets OSCF flag bit, the bit will be updated after $t_{RTCp}$ time.								
BPF	Backup Power Fail Flag. Set to '1' on power-up if the backup power (battery) failed. The backup power fail condition is determined by the voltage falling below their respective minimum specified voltage. BPF can hold the data only until a defined low level of the back-up voltage ( $V_{DR}$ ). User must reset this bit to clear this flag. When user resets BPF flag bit, the bit will be updated after $t_{RTCp}$ time.								
CAL	Calibration Mode. When set to '1', a 512 Hz square wave is output on the INT pin. When set to '0', the INT pin resumes normal operation. This bit takes priority than SQ0/SQ1 and other functions. This bit defaults to '0' (disabled) on power-up.								
W	Write Enable: Setting the W bit to '1' freezes updates of the RTC registers. The user can then write to RTC registers, alarm registers, calibration register, interrupt register and flags register. Setting the W bit to '0' causes the contents of the RTC registers to be transferred to the time keeping counters if the time has changed. This transfer process takes $t_{RTCp}$ time to complete. This bit defaults to '0' on power-up.								
R	Read Enable: Setting the R bit to '1', stops clock updates to user RTC registers so that clock updates are not seen during the reading process. Set the R bit to '0' to resume clock updates to the holding register. Setting this bit does not require the W bit to be set to '1'. This bit defaults to '0' on power-up.								

### Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

- Storage temperature ..... -65 °C to +150 °C
- Maximum accumulated storage time
  - At 150 °C ambient temperature ..... 1000 h
  - At 85 °C ambient temperature ..... 20 Years
- Maximum junction temperature ..... 150 °C
- Supply voltage on V<sub>CC</sub> relative to V<sub>SS</sub> ..... -0.5 V to +4.1 V
- Supply voltage on V<sub>CCQ</sub> relative to V<sub>SS</sub> ..... -0.5 V to +2.45 V
- DC voltage applied to outputs in HI-Z state ..... -0.5 V to V<sub>CCQ</sub> + 0.5 V
- Input voltage ..... -0.5 V to V<sub>CCQ</sub> + 0.5 V
- Transient voltage (< 20 ns) on any pin to ground potential ..... -2.0 V to V<sub>CCQ</sub> + 2.0 V

- Package power dissipation capability (T<sub>A</sub> = 25 °C)
  - 16-pin SOIC ..... 1.0 W
- Package power dissipation capability (T<sub>A</sub> = 25 °C) ..... 1.0 W
- Surface mount lead soldering temperature (3 seconds) ..... +260 °C
- DC output current (1 output at a time, 1-s duration) ... 15 mA
- Static discharge voltage (per MIL-STD-883, Method 3015) ..... > 2001 V
- Latch-up current ..... > 140 mA

### Operating Range

Range	Ambient Temperature	V <sub>CC</sub>	V <sub>CCQ</sub>
Industrial	-40 °C to +85 °C	2.7 V to 3.6 V	1.71 V to 2.0 V

### DC Specifications

Parameter	Description	Test Conditions	Min	Typ <sup>[6]</sup>	Max	Units
V <sub>CC</sub>	Power Supply - Core voltage	-	2.70	3.00	3.60	V
V <sub>CCQ</sub>	Power Supply - I/O voltage	-	1.71	1.80	2.00	V
I <sub>CC1</sub>	Average Read/Write V <sub>CC</sub> Current (all inputs toggling, no output load)	SPI = 1 MHz	-	-	1.00	mA
		SPI = 40 MHz	-	-	3.00	mA
		QPI = 108 MHz	-	-	33.00	mA
I <sub>CCQ1</sub>	Average V <sub>CCQ</sub> Current (all inputs toggling, no output load)	SPI = 1 MHz	-	-	150.00	µA
		SPI = 40 MHz	-	-	1.00	mA
		QPI = 108 MHz	-	-	5.00	mA
I <sub>SB1</sub>	Standby Current at 85 °C (V <sub>CC</sub> + V <sub>CCQ</sub> )	CS > (V <sub>CCQ</sub> - 0.2 V). Standby current level after nonvolatile cycle is complete (CS High, other I/Os have no restrictions, f <sub>SCK</sub> ≤ 108 MHz).	-	-	1.8	mA
I <sub>SB2</sub>	Standby Current at 85 °C (V <sub>CC</sub> + V <sub>CCQ</sub> )	CS > (V <sub>CCQ</sub> - 0.2 V). Standby current level after nonvolatile cycle is complete. All I/Os Static, f <sub>SCK</sub> = 0 MHz.	-	-	380.00	µA
I <sub>CC2</sub>	Average V <sub>CC</sub> current during STORE	-	-	-	6.00	mA
I <sub>CC4</sub>	Average V <sub>CAP</sub> current during AUTOSTORE	-	-	-	6.00	mA
I <sub>SLEEP</sub>	Sleep Mode current at 85 °C (V <sub>CC</sub> + V <sub>CCQ</sub> )	CS > (V <sub>CCQ</sub> - 0.2 V). Sleep current level after nonvolatile cycle is complete. All I/Os Static, f <sub>SCK</sub> = 0 MHz.	-	-	380	µA
I <sub>ZZ</sub>	Hibernate mode current at 85 °C (V <sub>CC</sub> + V <sub>CCQ</sub> )	CS > (V <sub>CCQ</sub> - 0.2 V). t <sub>HIBEN</sub> time after HIBEN Instruction is registered. All inputs are static and configured at CMOS logic level.	-	-	8.00	µA

**Notes**  
 6. Typical values are at 25 °C, V<sub>CC</sub> = V<sub>CC(TYP)</sub> and V<sub>CCQ</sub> = V<sub>CCQ(TYP)</sub>. Not 100% tested.

**DC Specifications** (continued)

Parameter	Description	Test Conditions	Min	Typ <sup>[6]</sup>	Max	Units
I <sub>IX</sub>	Input leakage current (except HSB)	V <sub>CCQ</sub> = Max, V <sub>SS</sub> < V <sub>IN</sub> < V <sub>CCQ</sub> –	–1.00	–	1.00	μA
	Input leakage current (for HSB)		–100.00	–	1.00	μA
	Input leakage current (for WP in SPI/DPI modes)		–2	–	1	μA
I <sub>OZ</sub>	Off State Output Leakage Current	V <sub>CCQ</sub> = Max, V <sub>SS</sub> < V <sub>IN</sub> < V <sub>CCQ</sub>	–1.00	–	1.00	μA
V <sub>IH</sub>	Input high voltage	–	0.70 * V <sub>CCQ</sub>	–	V <sub>CCQ</sub> + 0.30	V
V <sub>IL</sub>	Input low voltage	–	–0.30	–	0.30 * V <sub>CCQ</sub>	V
V <sub>OH</sub>	Output high voltage at –2 mA	I <sub>OH</sub> = –2 mA	V <sub>CCQ</sub> –0.45	–	–	V
V <sub>OL</sub>	Output low voltage at 2 mA	I <sub>OL</sub> = 2 mA	–	–	0.45	V
V <sub>CAP</sub> <sup>[7]</sup>	Storage capacitor	Between V <sub>CAP</sub> pin and V <sub>SS</sub>	61.00	68.00	120.00	μF
V <sub>VCAP</sub> <sup>[8]</sup>	Maximum Voltage Driven on V <sub>CAP</sub> Pin	–	–	–	V <sub>CC</sub>	V

**Data Retention and Endurance**

Parameter	Description	Min	Unit
DATA <sub>R</sub>	Data retention at 85 °C	20	Years
NV <sub>C</sub>	Nonvolatile STORE operations	1,000	K

**Capacitance**

Parameter <sup>[8]</sup>	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	T <sub>A</sub> = 25 °C, f = 1 MHz, V <sub>CC</sub> = V <sub>CC(typ)</sub> , V <sub>CCQ</sub> = V <sub>CCQ(typ)</sub>	6.00	pF
C <sub>SCK</sub>	Clock input capacitance			
C <sub>OUT</sub>	Output pin capacitance			

**Thermal Resistance**

Parameter <sup>[8]</sup>	Description	Test Conditions	16-Pin SOIC	Unit
Θ <sub>JA</sub>	Thermal resistance (junction to ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51.	61.21	°C/W
Θ <sub>JC</sub>	Thermal resistance (junction to case)		26.20	

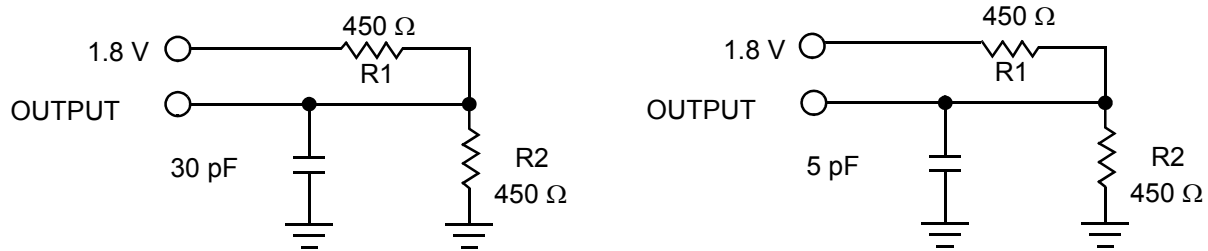
**Notes**

- Min V<sub>CAP</sub> value guarantees that there is a sufficient charge available to complete a successful AutoStore operation. Max V<sub>CAP</sub> value guarantees that the capacitor on V<sub>CAP</sub> is charged to a minimum voltage during a power-up RECALL cycle so that an immediate power-down cycle can complete a successful AutoStore. Therefore, it is always recommended to use a capacitor within the specified min and max limits. Refer application note [AN43593](#) for more details on V<sub>CAP</sub> options.
- These parameters are guaranteed by design and are not tested.



## AC Test Loads and Waveforms

Figure 104. AC Test Loads and Waveforms



## AC Test Conditions

Description	CY14V101PS
Input pulse levels	0 V to 1.8 V
Input rise and fall times (10%–90%)	≤ 1.8 ns
Input and output timing reference levels	0.9 V

## RTC Characteristics

Parameter	Description	Min	Typ <sup>[9]</sup>	Max	Units
V <sub>RTCbat</sub>	RTC battery pin voltage	1.80	3.00	3.60	V
I <sub>BAK</sub> <sup>[10]</sup>	RTC backup current (Refer <a href="#">Figure 102</a> for the recommended external components for RTC)	–	0.60	1.00	μA
t <sub>OCS</sub>	RTC oscillator time to start	–	1.00	2.00	sec
V <sub>BAKFAIL</sub>	Backup failure threshold	1.80	–	2.50	V
t <sub>RTCP</sub>	RTC processing time from end of 'W' bit set to '0'	–	–	1	ms

### Notes

9. Typical values are at 25 °C, V<sub>CC</sub> = V<sub>CC(Typ)</sub>. Not 100% tested.

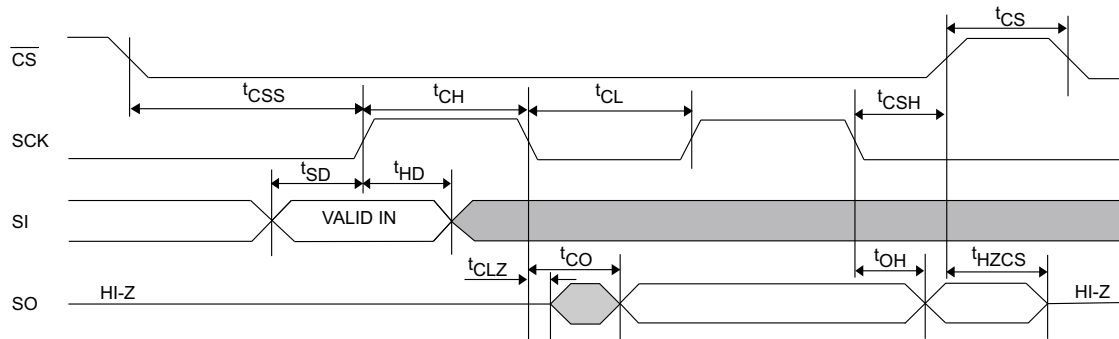
10. Current drawn from V<sub>RTCbat</sub> when V<sub>CC</sub> < V<sub>SWITCH</sub>.

## AC Switching Characteristics

Parameter <sup>[11]</sup>	Description	Min	Max	Units
$f_{SCK}$	Clock frequency (QPI)	–	108.00	MHz
$t_{CL}$	Clock Pulse Width Low	$0.45 * 1/f_{SCK}$	–	ns
$t_{CH}$	Clock Pulse Width High	$0.45 * 1/f_{SCK}$	–	ns
$t_{CS}$	CS HIGH time			
	End of READ	10.00	–	ns
	End of WRITE	10.00	–	ns
$t_{CSS}$	CS setup time	5.00	–	ns
$t_{CSH}$	CS hold time	5.00	–	ns
$t_{SD}$	Data in setup time	2.00	–	ns
$t_{HD}$	Data in hold time	3.00	–	ns
$t_{SW}$	WP setup time	2.00	–	ns
$t_{HW}$	WP hold time	2.00	–	ns
$t_{CO}$	Output Valid	–	7.00	ns
$t_{CLZ}$	Clock Low to Output Low Z	0.00	–	ns
$t_{OH}$	Output Hold Time	1.00	–	ns
$t_{HZCS}$ <sup>[12]</sup>	Output Disable Time	–	7.00	ns

## Switching Waveforms

Figure 105. Synchronous Data Timing (Mode 0)



### Notes

- Test conditions assume signal transition time of 1.8 ns or less, timing reference levels of  $V_{CCQ}/2$ , input pulse levels of 0 to  $V_{CCQ(typ)}$ , and output loading of the specified  $I_{OL}/I_{OH}$  and load capacitance shown in Figure 104 on page 57.
- These parameters are guaranteed by design and are not tested.

## AutoStore or Power-Up RECALL

Over the [Operating Range](#)

Parameter	Description	Min	Max	Unit
$t_{FA}^{[13]}$	Power-Up RECALL duration	–	20.00	ms
$t_{STORE}^{[14]}$	STORE cycle duration	–	8.00	ms
$t_{DELAY}^{[15]}$	Time taken to initiate store cycle	–	25.00	ns
$V_{SWITCH}$	Low voltage trigger level for $V_{CC}$	–	2.60	V
$t_{VCCRISE}^{[16]}$	$V_{CC}$ rise time	150.00	–	$\mu$ s
$V_{HDIS}^{[16]}$	HSB output disable voltage	–	1.90	V
$V_{IODIS}^{[17]}$	I/O disable voltage on $V_{CCQ}$	–	1.50	V
$t_{LZHSB}^{[16]}$	$\overline{HSB}$ HIGH to nvSRAM active time	–	5.00	$\mu$ s
$t_{HHHD}^{[16]}$	HSB HIGH active time	–	500.00	ns
$t_{WAKE}$	Time for nvSRAM to wake up from HIBERNATE mode	–	20.00	ms
$t_{HIBEN}$	Time to enter HIBERNATE mode after issuing HIBEN instruction	–	8.00	ms
$t_{SLEEP}$	Time to enter into sleep mode after $\overline{CS}$ going HIGH	–	0.00	$\mu$ s
$t_{EXSLP}$	Time to exit from sleep mode after $\overline{CS}$ going HIGH	–	0.00	$\mu$ s
$t_{RESET}$	Soft reset duration	–	500.00	$\mu$ s

### Notes

13.  $t_{FA}$  starts from the time  $V_{CC}$  rises above  $V_{SWITCH}$ .

14. If an SRAM write has not taken place since the last nonvolatile cycle, AutoStore or Hardware STORE is not initiated.

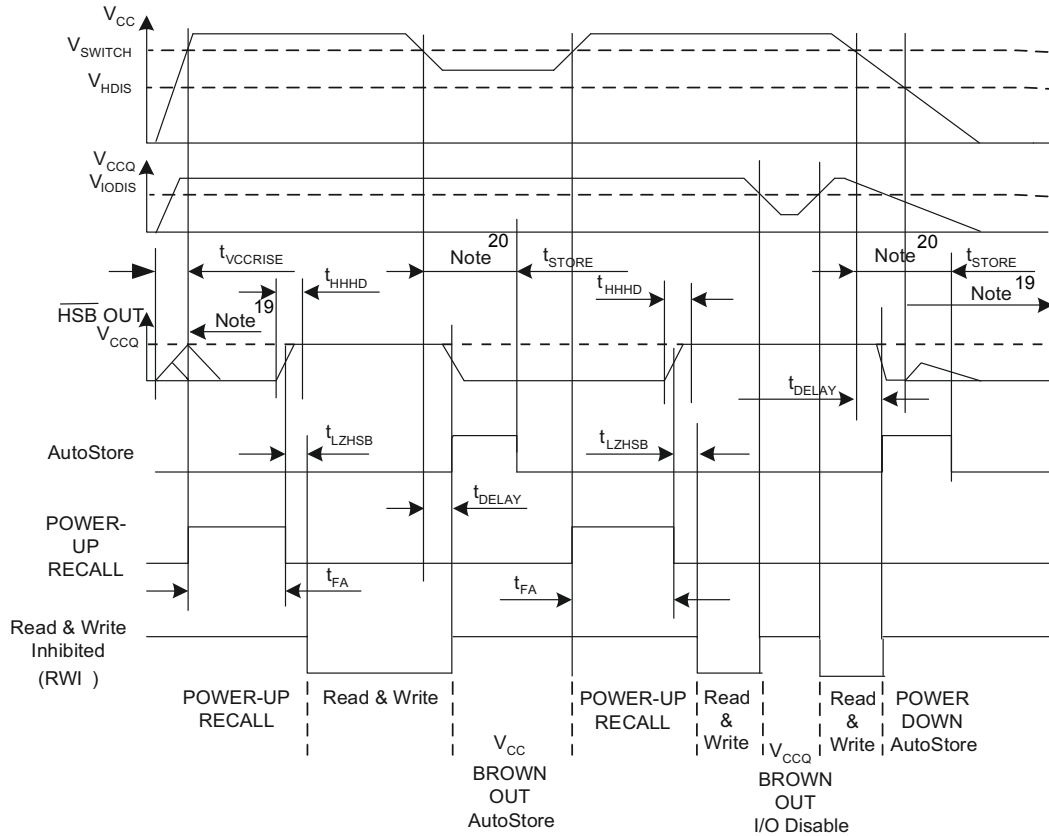
15. On a Hardware STORE, Software STORE/RECALL, AutoStore Enable/Disable and AutoStore initiation, SRAM operation continues to be enabled for time  $t_{DELAY}$ .

16. These parameters are guaranteed by design and are not tested.

17. HSB is not defined below  $V_{IODIS}$  voltage.

## Switching Waveforms

Figure 106. AutoStore or Power-Up RECALL<sup>[18]</sup>



### Notes

18. Read and write cycles are ignored during STORE, RECALL, and while  $V_{CC}$  is below  $V_{SWITCH}$ .
19. During power-up and power-down, HSB glitches when HSB pin is pulled up through an external resistor.
20. If an SRAM write has not taken place since the last nonvolatile cycle, AutoStore or Hardware STORE is not initiated.

## Software Controlled STORE and RECALL Cycles

Over the [Operating Range](#)

Parameter	Description	Min	Max	Unit
$t_{\text{RECALL}}$	RECALL duration	–	500	$\mu\text{s}$
$t_{\text{SS}}^{[21, 22]}$	Soft sequence processing time	–	500	$\mu\text{s}$

## Switching Waveforms

Figure 107. Software STORE Cycle<sup>[22]</sup>

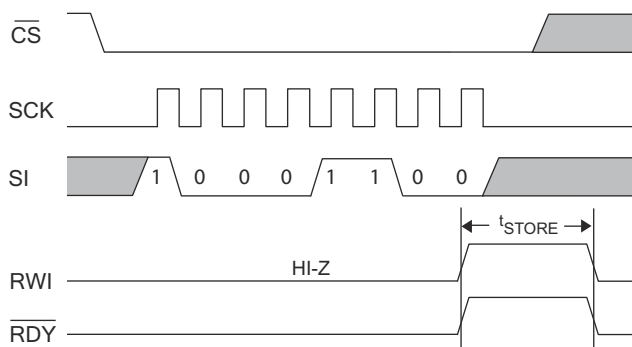


Figure 108. Software RECALL Cycle<sup>[22]</sup>

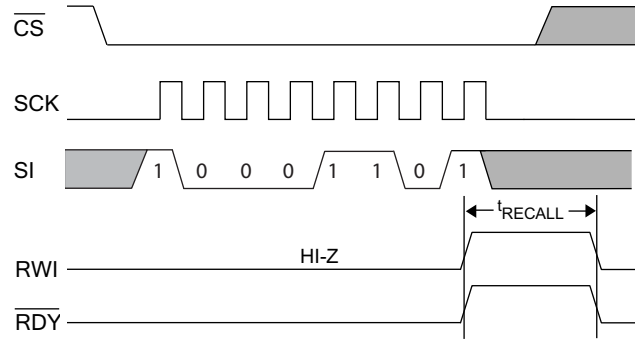


Figure 109. AutoStore Enable Cycle

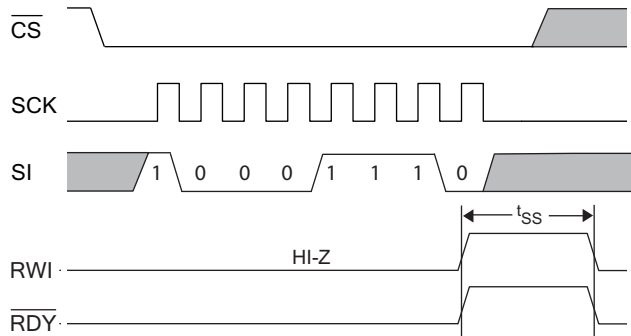
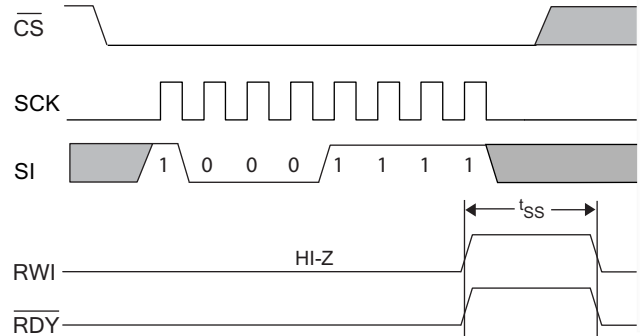


Figure 110. AutoStore Disable Cycle



### Notes

- 21. This is the amount of time it takes to take action on a soft sequence command. Vcc power must remain HIGH to effectively register command.
- 22. Commands such as STORE and RECALL lock out I/O until operation is complete which further increases this time. See the specific command.

## Hardware STORE Cycle

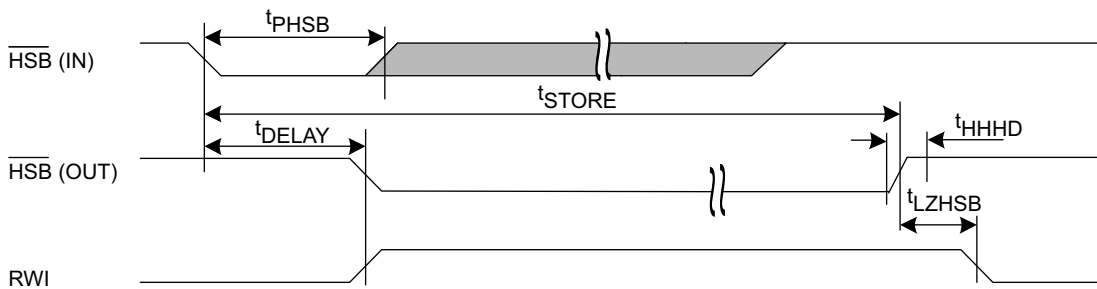
Over the [Operating Range](#)

Parameter	Description	Min	Max	Unit
t <sub>PHSB</sub>	Hardware STORE pulse width	15	600	ns

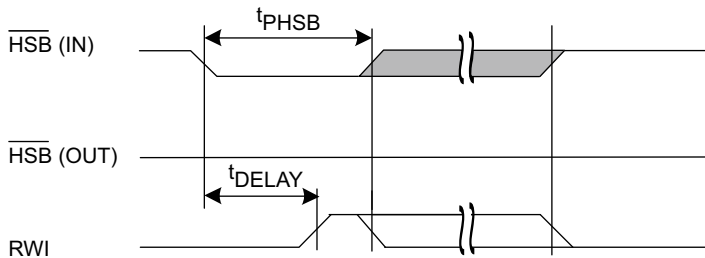
## Switching Waveforms

Figure 111. Hardware STORE Cycle<sup>[23]</sup>

Write Latch set



Write Latch not set



HSB pin is driven HIGH to V<sub>CC</sub> only by Internal 100 KΩ resistor, HSB driver is disabled  
SRAM is disabled as long as HSB (IN) is driven LOW.

Figure 112. Data Valid to HSB

**Note**

23. If an SRAM write has not taken place since the last nonvolatile cycle, AutoStore or Hardware STORE is not initiated.

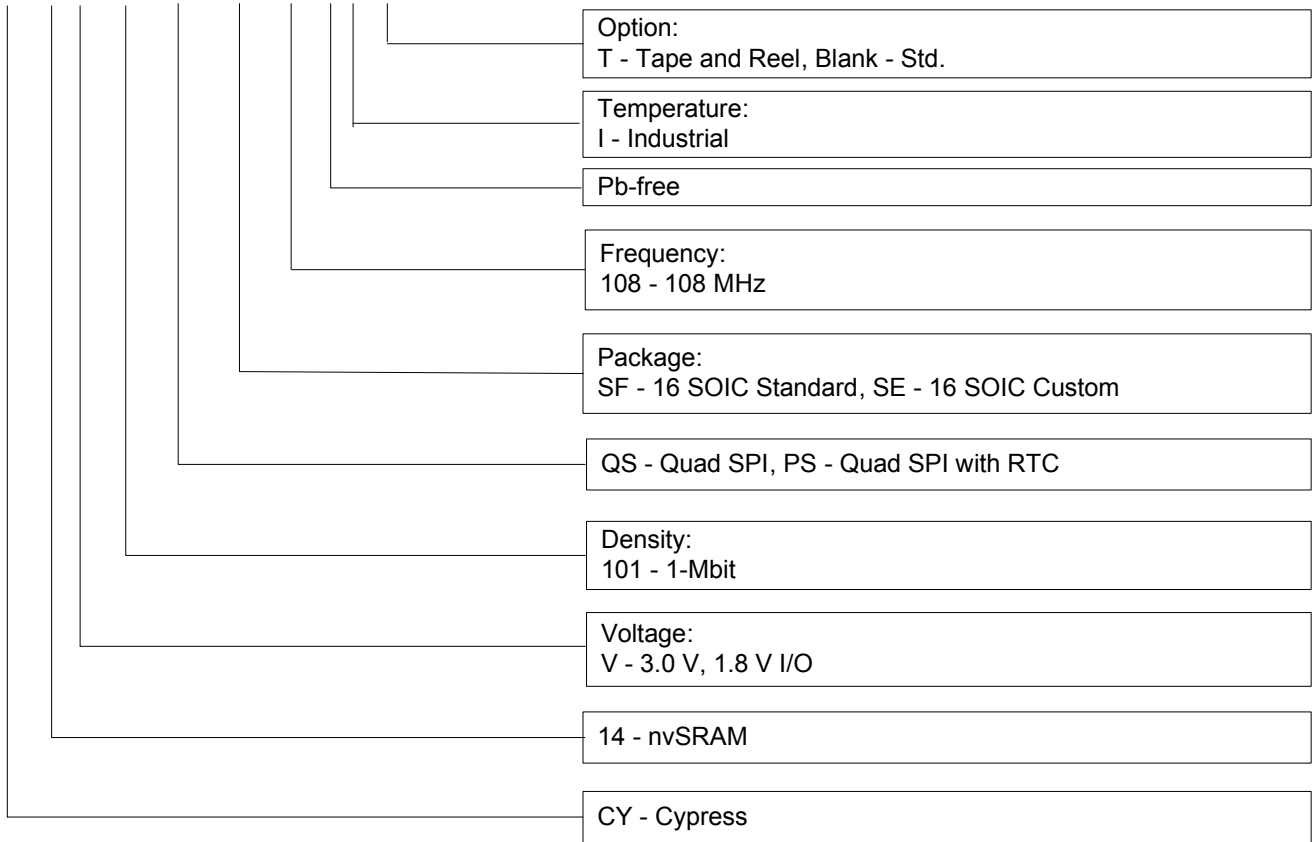
**Ordering Information**

Ordering Code	Package Diagram	Package Type, Pinout	Operating Range
CY14V101PS-SF108XI	51-85022	16-SOIC	Industrial
CY14V101PS-SF108XIT			

All these parts are Pb-free. Contact your local Cypress sales representative for availability of these parts.

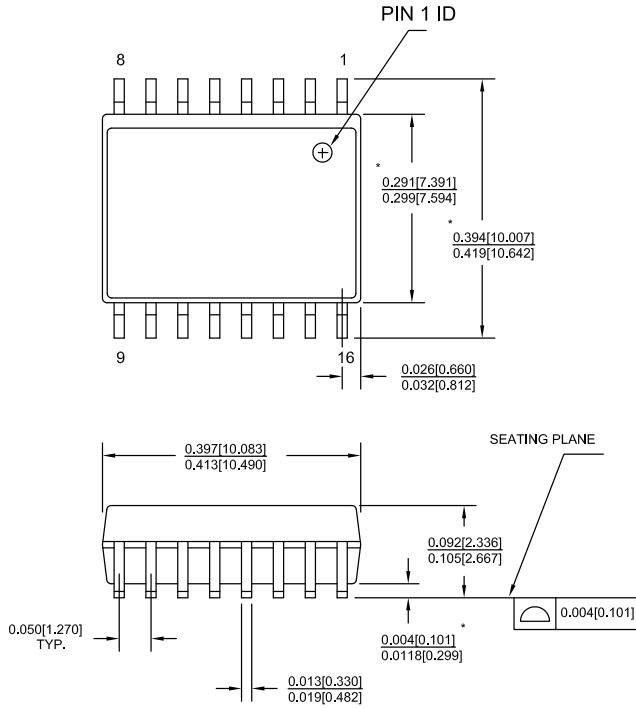
**Ordering Code Definitions**

**CY 14 V 101 PS - SF 108 X I T**



Package Diagrams

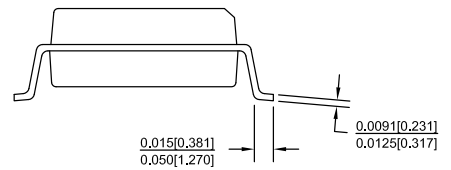
Figure 113. 16-Pin SOIC (0.413 × 0.299 × 0.0932 Inches) Package Outline, 51-85022



DIMENSIONS IN INCHES[MM] MIN.  
MAX.

REFERENCE JEDEC MO-119

PART #	
S16.3	STANDARD PKG.
SZ16.3	LEAD FREE PKG.



51-85022 \*E



## Acronyms

Acronym	Description
CPHA	clock phase
CPOL	clock polarity
CMOS	complementary metal oxide semiconductor
CRC	cyclic redundancy check
EEPROM	electrically erasable programmable read-only memory
EIA	Electronic Industries Alliance
I/O	input/output
JEDEC	Joint Electron Devices Engineering Council
LSB	least significant bit
MSB	most significant bit
nvSRAM	nonvolatile static random access memory
RWI	read and write inhibit
RoHS	restriction of hazardous substances
SNL	serial number lock
SPI	serial peripheral interface
SONOS	silicon-oxide-nitride-oxide semiconductor
SOIC	small outline integrated circuit
SRAM	static random access memory

## Document Conventions

### Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
Hz	hertz
kHz	kilohertz
kΩ	kilohm
Mbit	megabit
MHz	megahertz
μA	microampere
μF	microfarad
μs	microsecond
mA	milliampere
ms	millisecond
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

**Document History Page**

Document Title: CY14V101PS, 1-Mbit (128K × 8) Quad SPI nvSRAM with Real Time Clock				
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Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*H	5003596	SZZX	11/05/2015	Release to web.
*I	5081889	JLTO	01/19/2016	Updated <a href="#">Functional Overview</a> , <a href="#">Pin Definitions</a> , <a href="#">Device Operation</a> , <a href="#">STORE Operation</a> , <a href="#">Hardware RECALL (Power-Up)</a> , <a href="#">Read Instructions</a> , <a href="#">DC Specifications</a> , and <a href="#">AC Switching Characteristics</a> . Updated <a href="#">Figure 4</a> through <a href="#">Figure 99</a> , <a href="#">Figure 102</a> , and <a href="#">Figure 107</a> through <a href="#">Figure 110</a> . Updated <a href="#">Table 1</a> and <a href="#">Table 2</a> . Updated $t_{\text{DELAY}}$ description in <a href="#">AutoStore or Power-Up RECALL</a> table. Added <a href="#">Figure 112</a> . Removed "Preliminary" document status.
*J	5973877	AESATMP8	11/24/2017	Updated logo and Copyright.